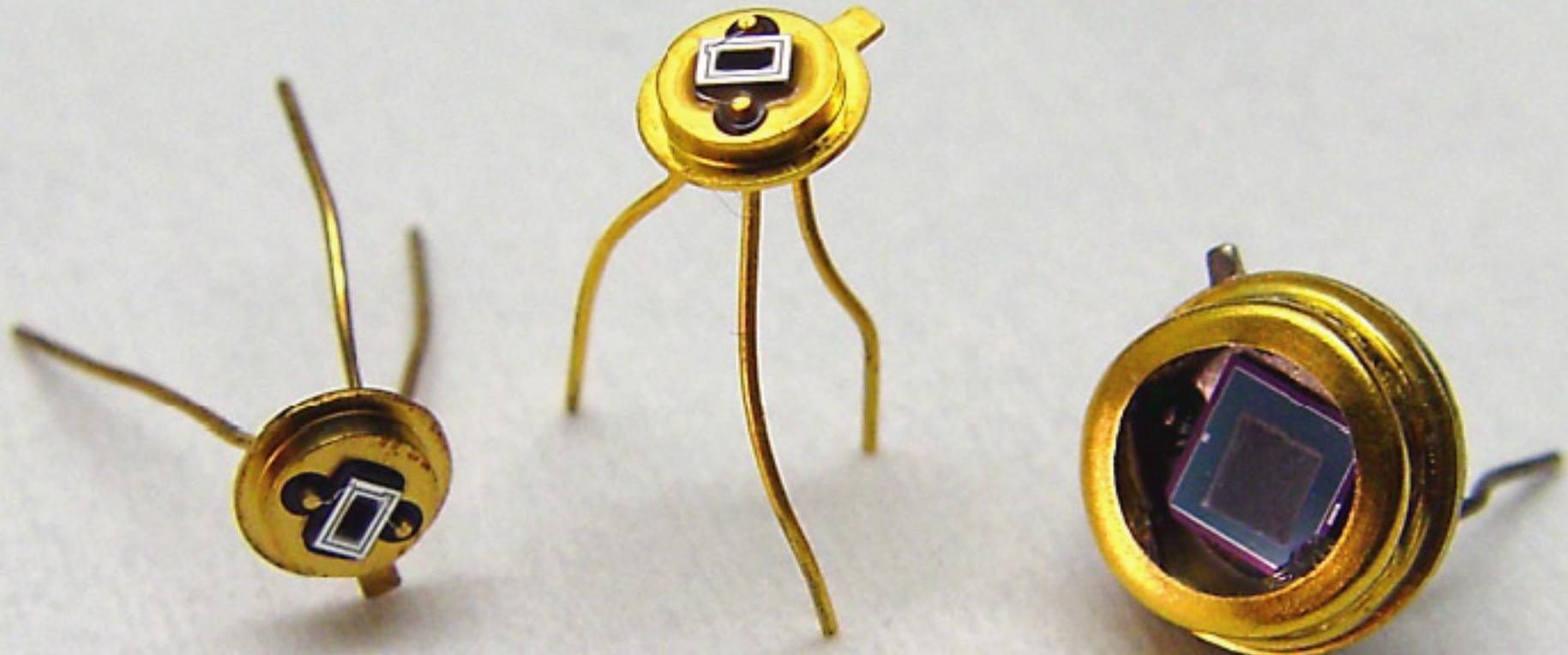


# Femtosecond-laser Microstructuring of Silicon for Novel Optoelectronic Devices



James Carey  
Photonics West  
San Jose, CA, 25 January 2005

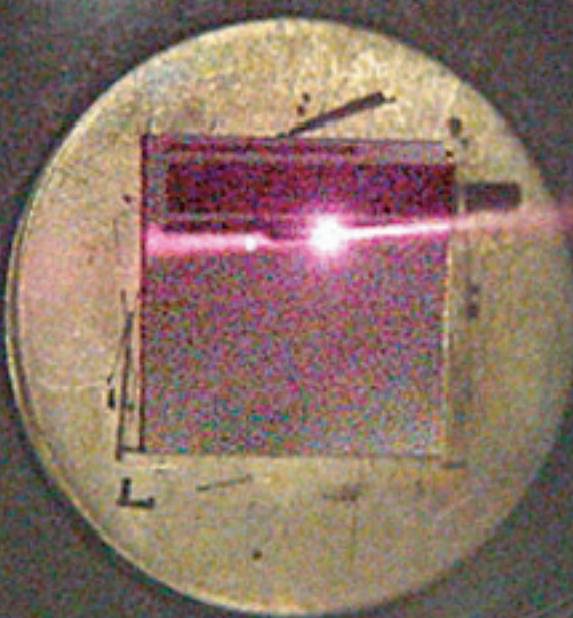


# Motivation

## Silicon:

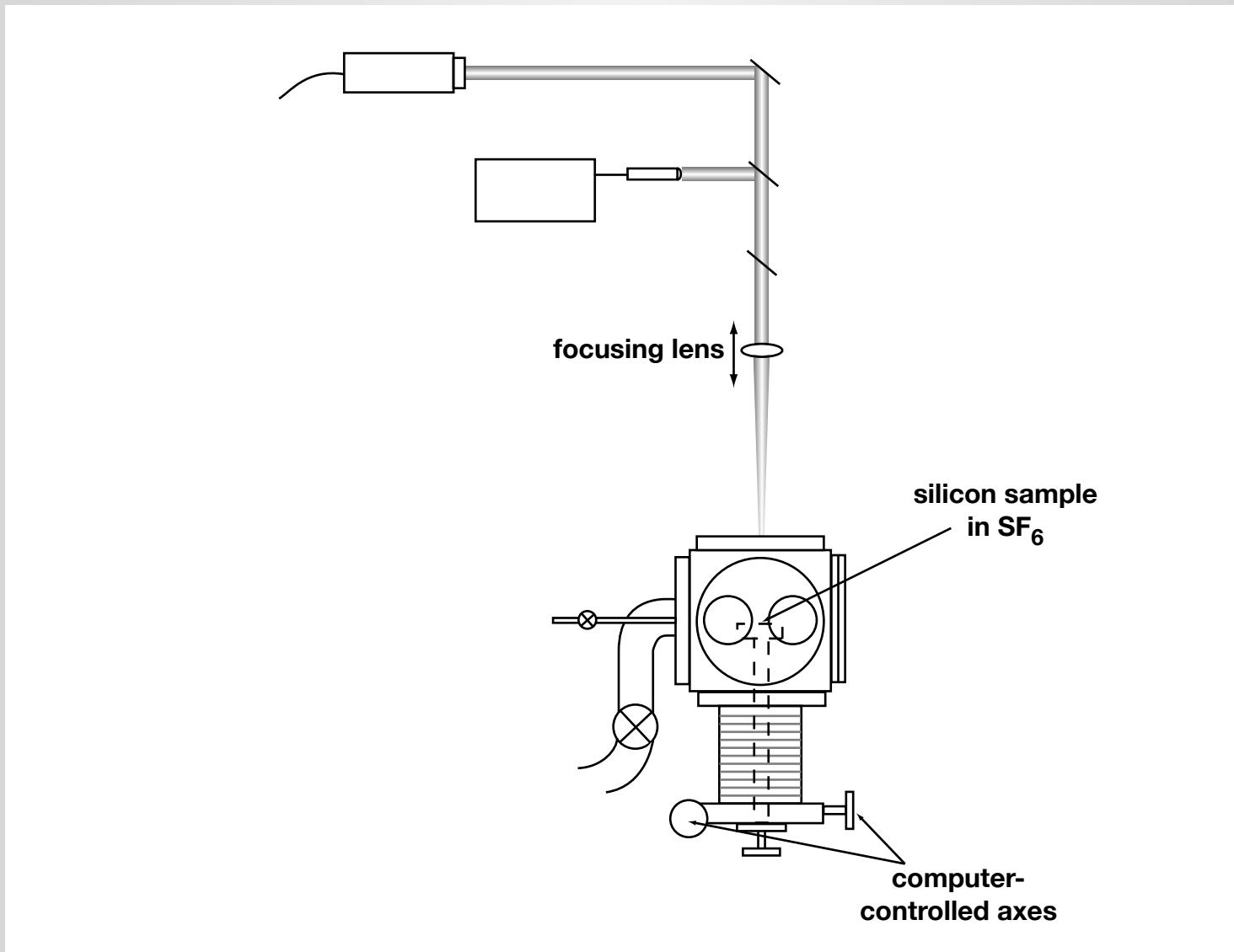
- **most widely used semiconductor**
- **enormous infrastructure, inexpensive**
- **can't do everything**
- **alter silicon to improve functionality**

# Introduction



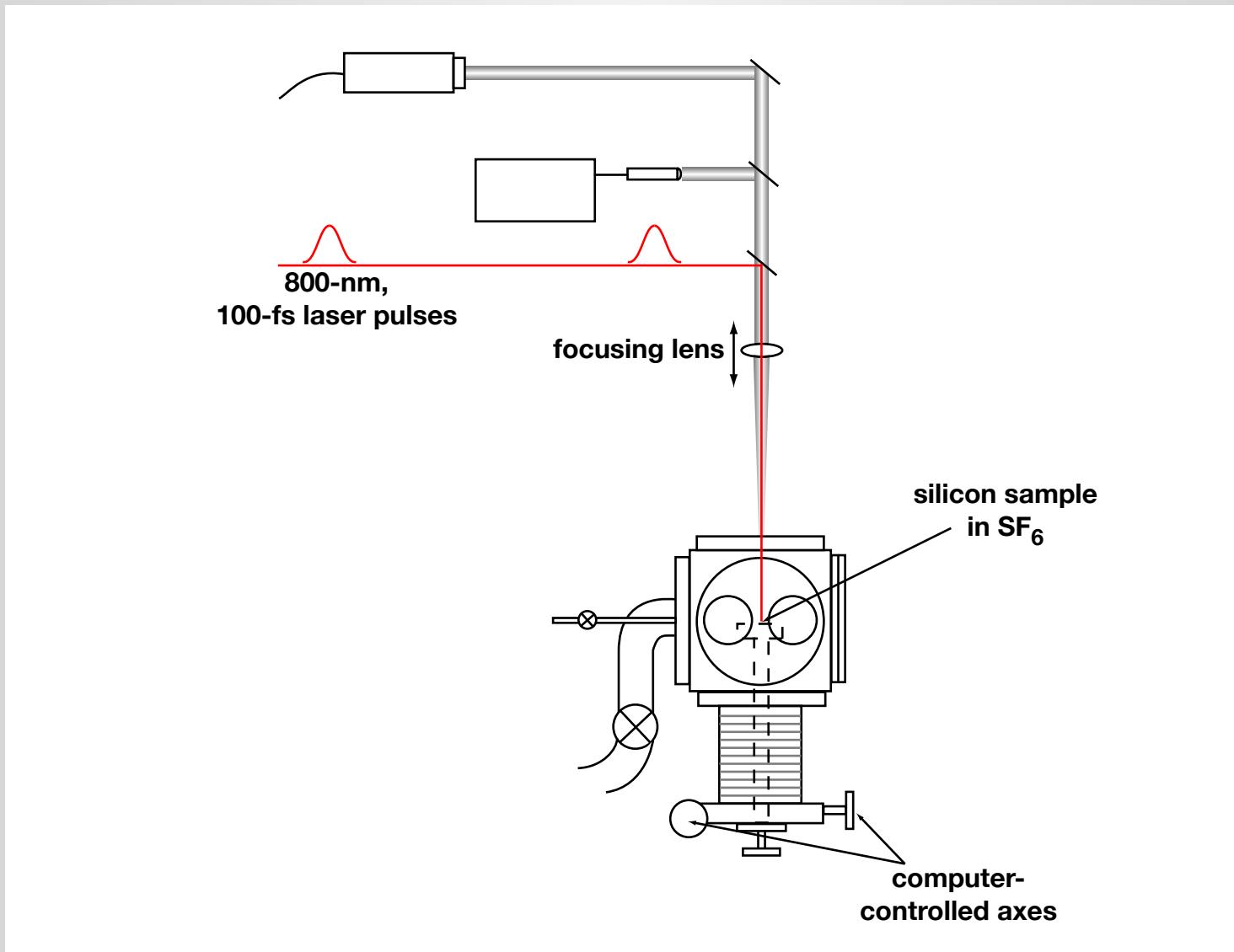
# Introduction

## apparatus

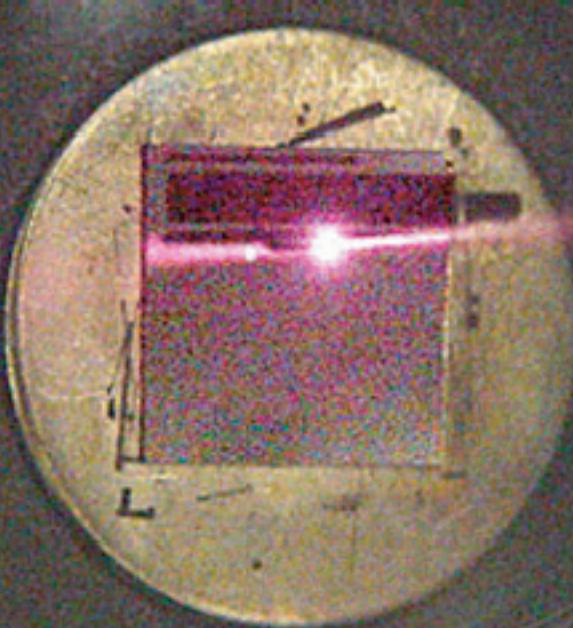


# Introduction

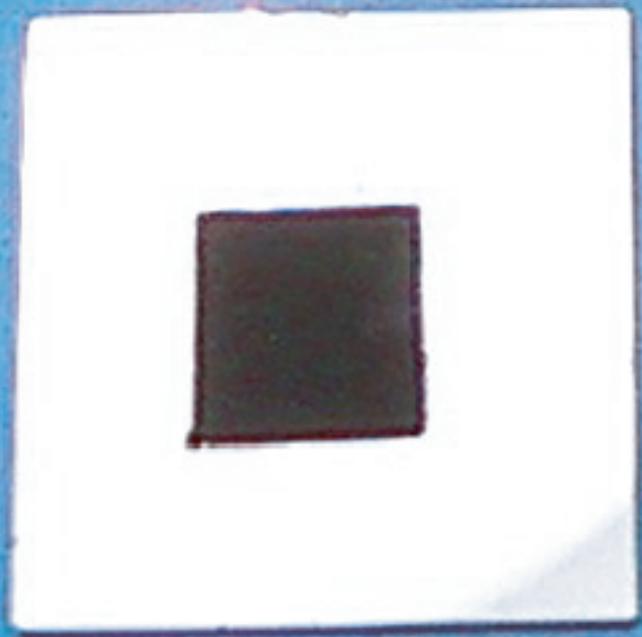
## apparatus



# Introduction



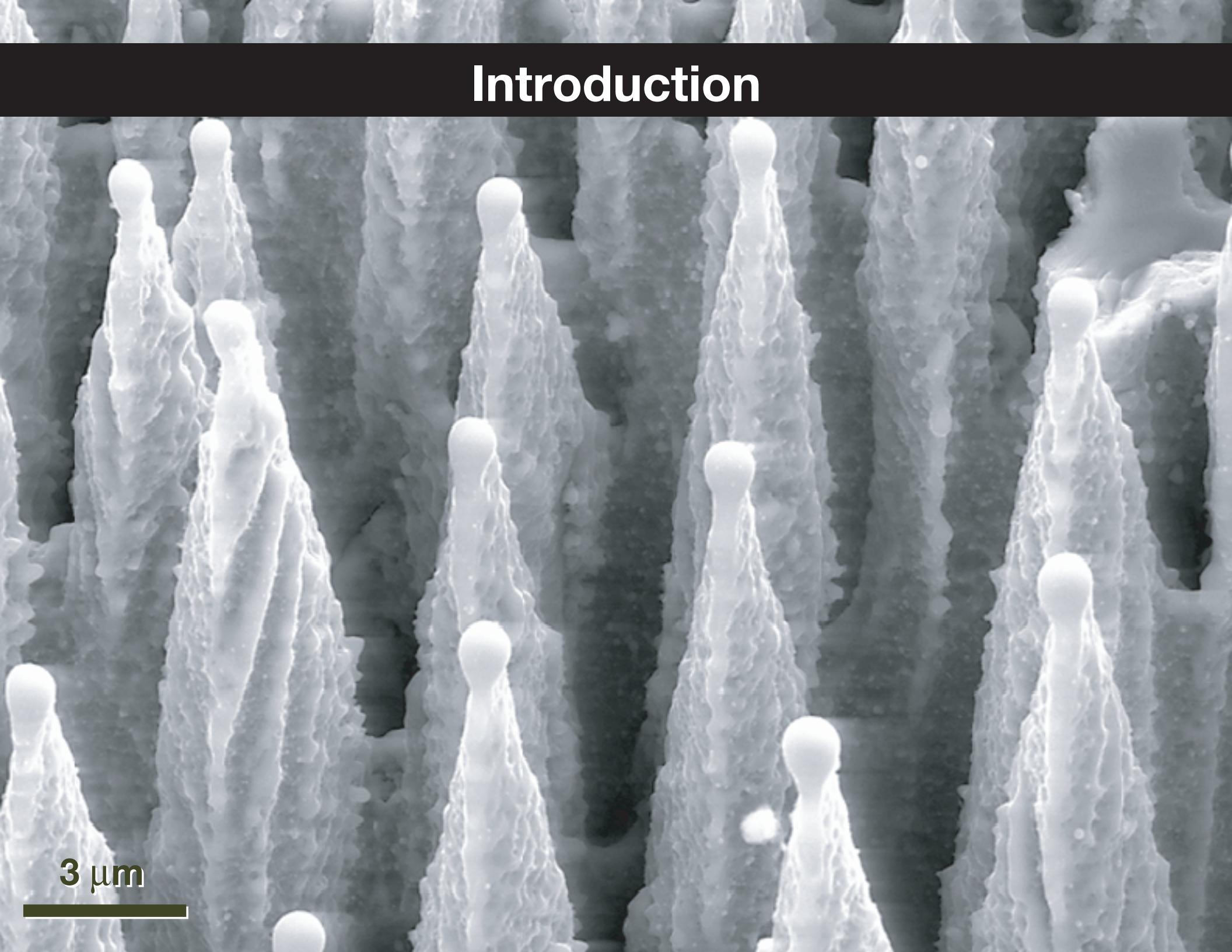
# Introduction



**"black silicon"**



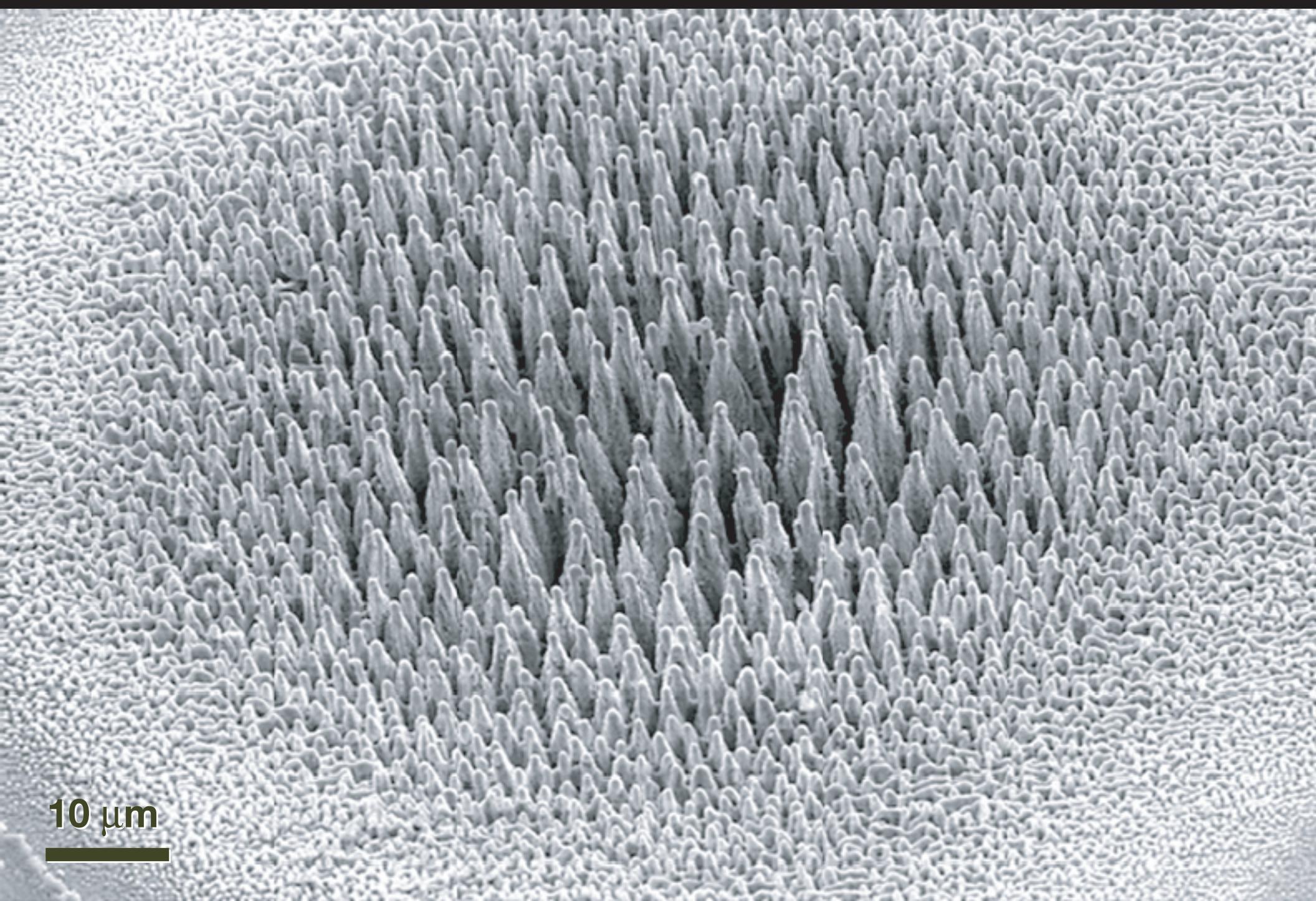
# Introduction



3  $\mu\text{m}$

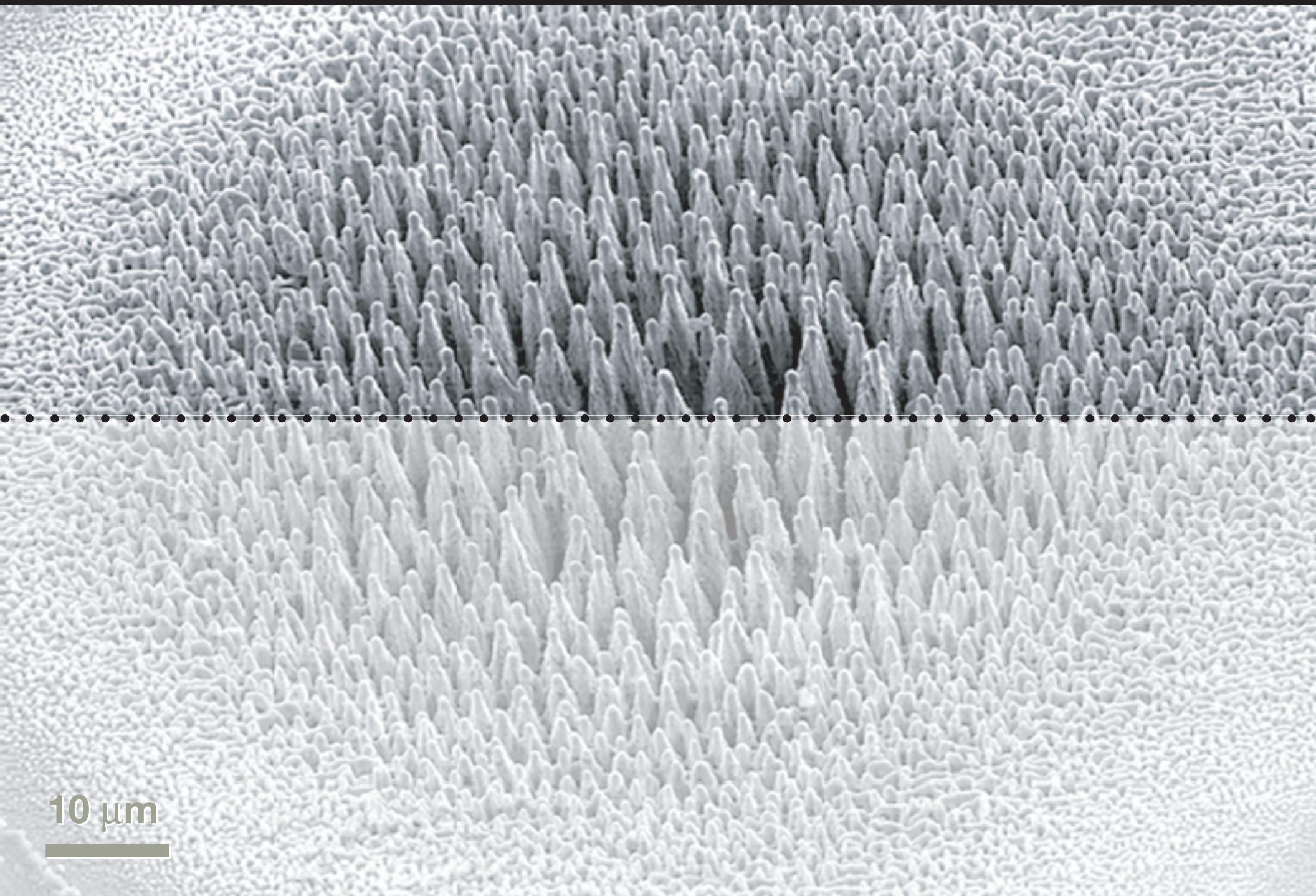


# Introduction

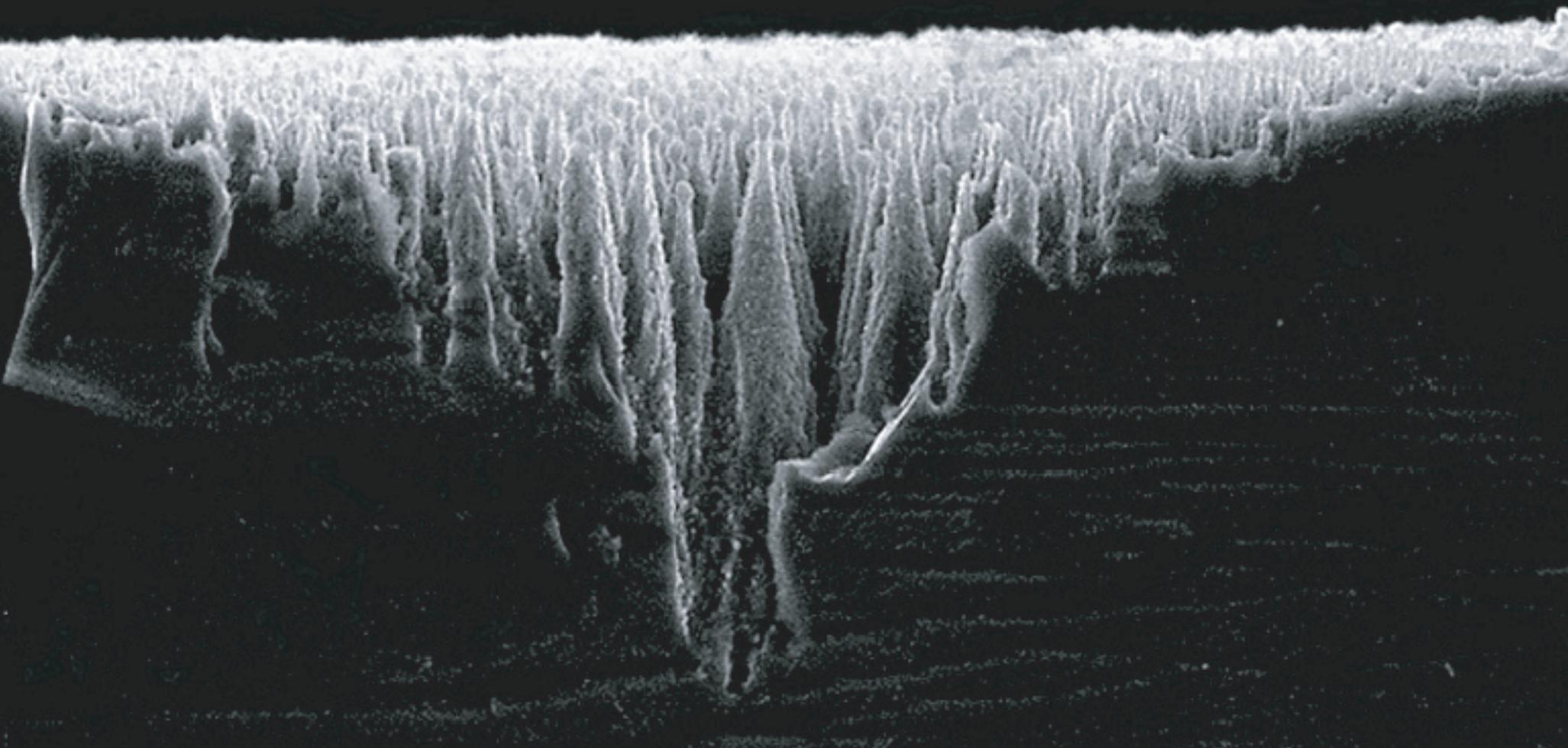


10  $\mu\text{m}$

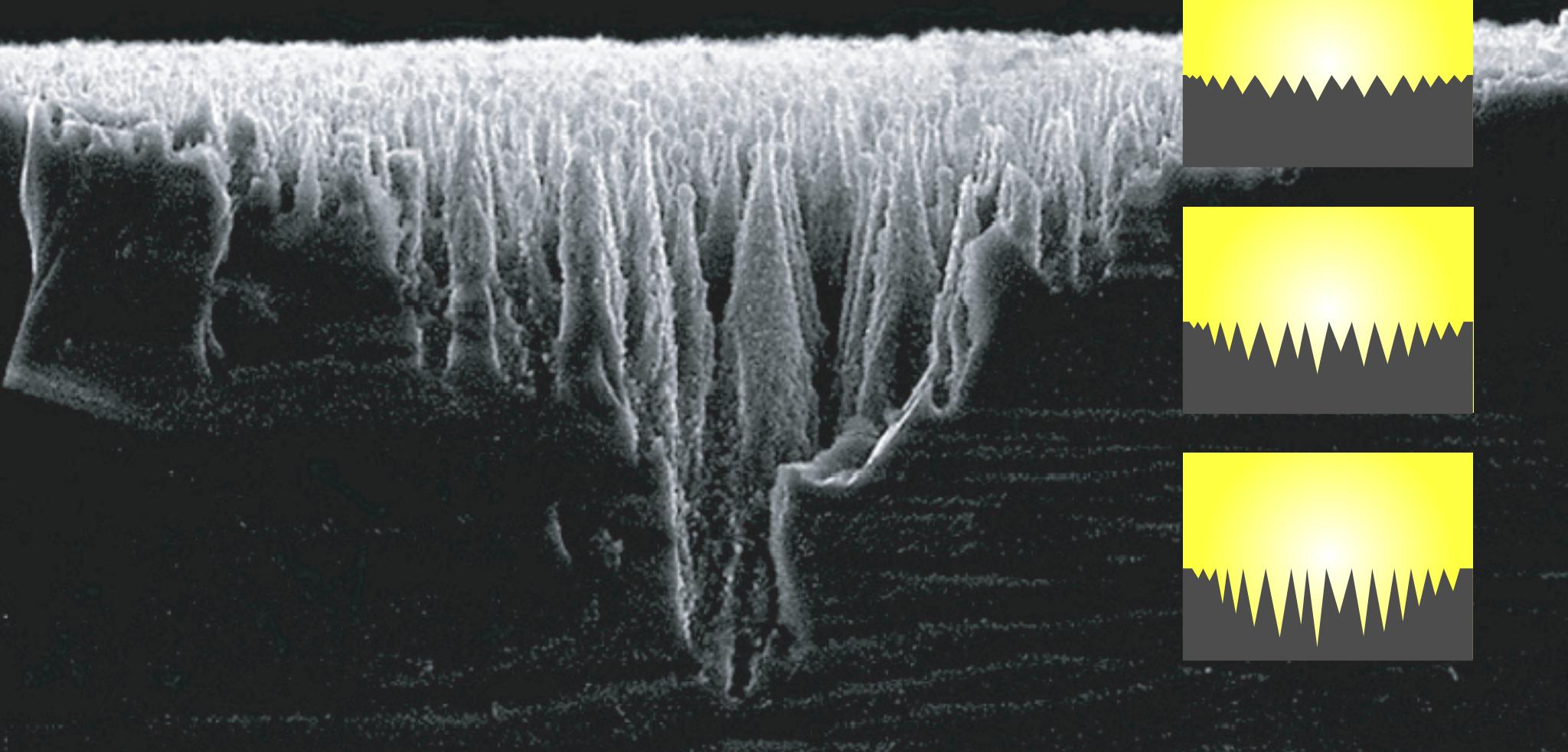
# Introduction



# Introduction



# Introduction



# Introduction

- **maskless etching process**
- **self-organized, conical microstructures**
- **highly light absorbing**

# Outline

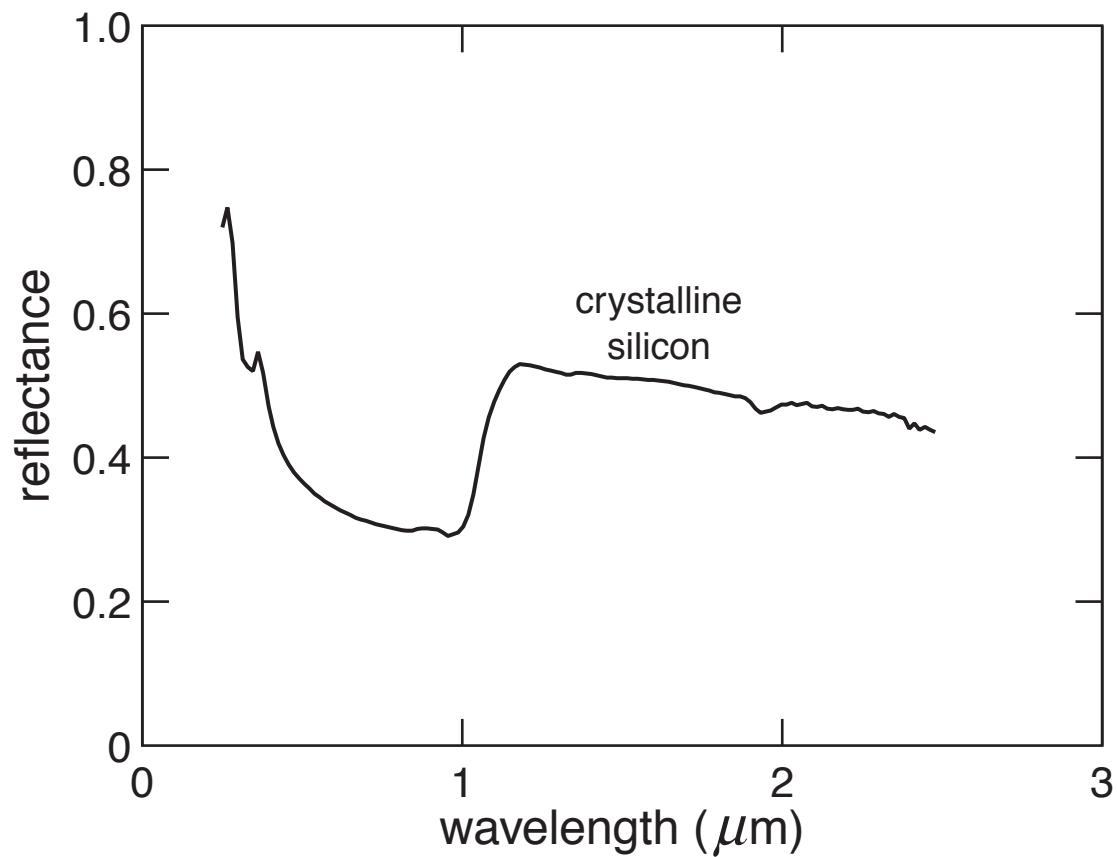
- optical properties
- structural and chemical analysis
- photodetectors
  - the *p-n* junction
  - femtosecond-laser microstructured silicon photodiodes
- outlook

# Outline

- optical properties
- structural and chemical analysis
- photodetectors
  - the *p-n* junction
  - femtosecond-laser microstructured silicon photodiodes
- outlook

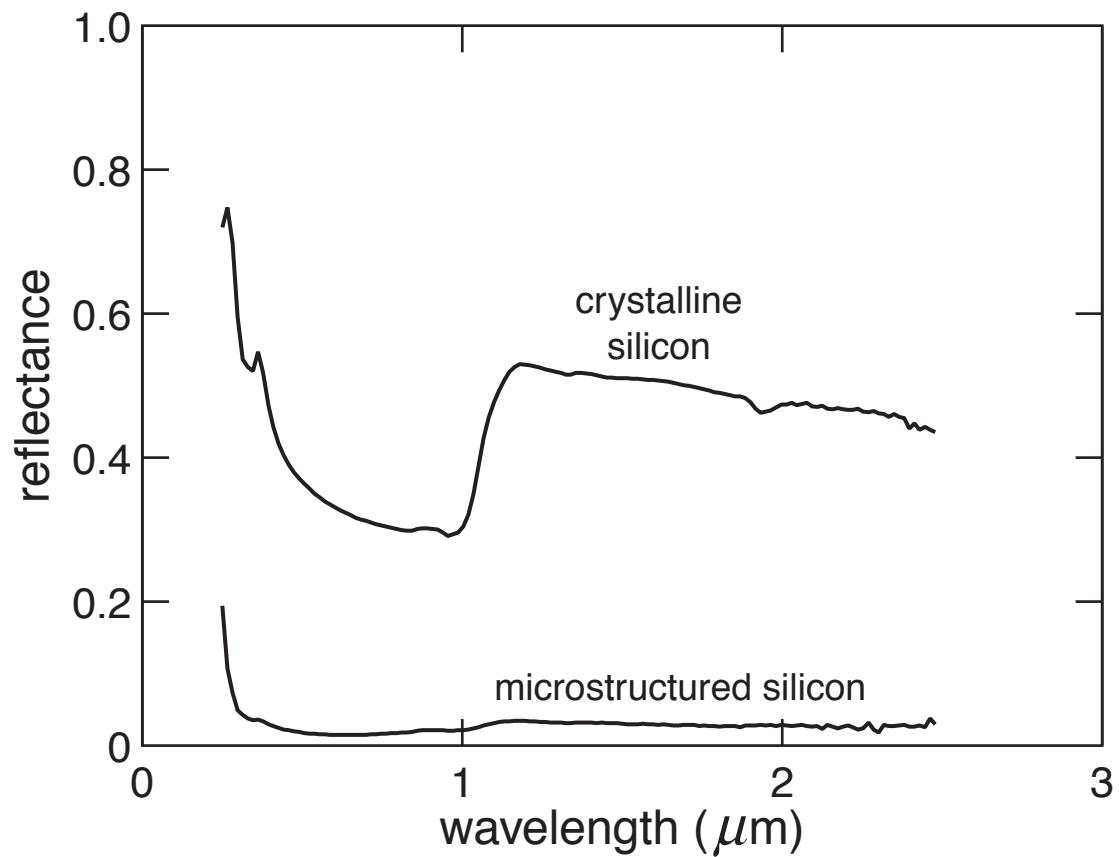
# Optical properties

reflectance (integrating sphere)



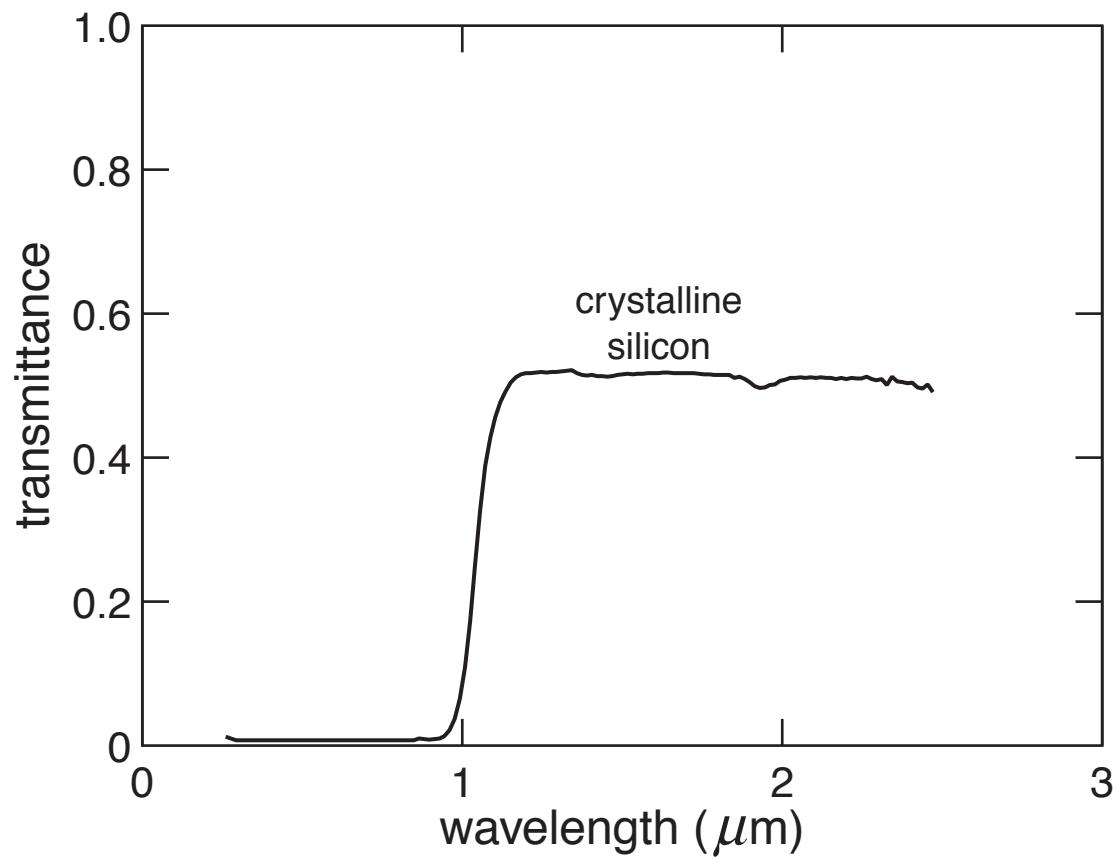
# Optical properties

## reflectance (integrating sphere)



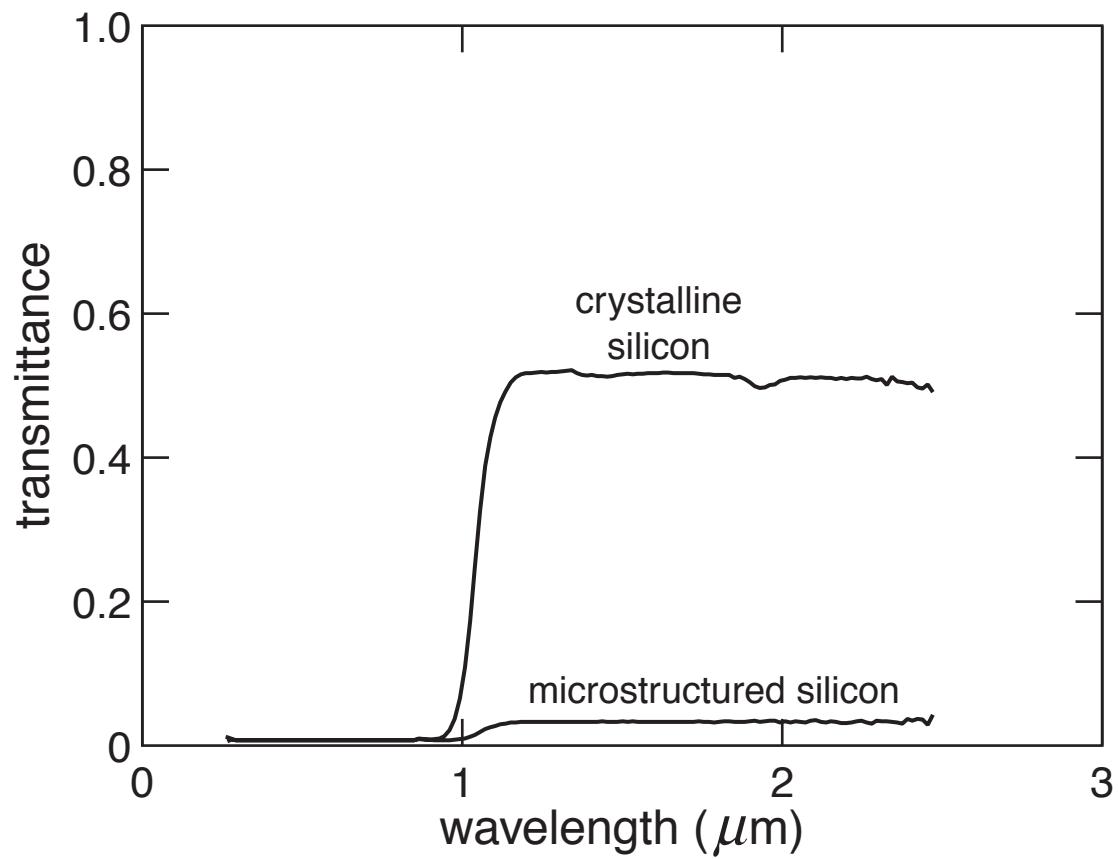
# Optical properties

transmittance (integrating sphere)



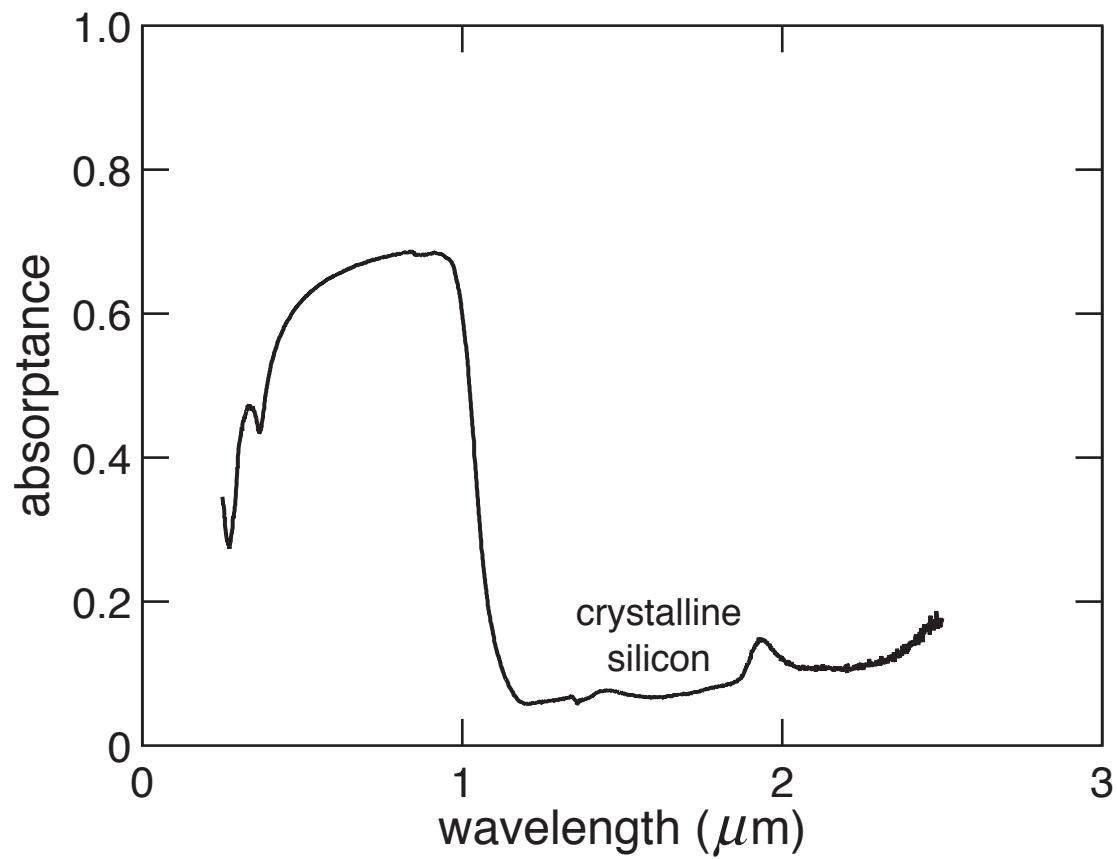
# Optical properties

## transmittance (integrating sphere)



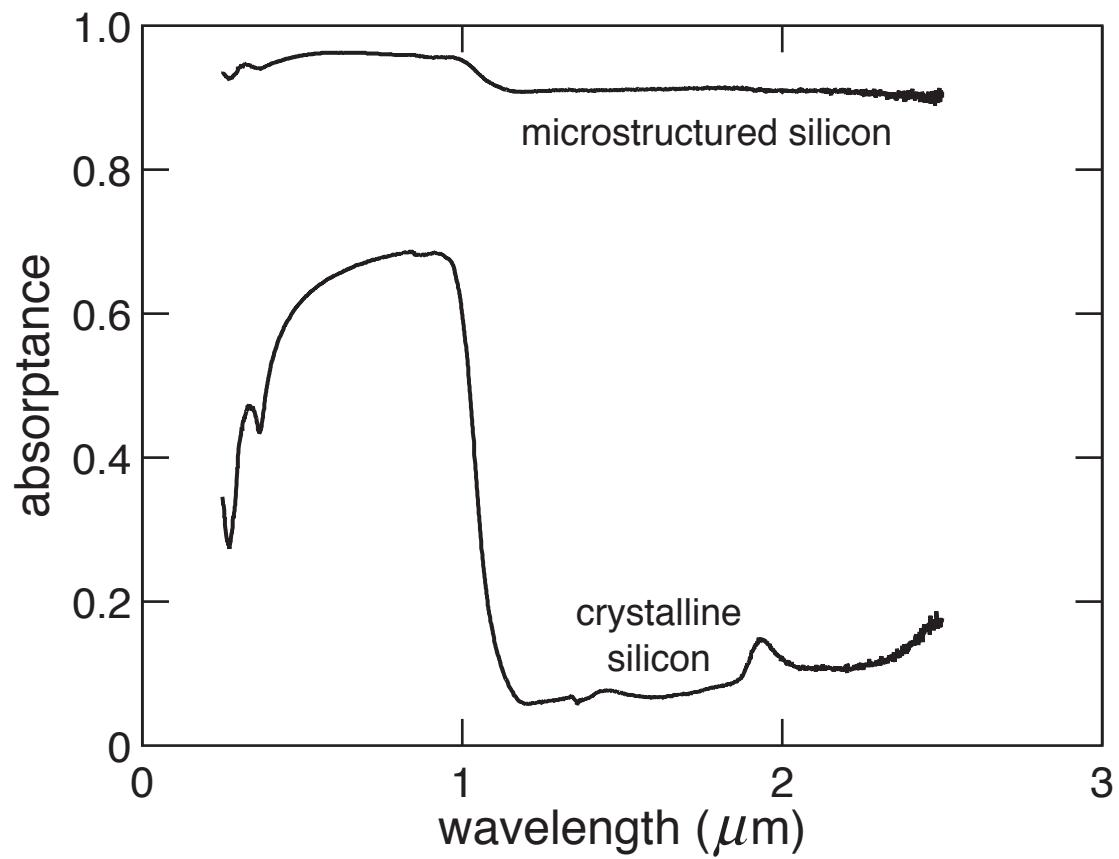
# Optical properties

absorptance ( $1 - R - T$ )



# Optical properties

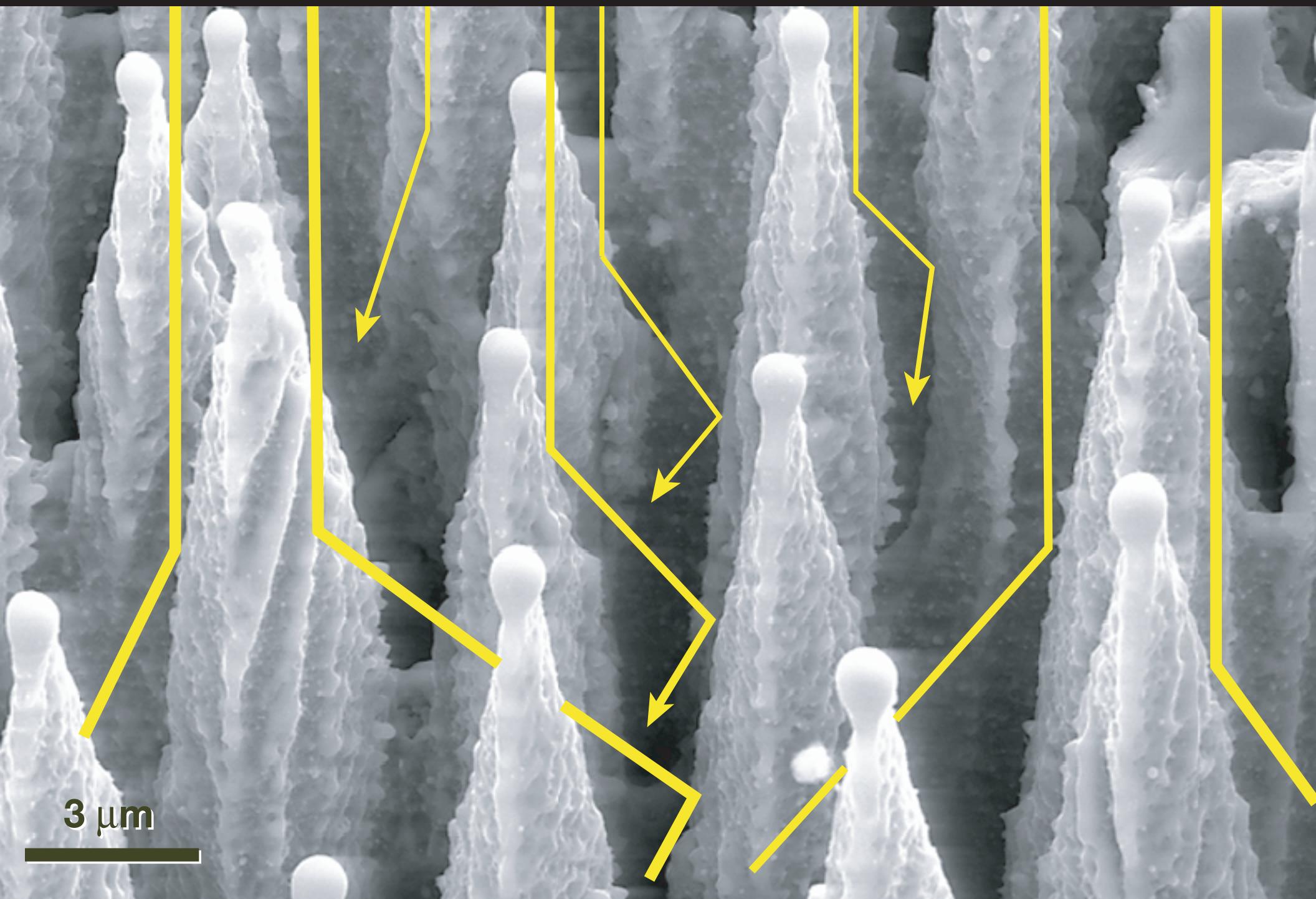
absorptance ( $1 - R - T$ )



# Optical properties

**What causes the near-unity absorptance?**

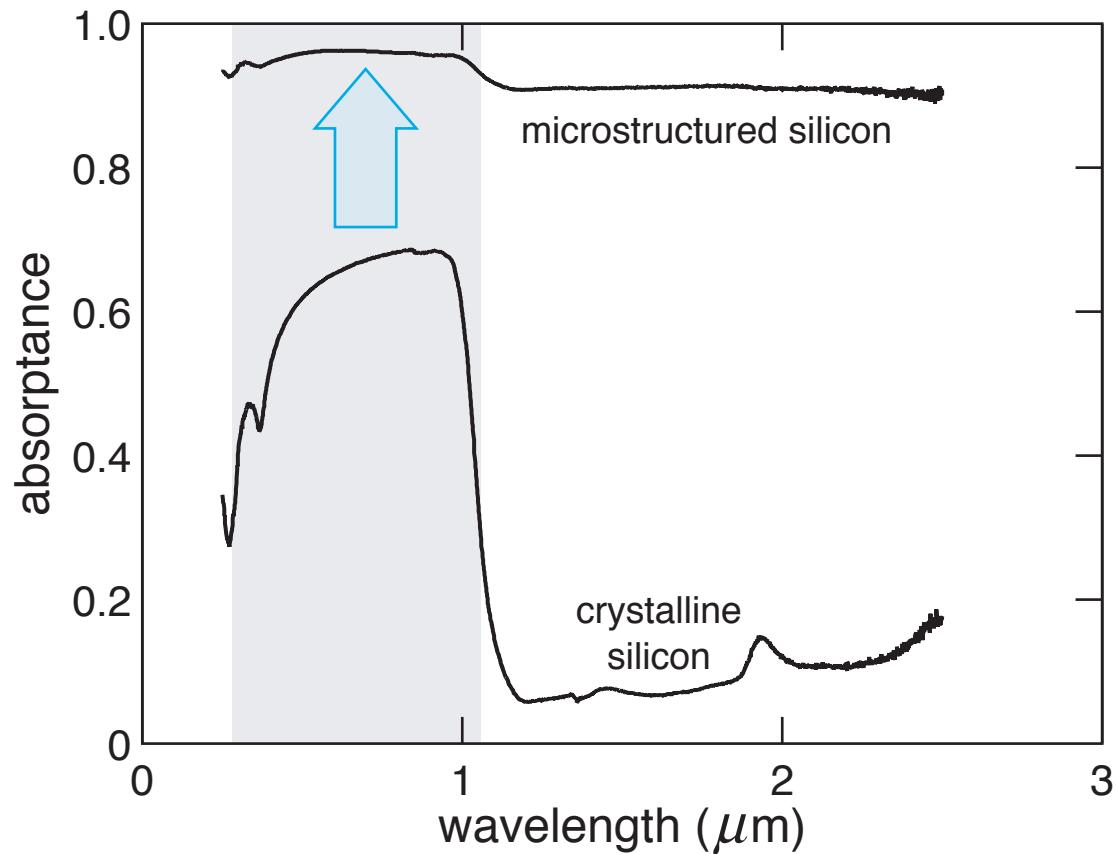
# Optical properties



3  $\mu\text{m}$

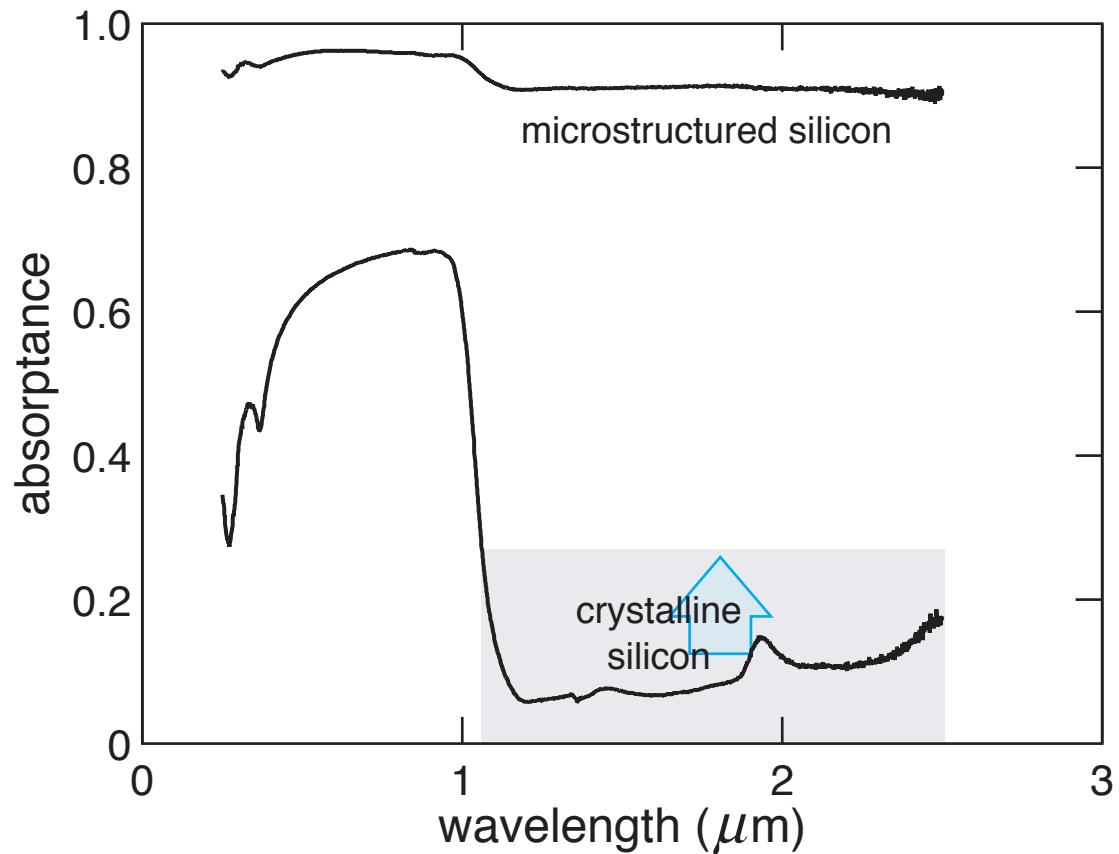
# Optical properties

multiple reflections enhance absorption



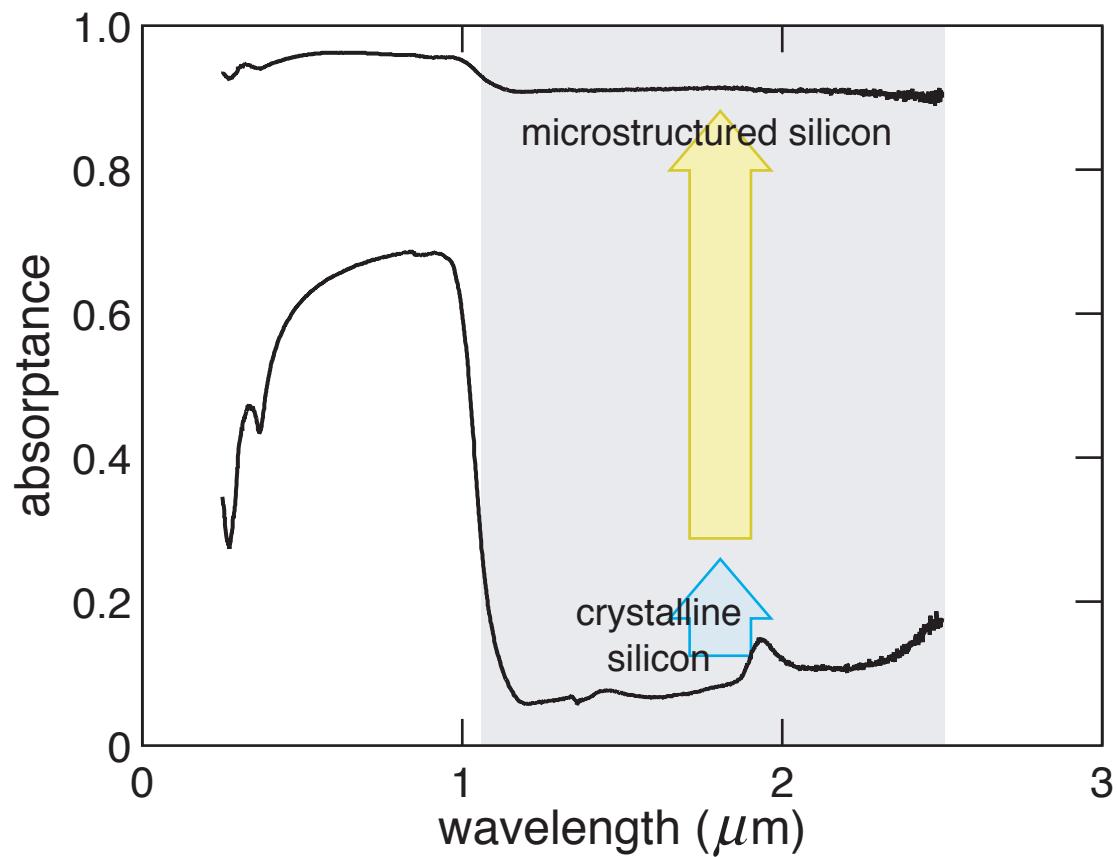
# Optical properties

multiple reflections enhance absorption



# Optical properties

## electronic band structure changes



# Optical properties

- **enhanced absorption in visible**
- **near-unity absorption in infrared**
- **modified electronic band structure**

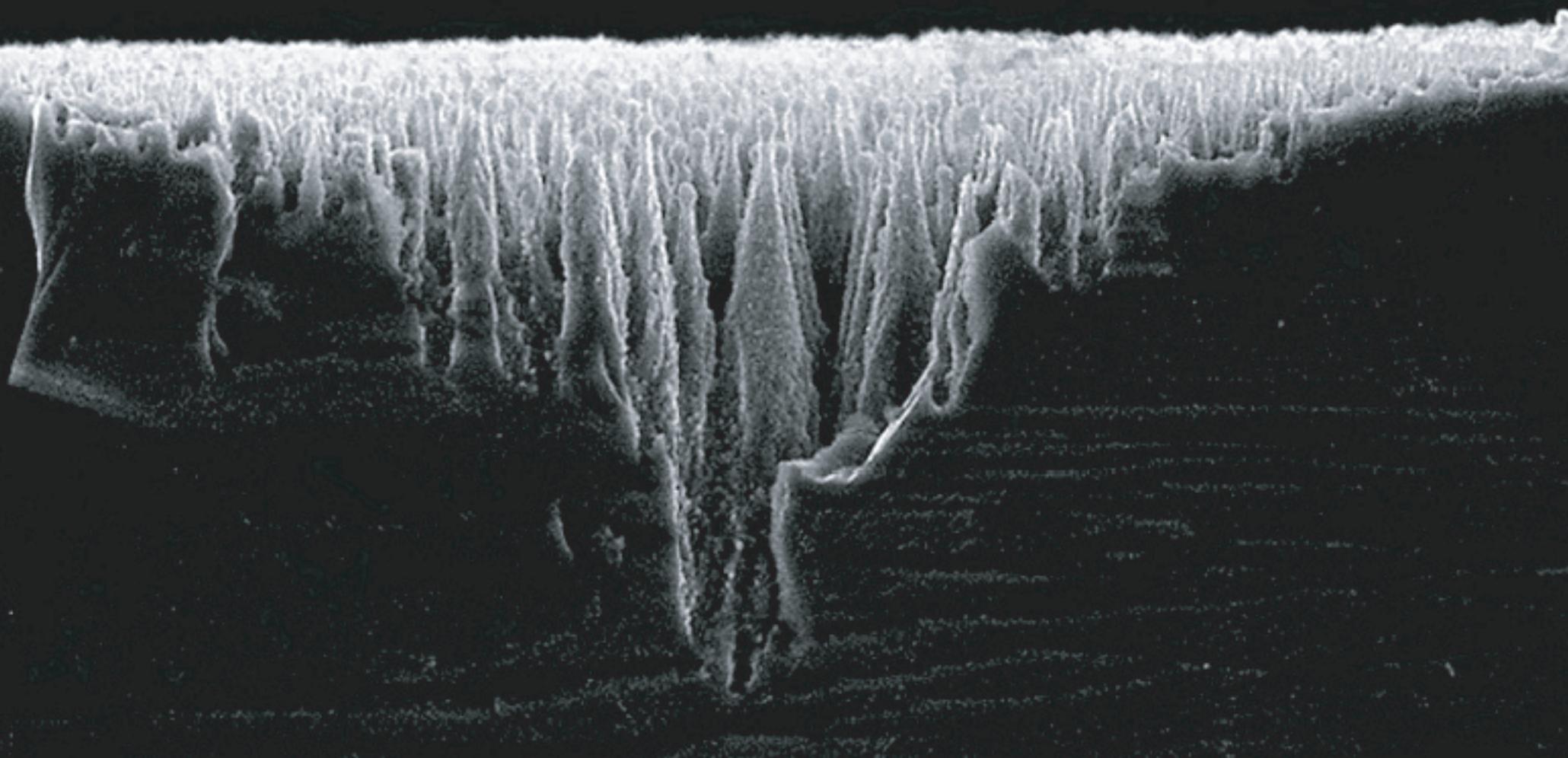
# Outline

- optical properties
- structural and chemical analysis
- photodetectors
  - the *p-n* junction
  - femtosecond-laser microstructured silicon photodiodes
- outlook

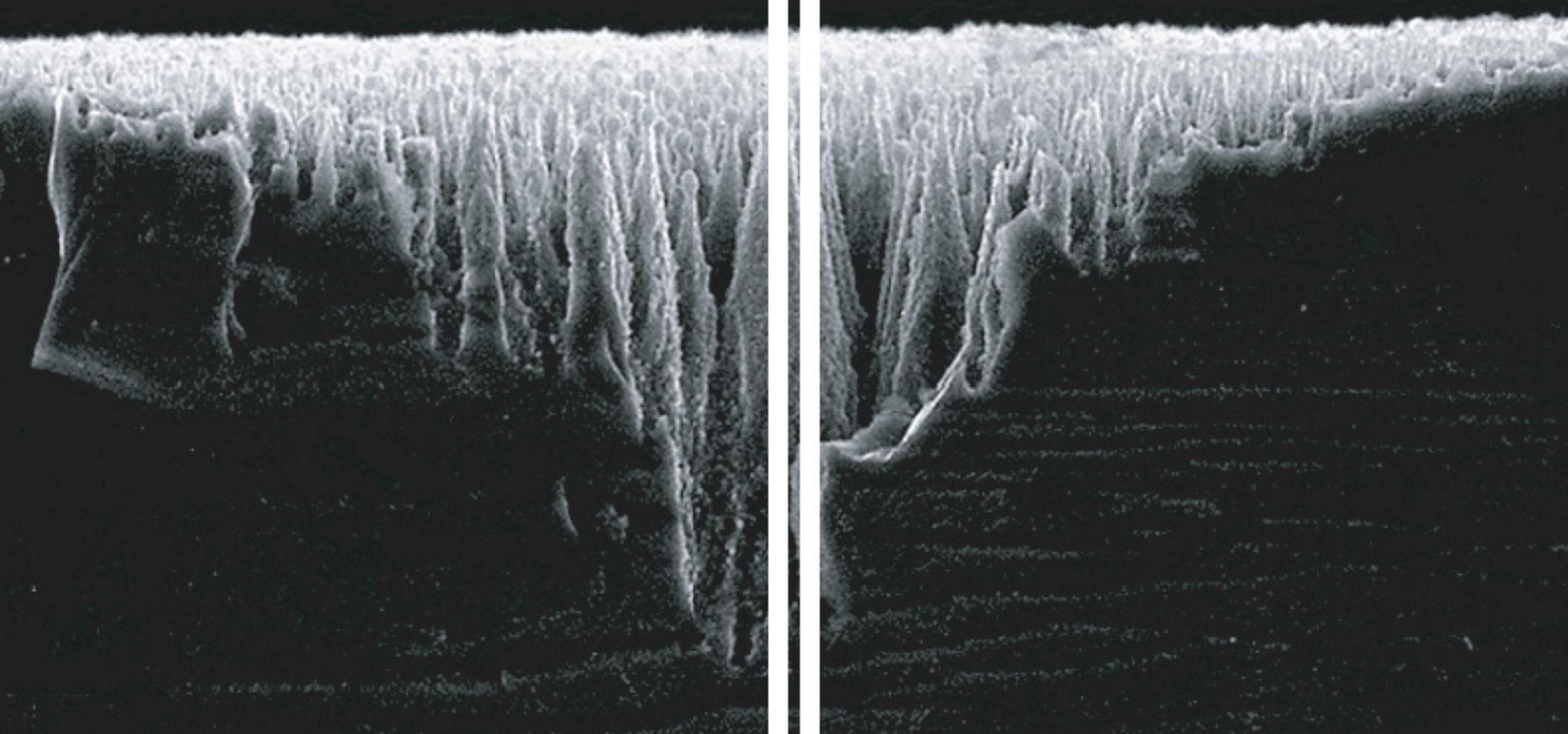
# Structural and chemical analysis

**Band structure changes: defects and/or impurities.**

# Structural and chemical analysis



# Structural and chemical analysis



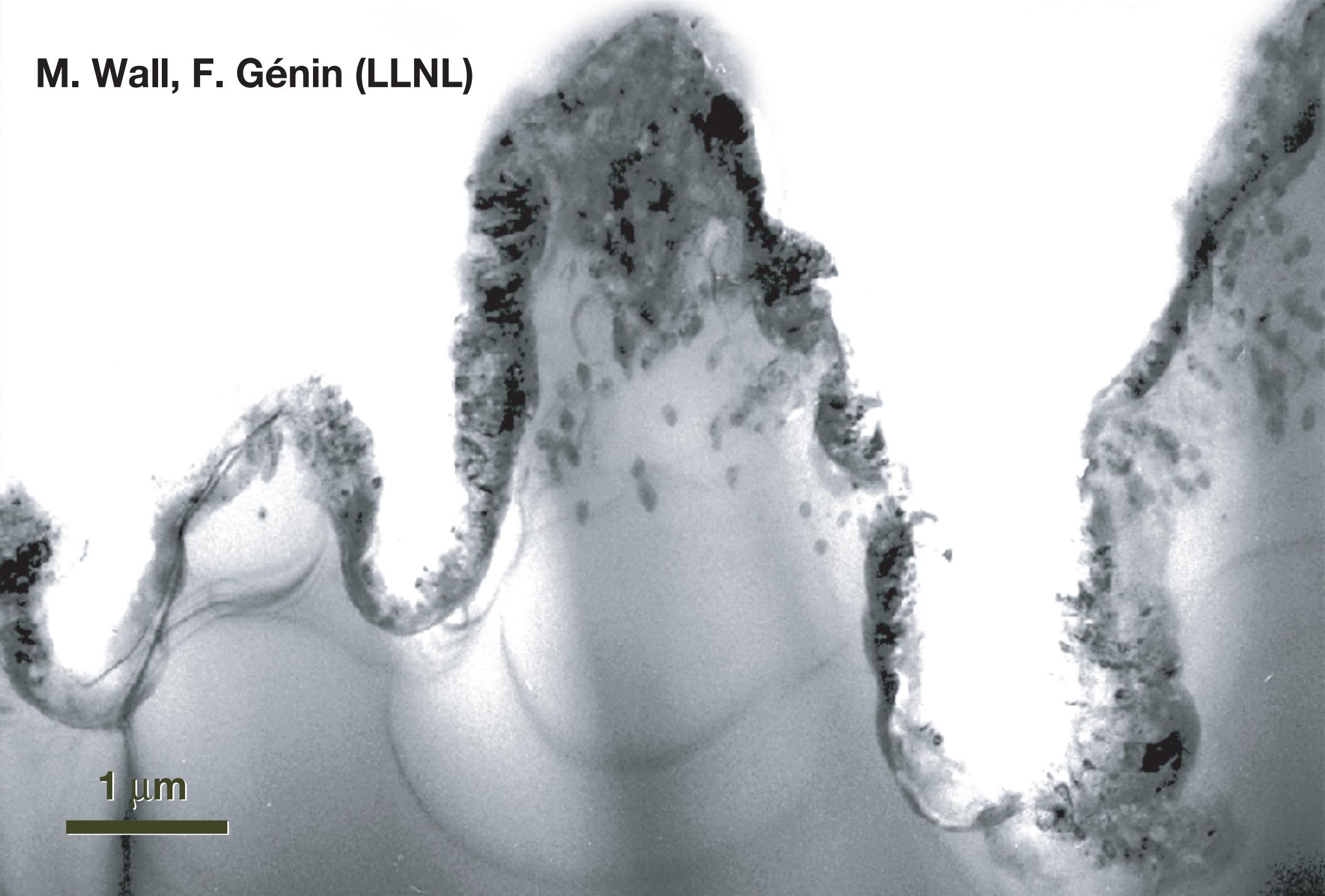
# Structural and chemical analysis

**cross-sectional  
Transmission Electron  
Microscopy**



# Structural and chemical analysis

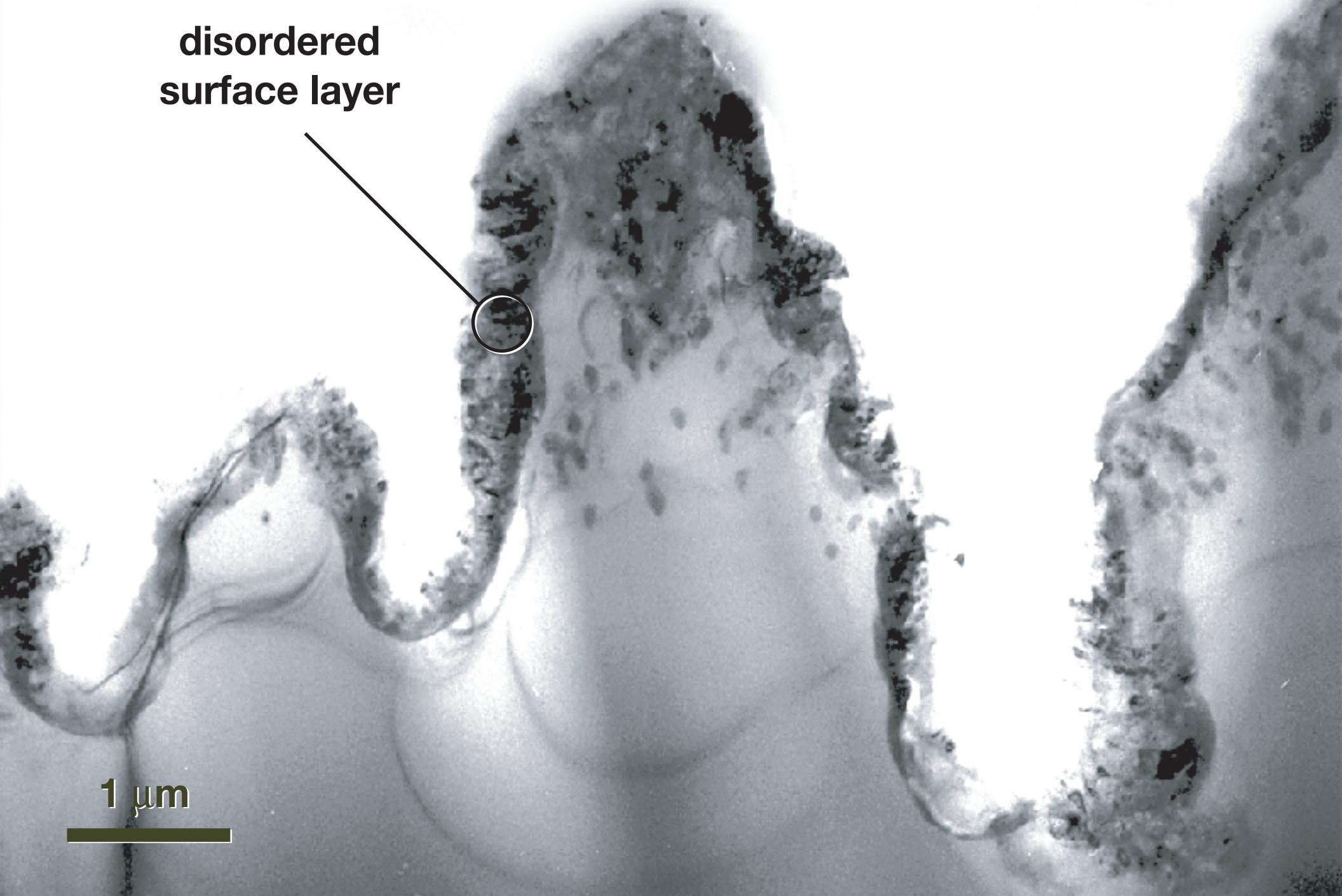
M. Wall, F. Génin (LLNL)



1  $\mu\text{m}$

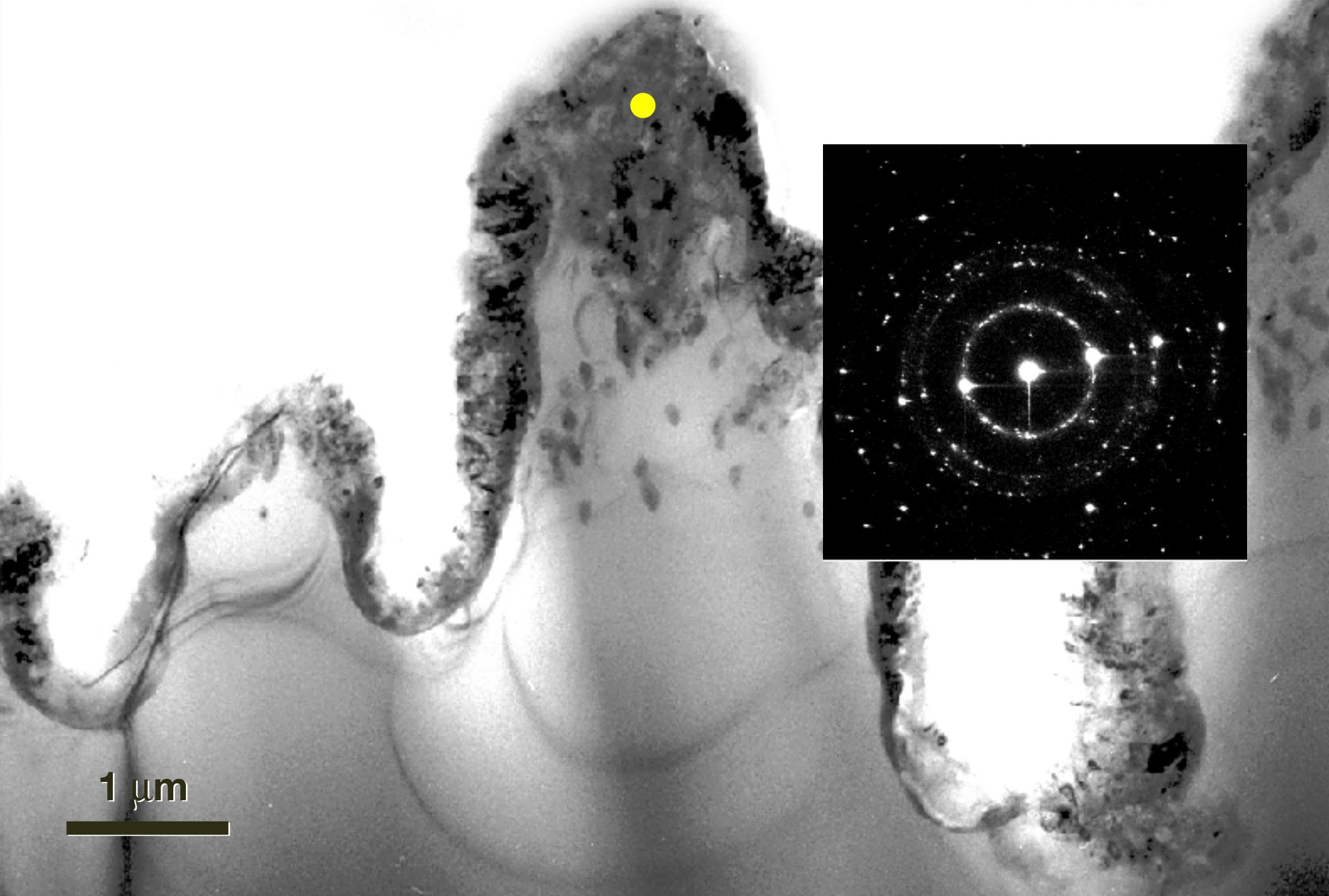
# Structural and chemical analysis

disordered  
surface layer

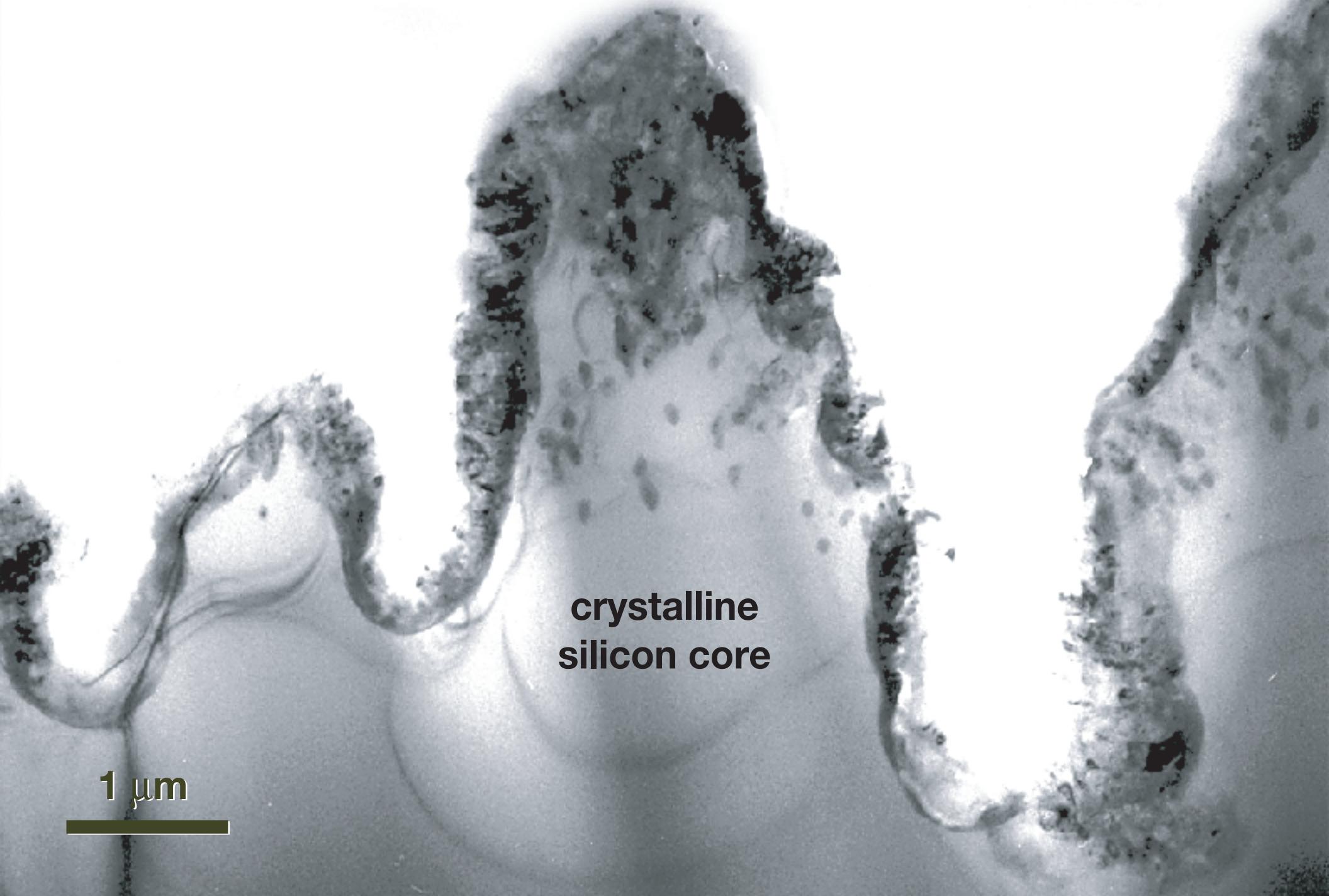


1  $\mu\text{m}$

# Structural and chemical analysis

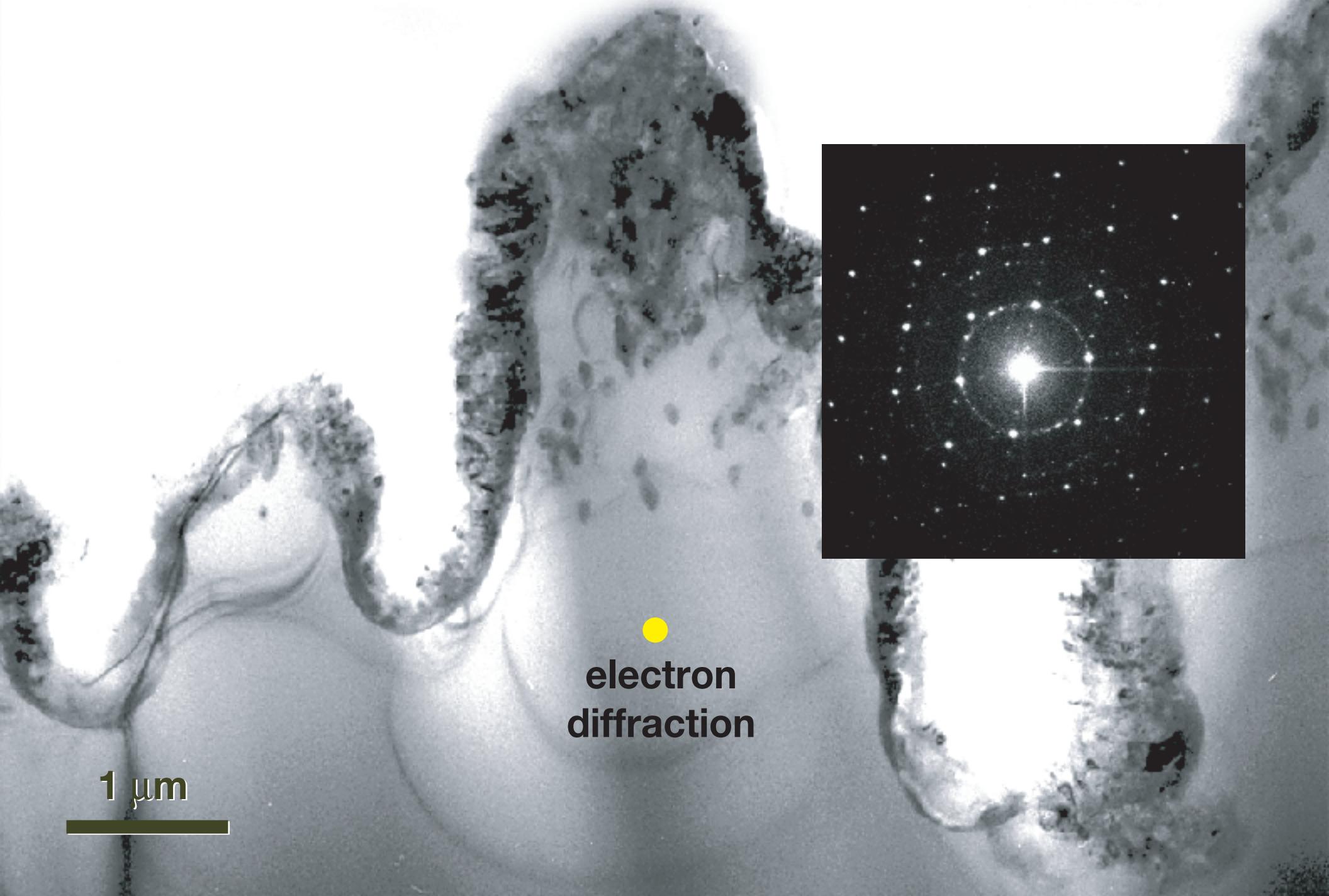


# Structural and chemical analysis



1  $\mu\text{m}$

# Structural and chemical analysis



1  $\mu\text{m}$

electron  
diffraction

# Structural and chemical analysis

- 300 nm disordered surface layer
- undisturbed crystalline below
- surface layer: polycrystalline Si with 1.6% sulfur

1  $\mu\text{m}$

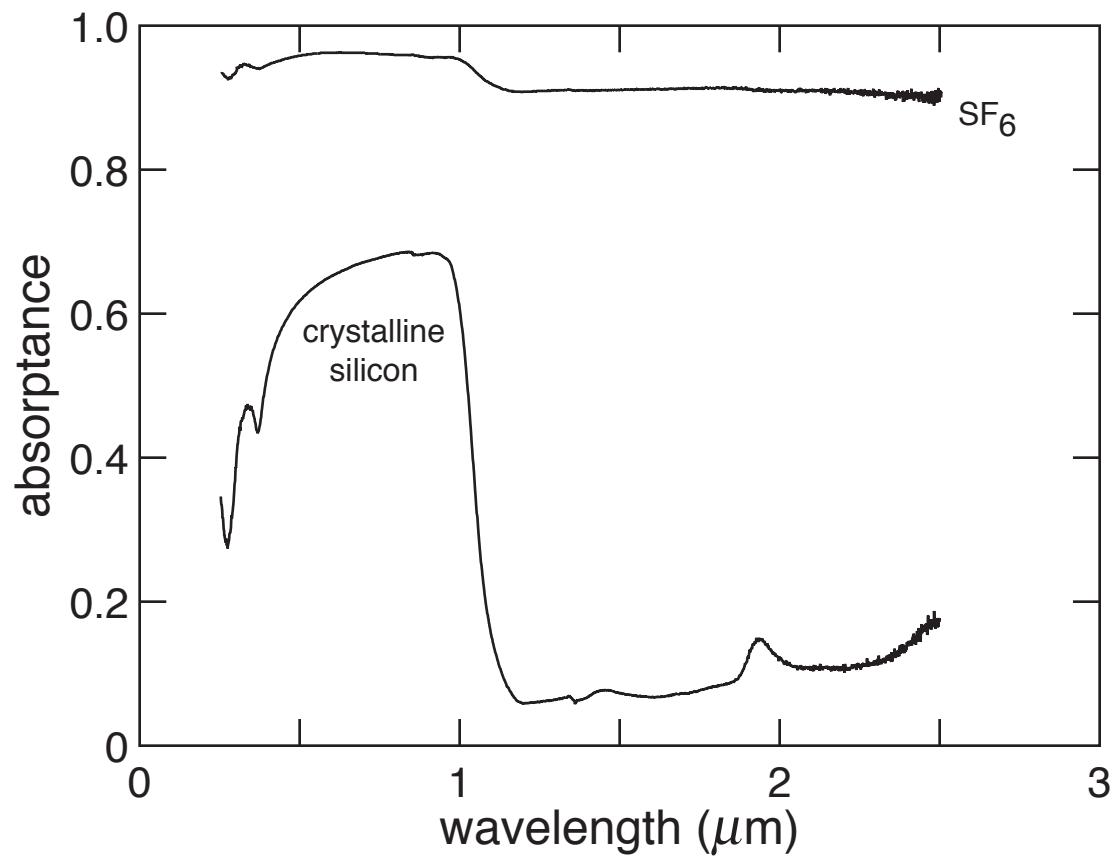
# Structural and chemical analysis

**Microstructure with different ambient gases:**

- **gas species incorporated into surface**
- **sulfur critical for below-band gap absorption**

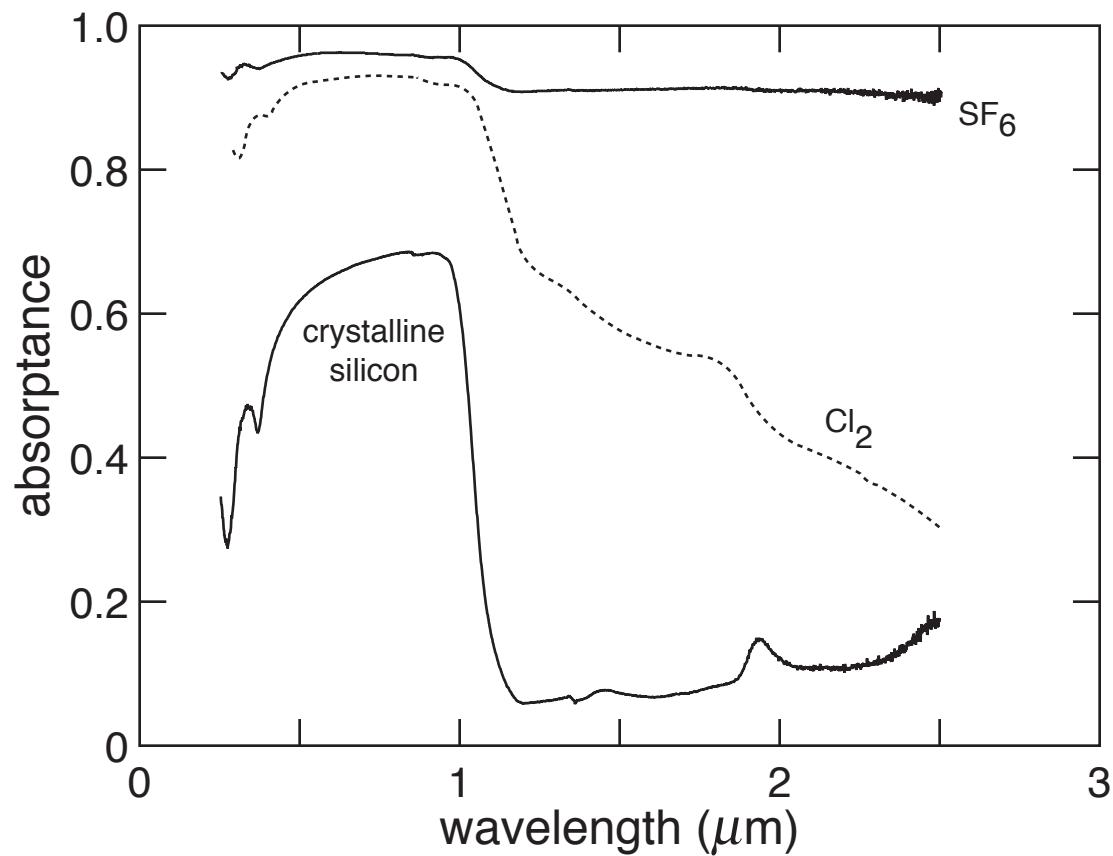
# Structural and chemical analysis

## microstructure with different gases



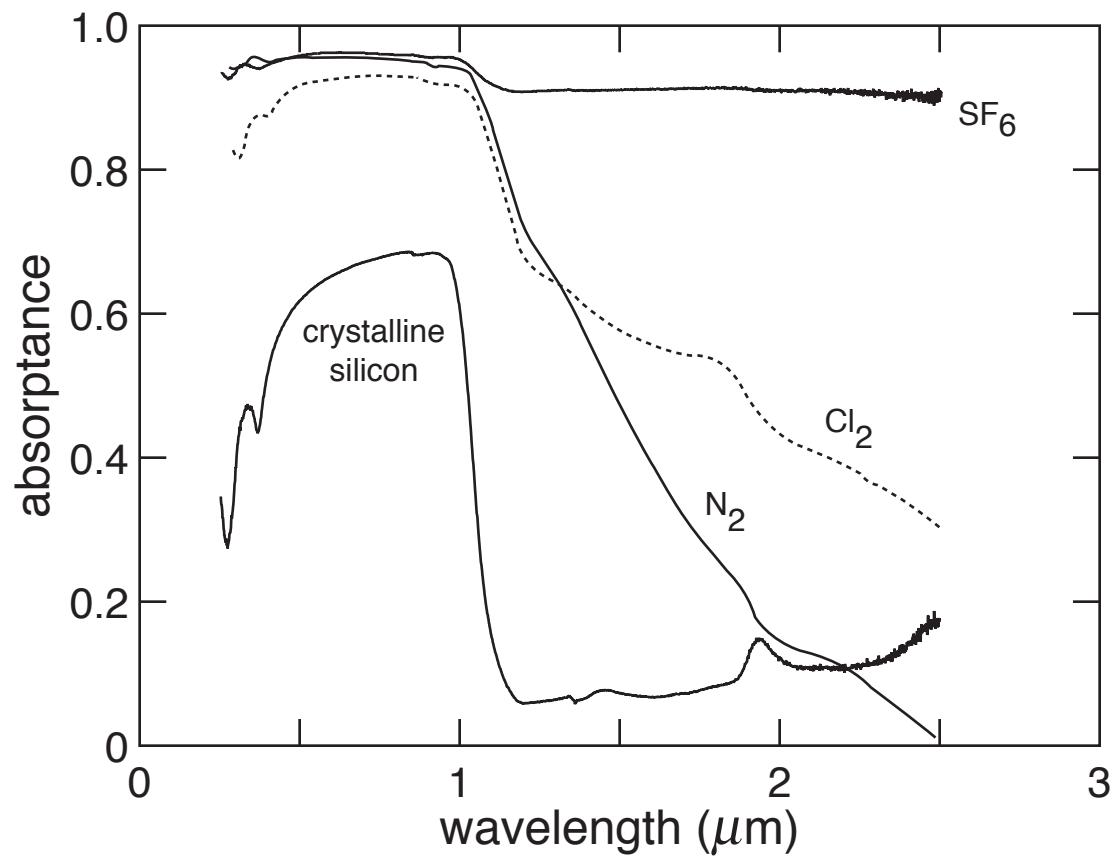
# Structural and chemical analysis

## microstructure with different gases



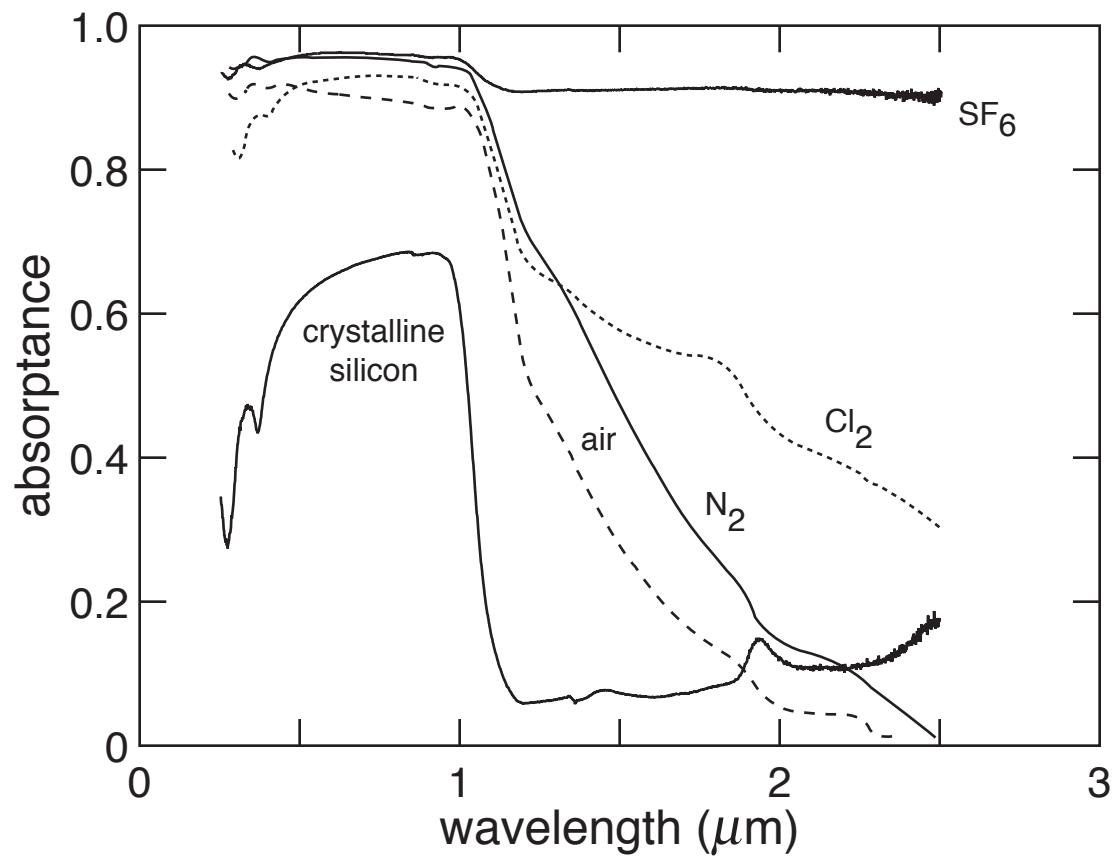
# Structural and chemical analysis

## microstructure with different gases



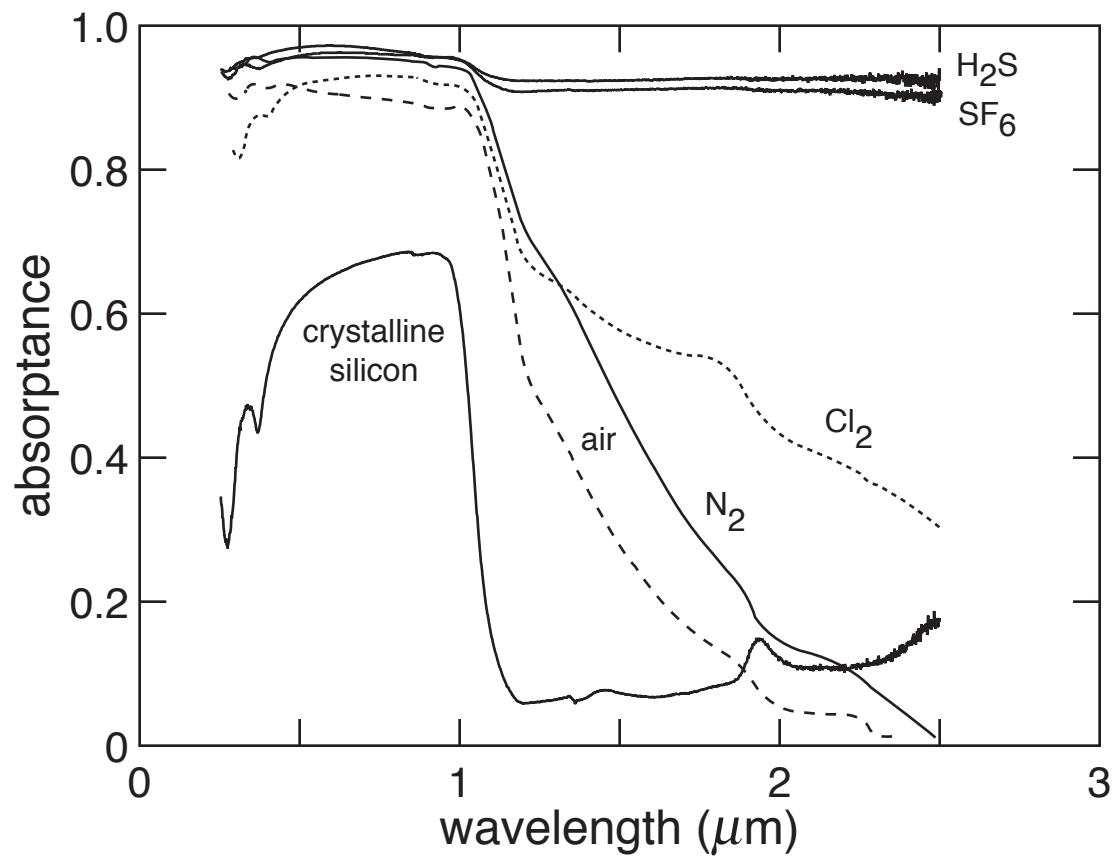
# Structural and chemical analysis

## microstructure with different gases



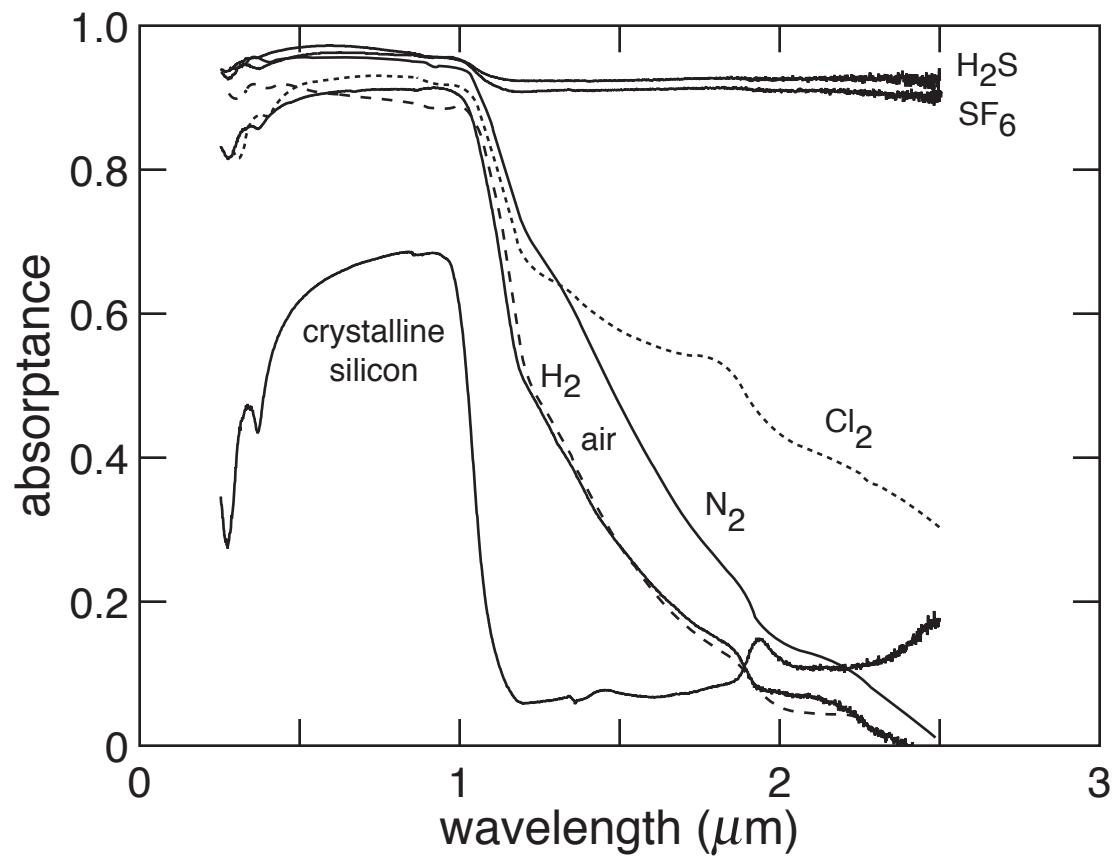
# Structural and chemical analysis

## microstructure with different gases



# Structural and chemical analysis

## microstructure with different gases



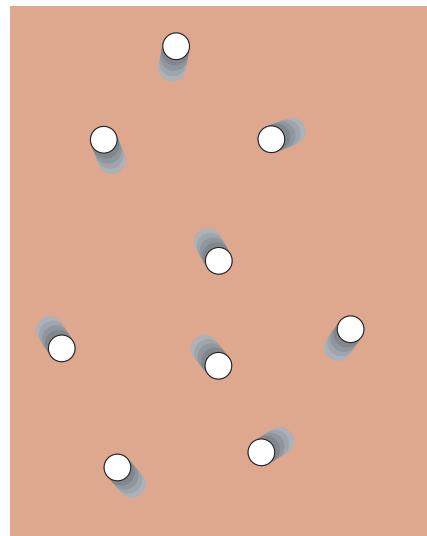
# Outline

- optical properties
- structural and chemical analysis
- photodetectors
  - the *p-n* junction
  - femtosecond-laser microstructured silicon photodiodes
- outlook

# Photodetectors

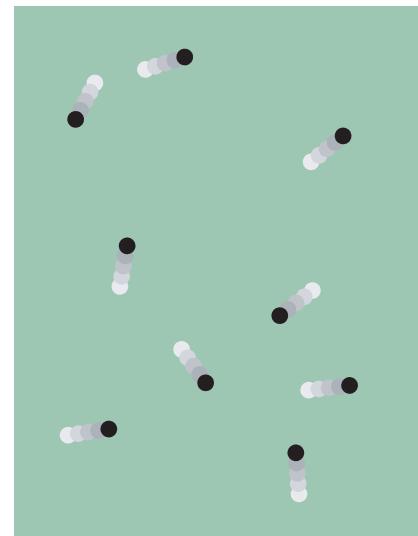
join acceptor and donor type Si...

neutral



*p*-type

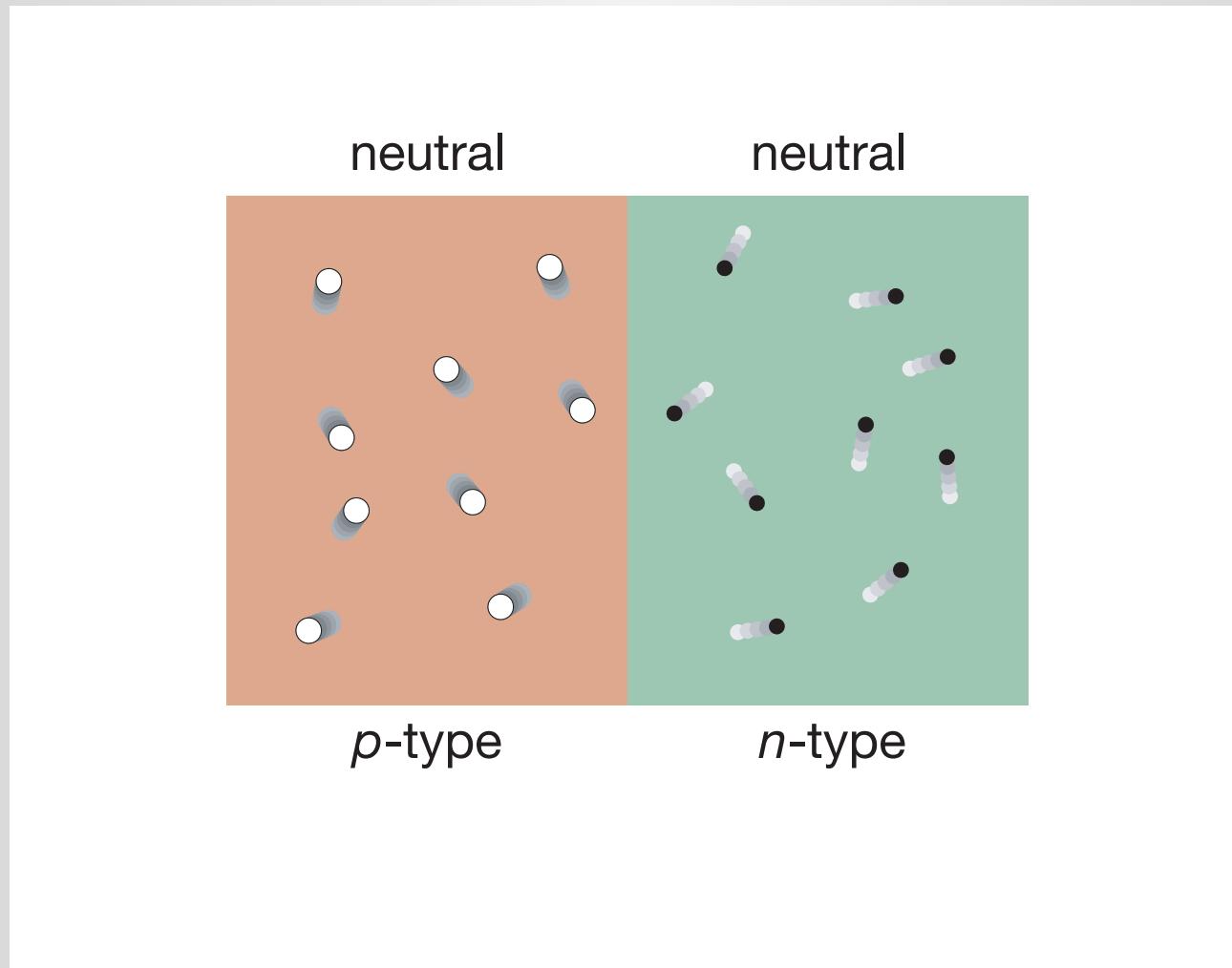
neutral



*n*-type

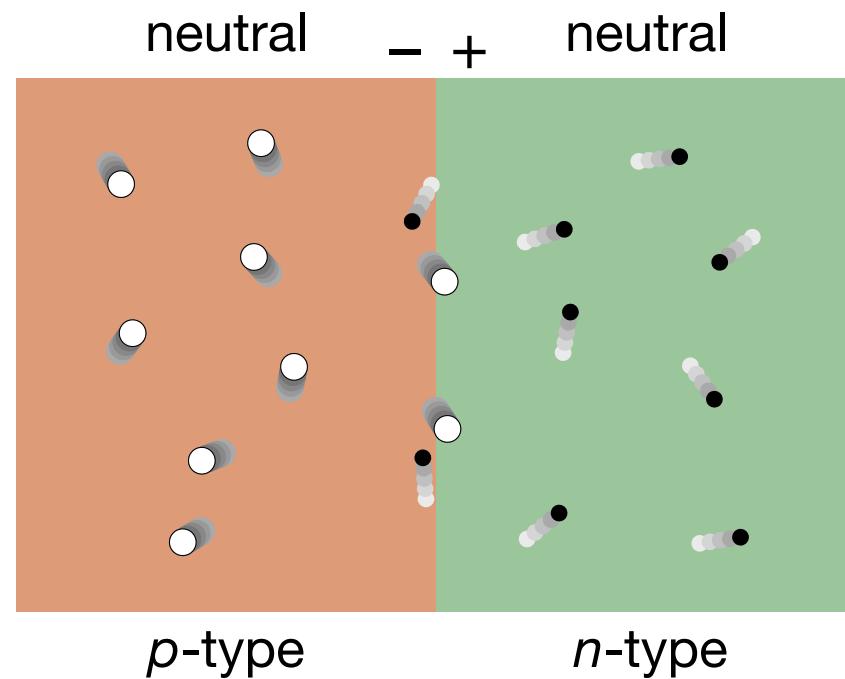
# Photodetectors

join acceptor and donor type Si...



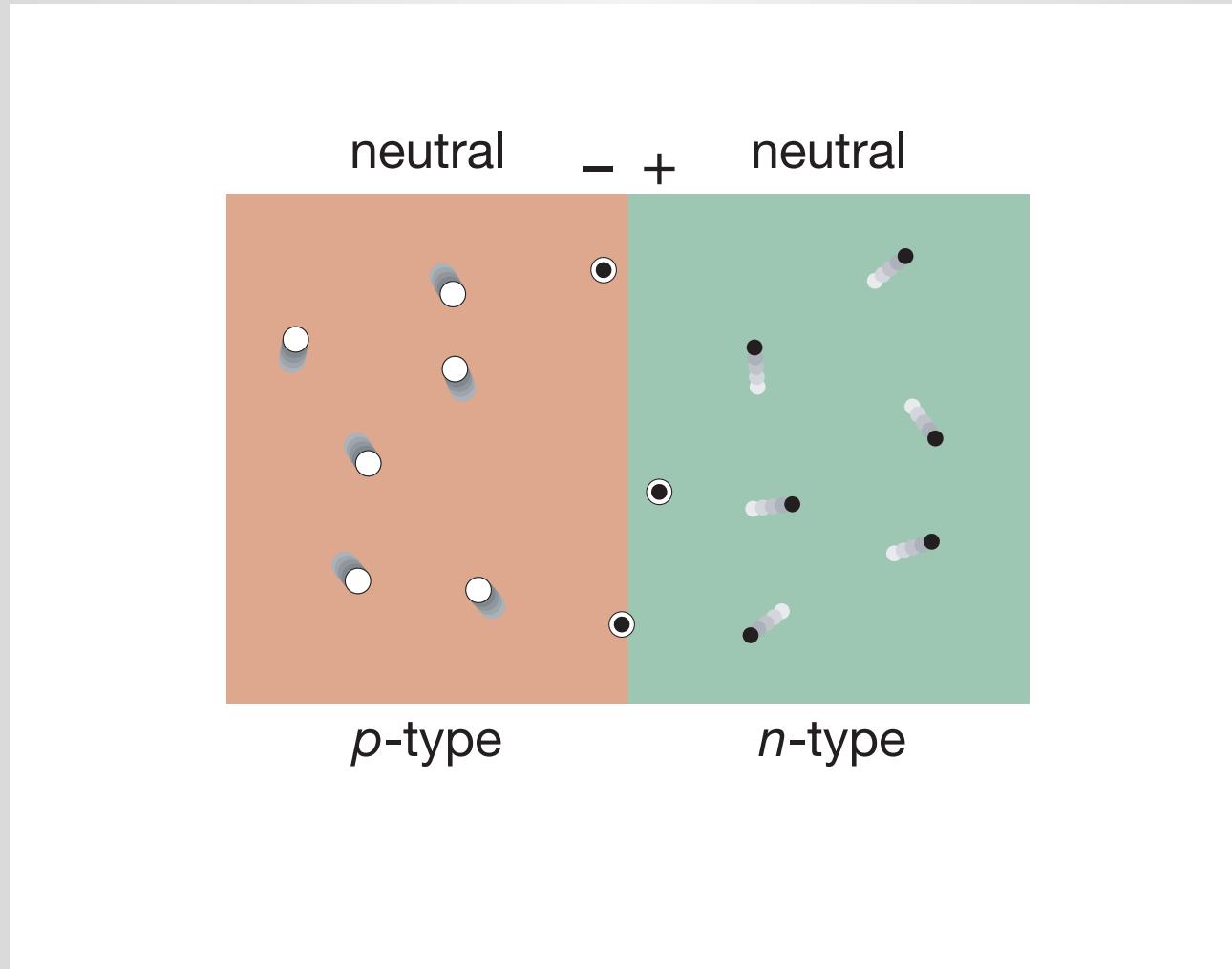
# Photodetectors

electrons and holes diffuse across junction...



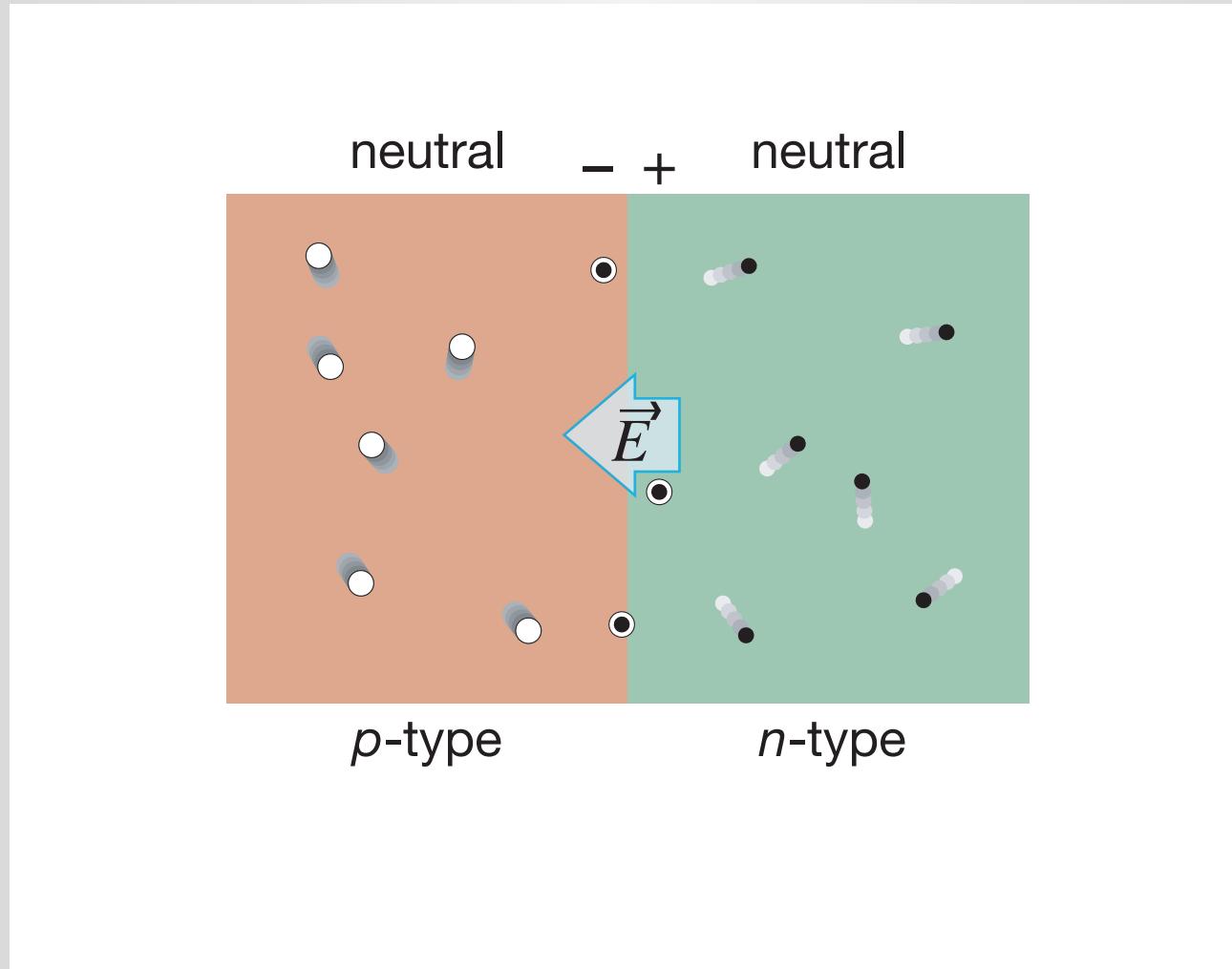
# Photodetectors

...and get 'trapped' after they combine



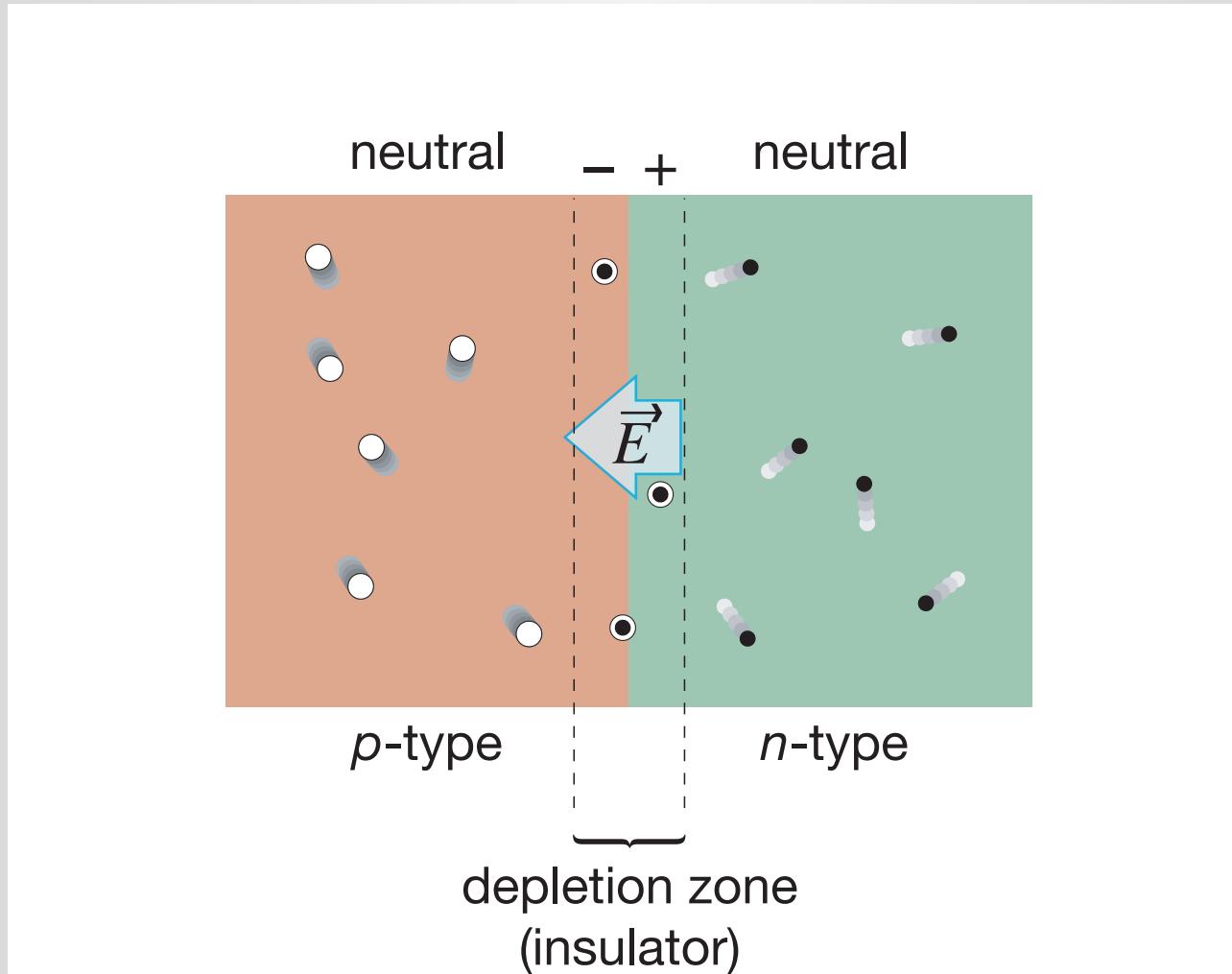
# Photodetectors

**build-up of charge leads to electric field that stops diffusion**



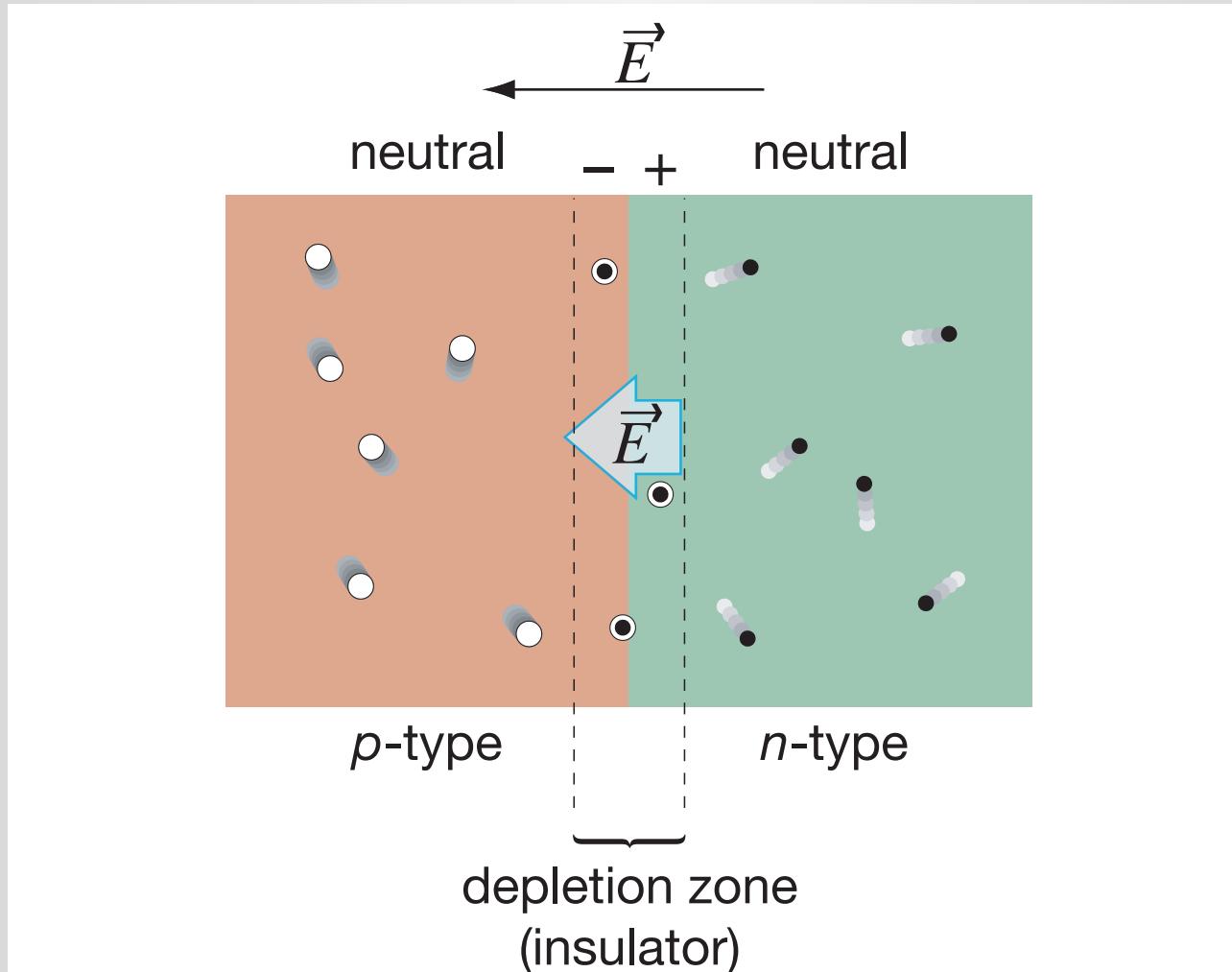
# Photodetectors

non-conducting layer at junction



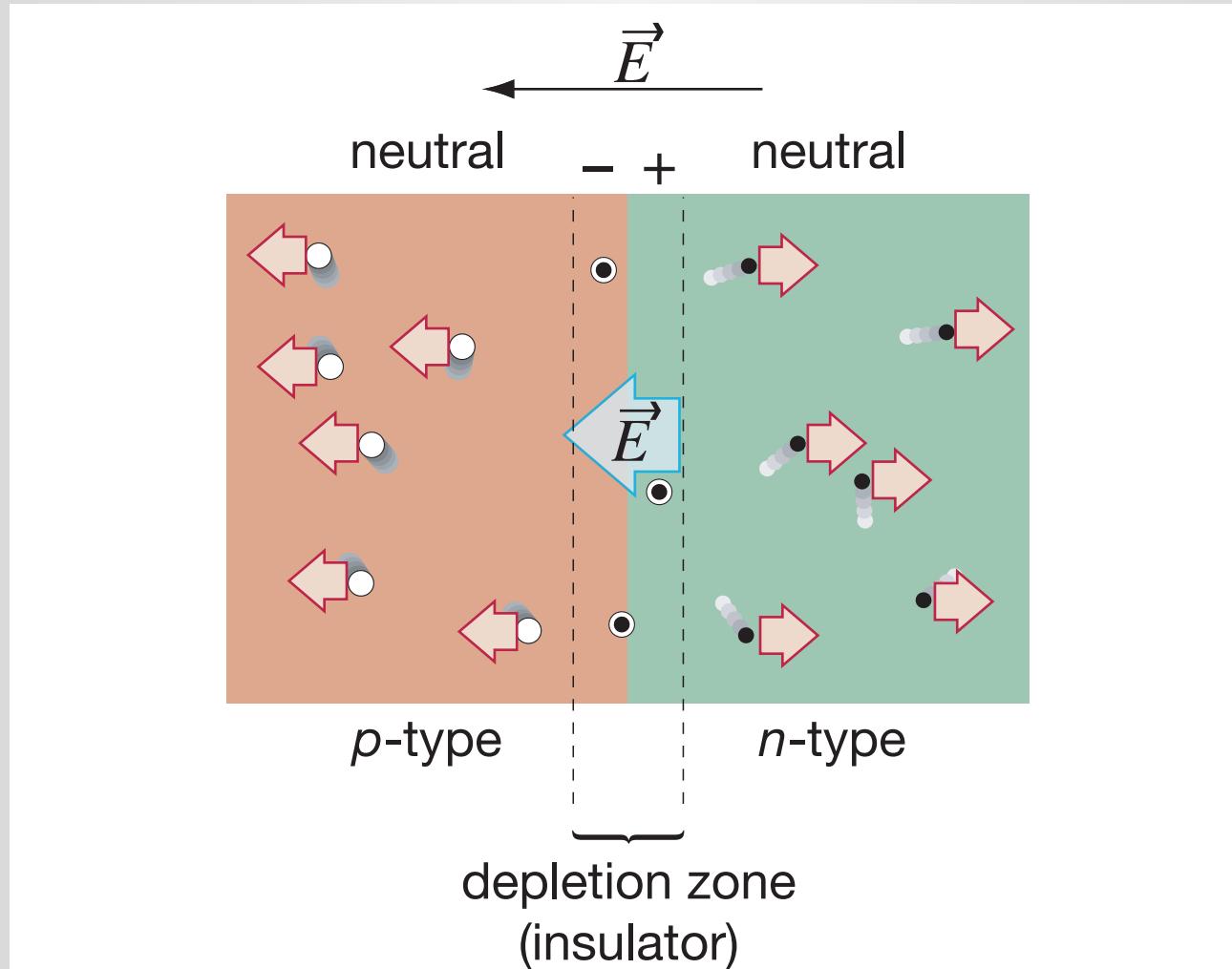
# Photodetectors

apply electric field...



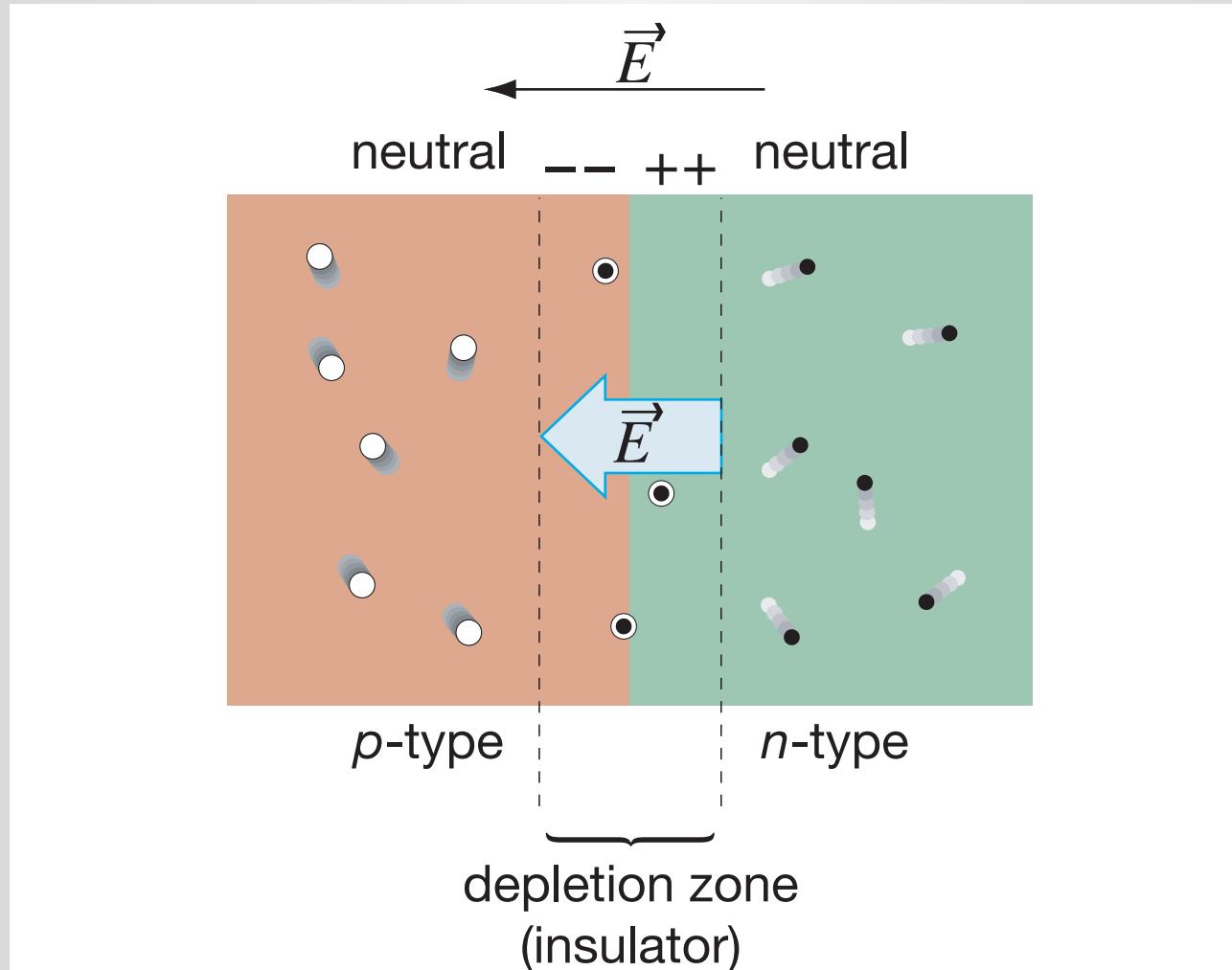
# Photodetectors

...holes pushed left, electrons to right...



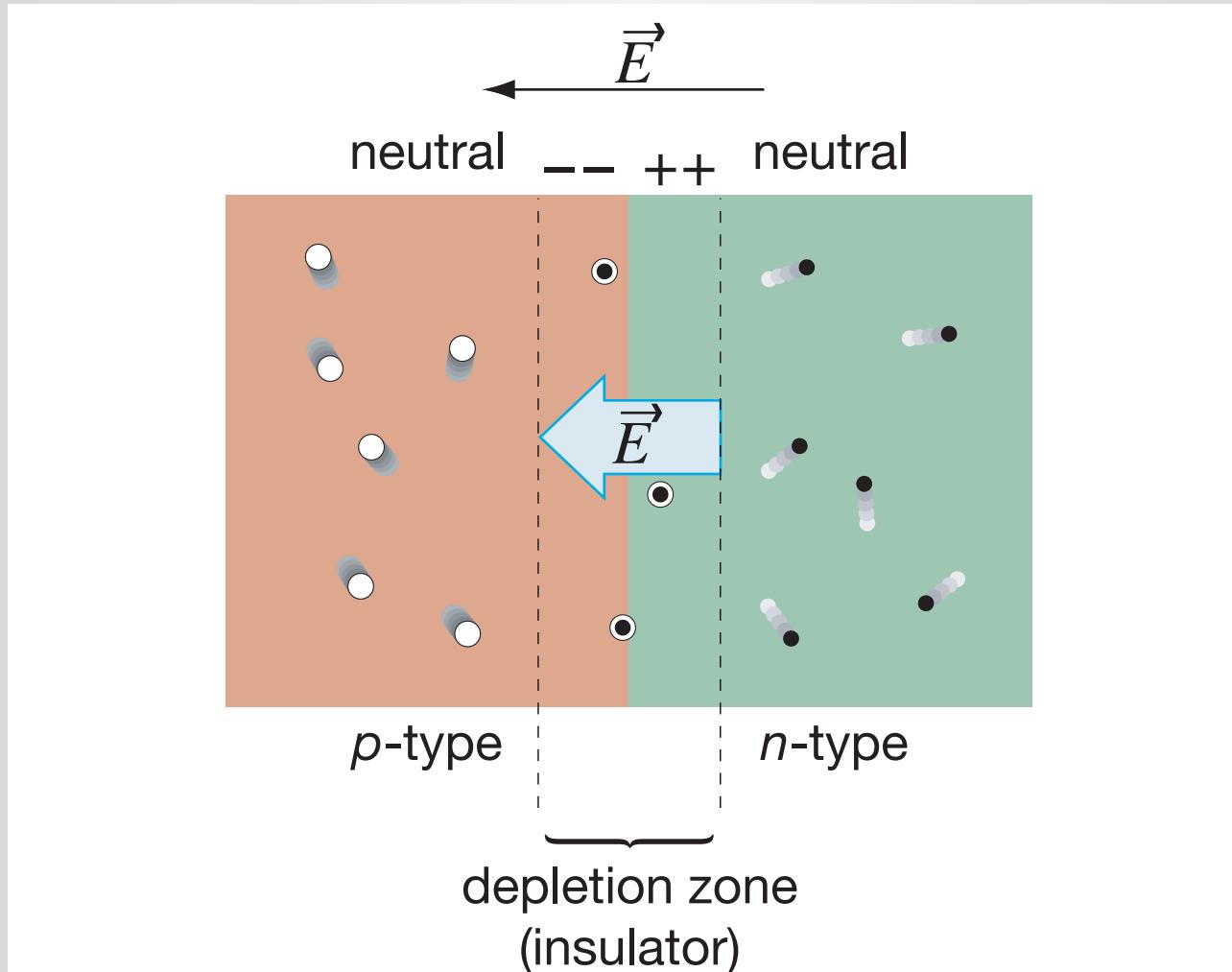
# Photodetectors

and so depletion zone expands



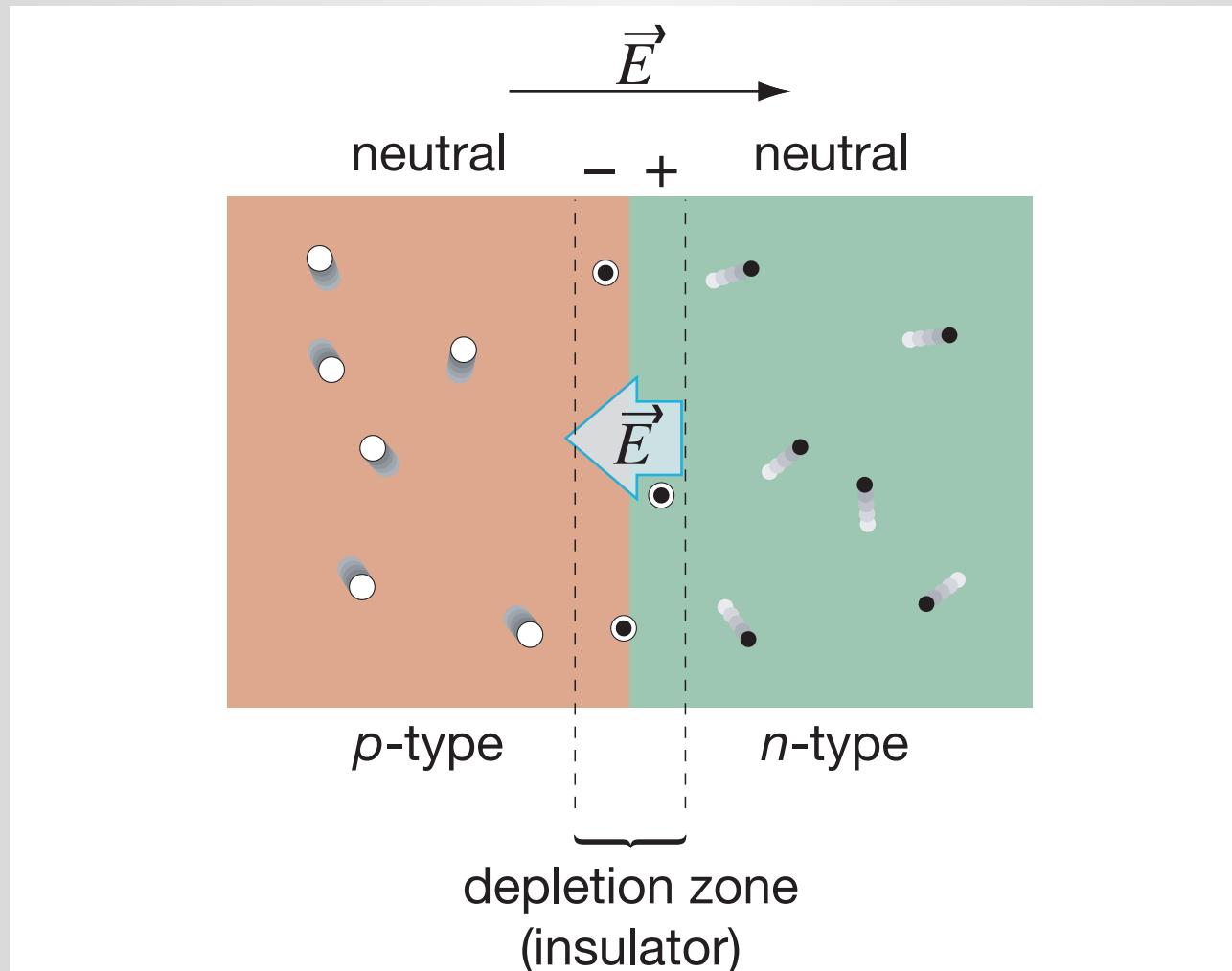
# Photodetectors

NO conduction



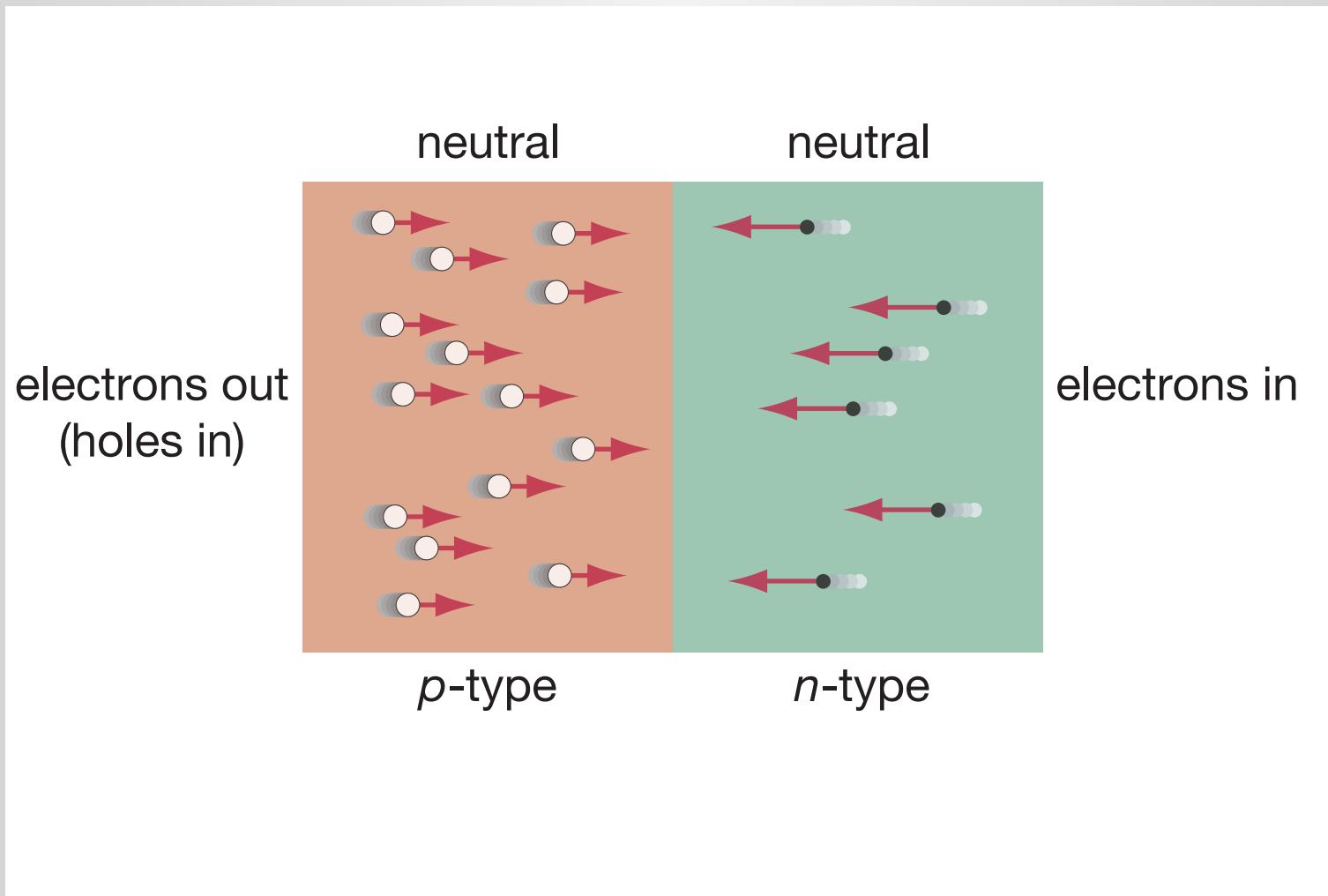
# Photodetectors

reverse electric field...



# Photodetectors

...depletion zone shrinks and current flows

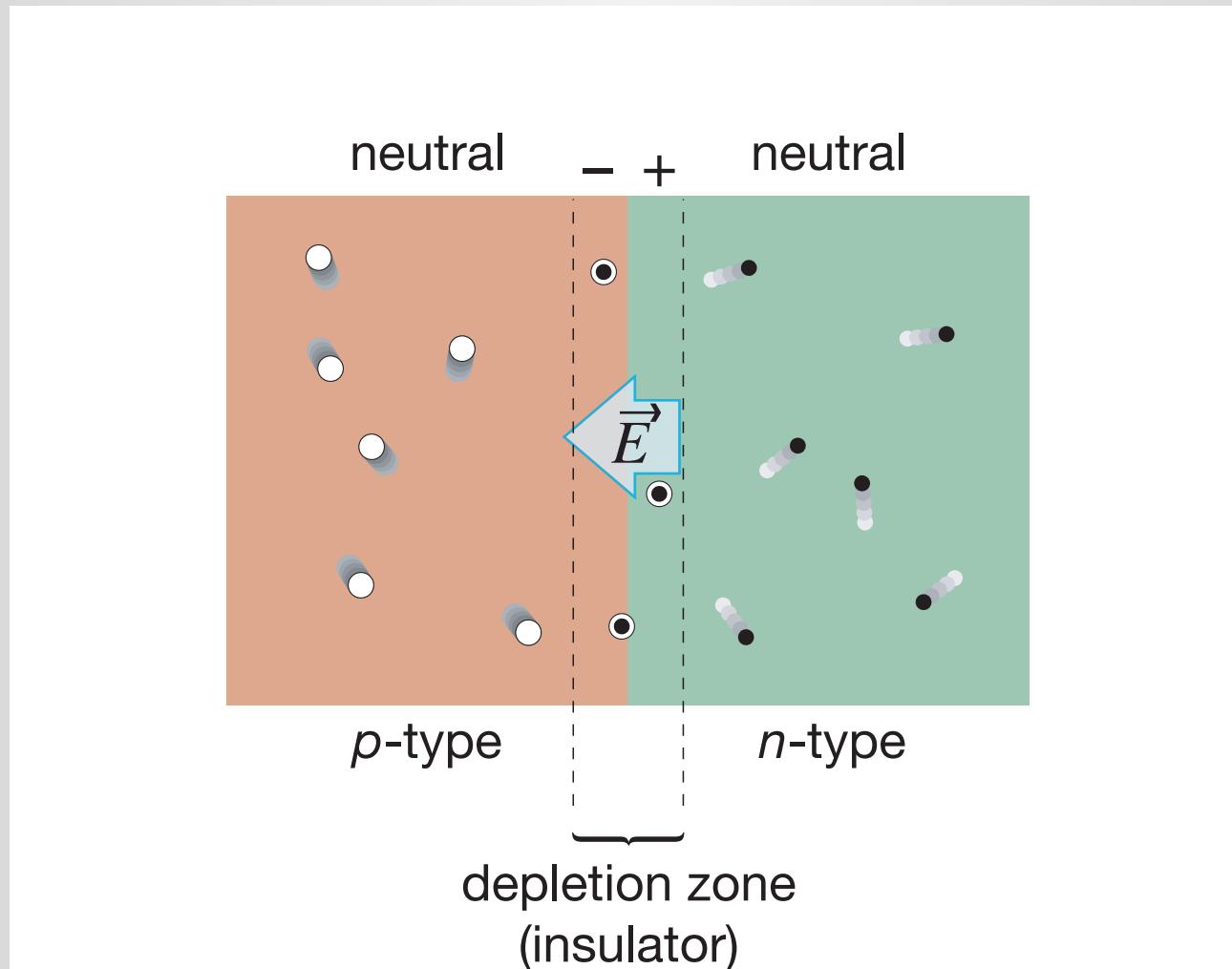


# Photodetectors

**so pn-junction like one-way valve for charge flow: a diode**

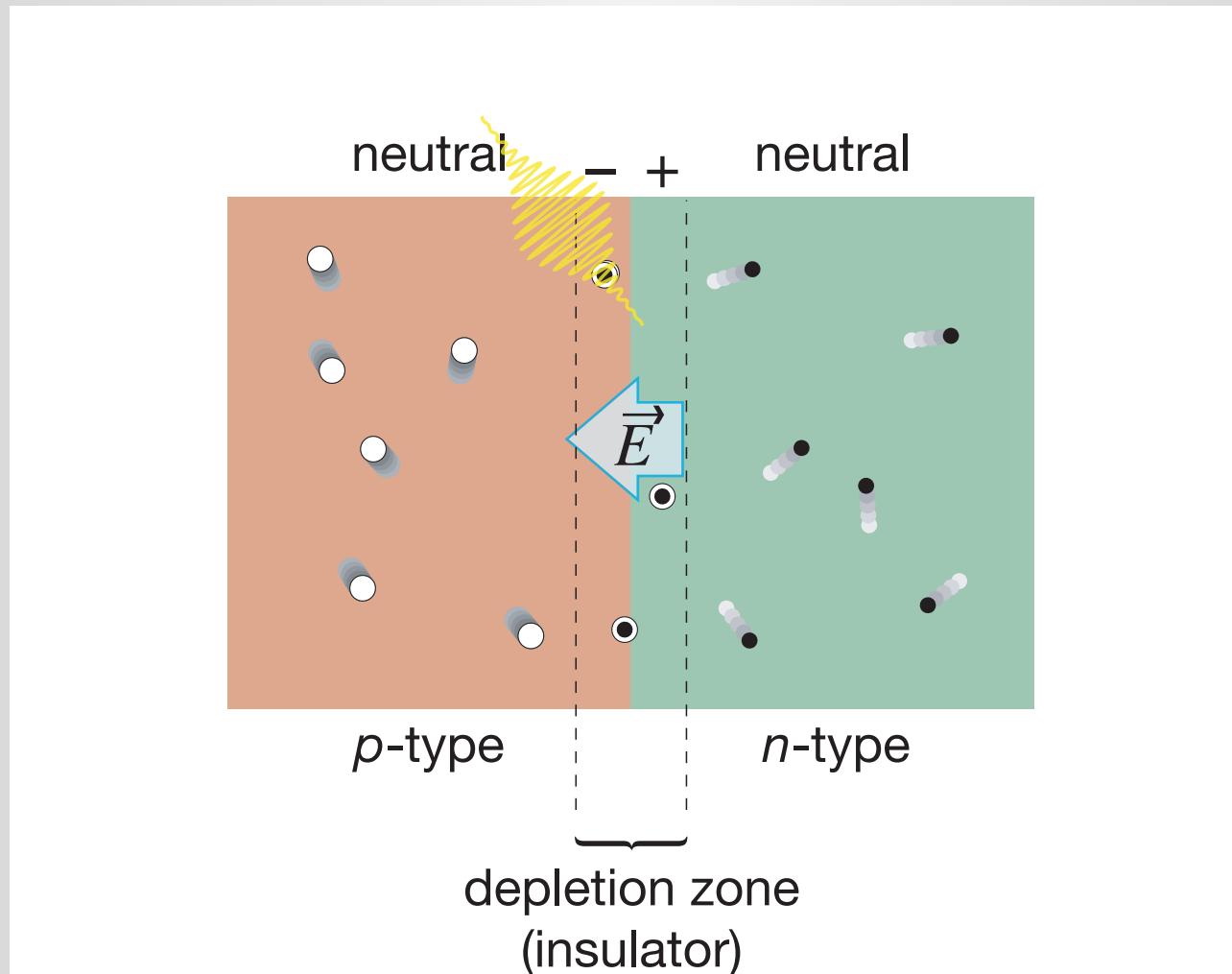
# Photodetectors

depletion layer can convert light into electric energy



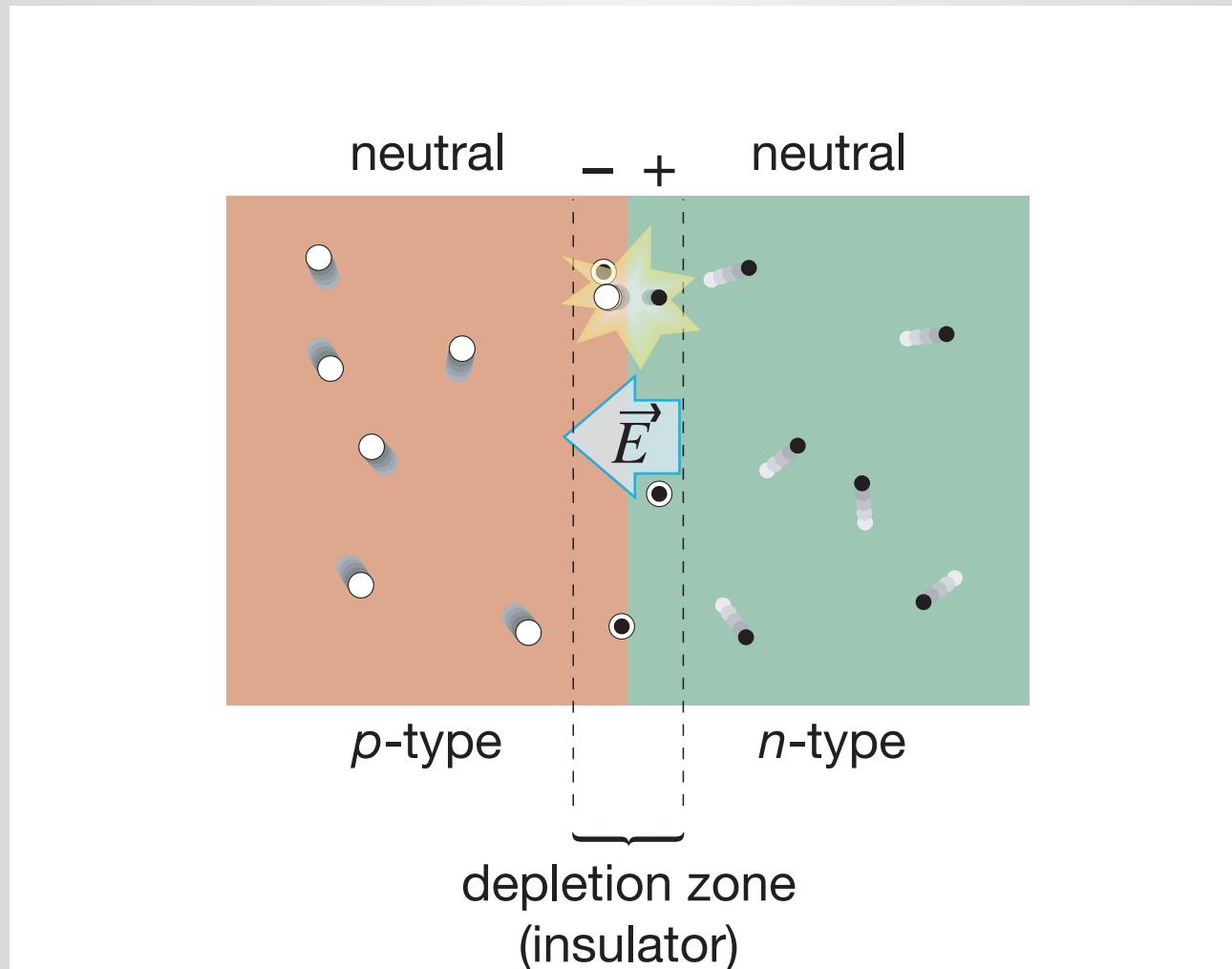
# Photodetectors

incident photon knocks out electron...



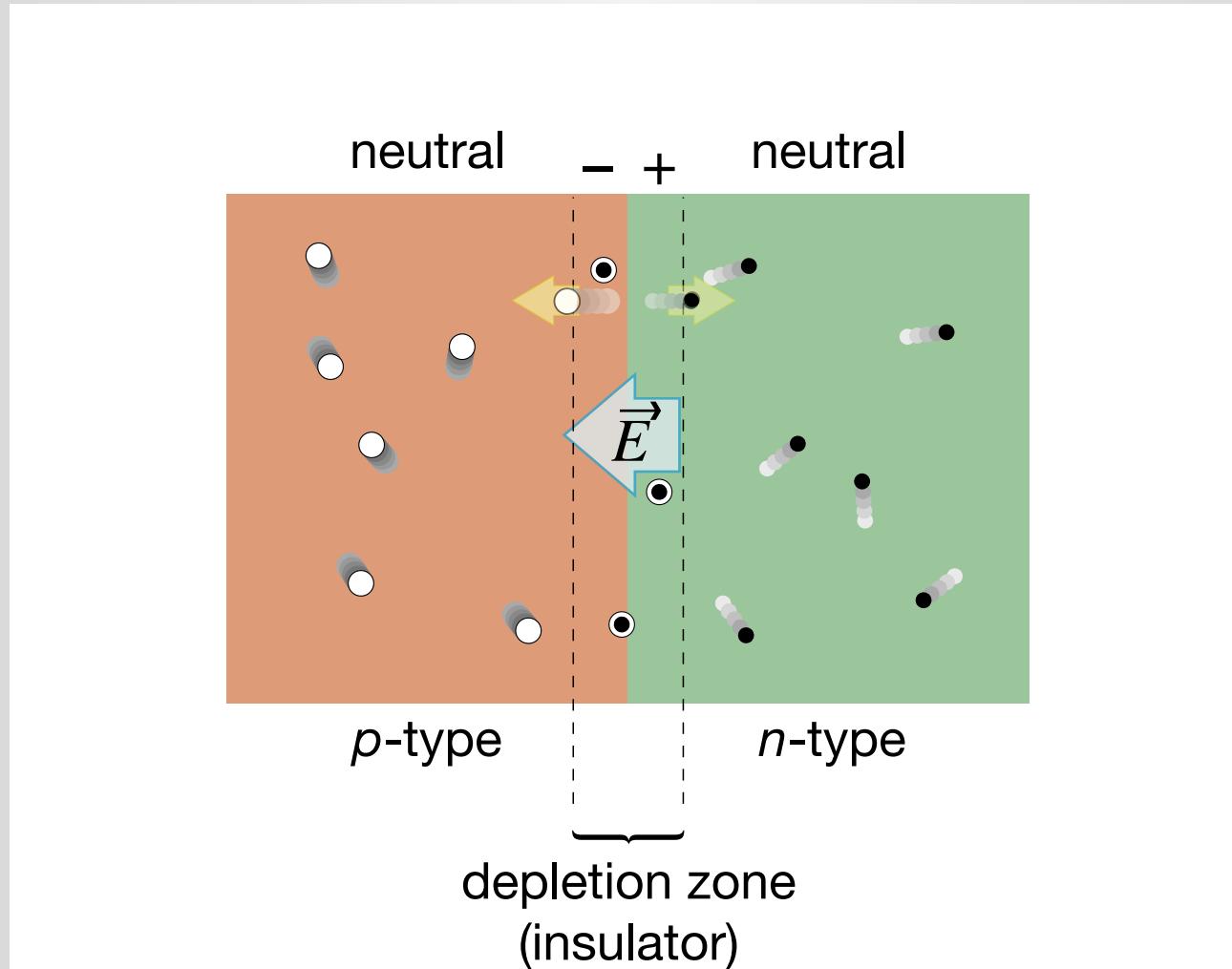
# Photodetectors

...creating an electron-hole pair



# Photodetectors

**E-field separates eh-pair, causing current**



# Outline

- optical properties
- structural and chemical analysis
- photodetectors
  - the *p-n* junction
  - femtosecond-laser microstructured silicon photodiodes
- outlook

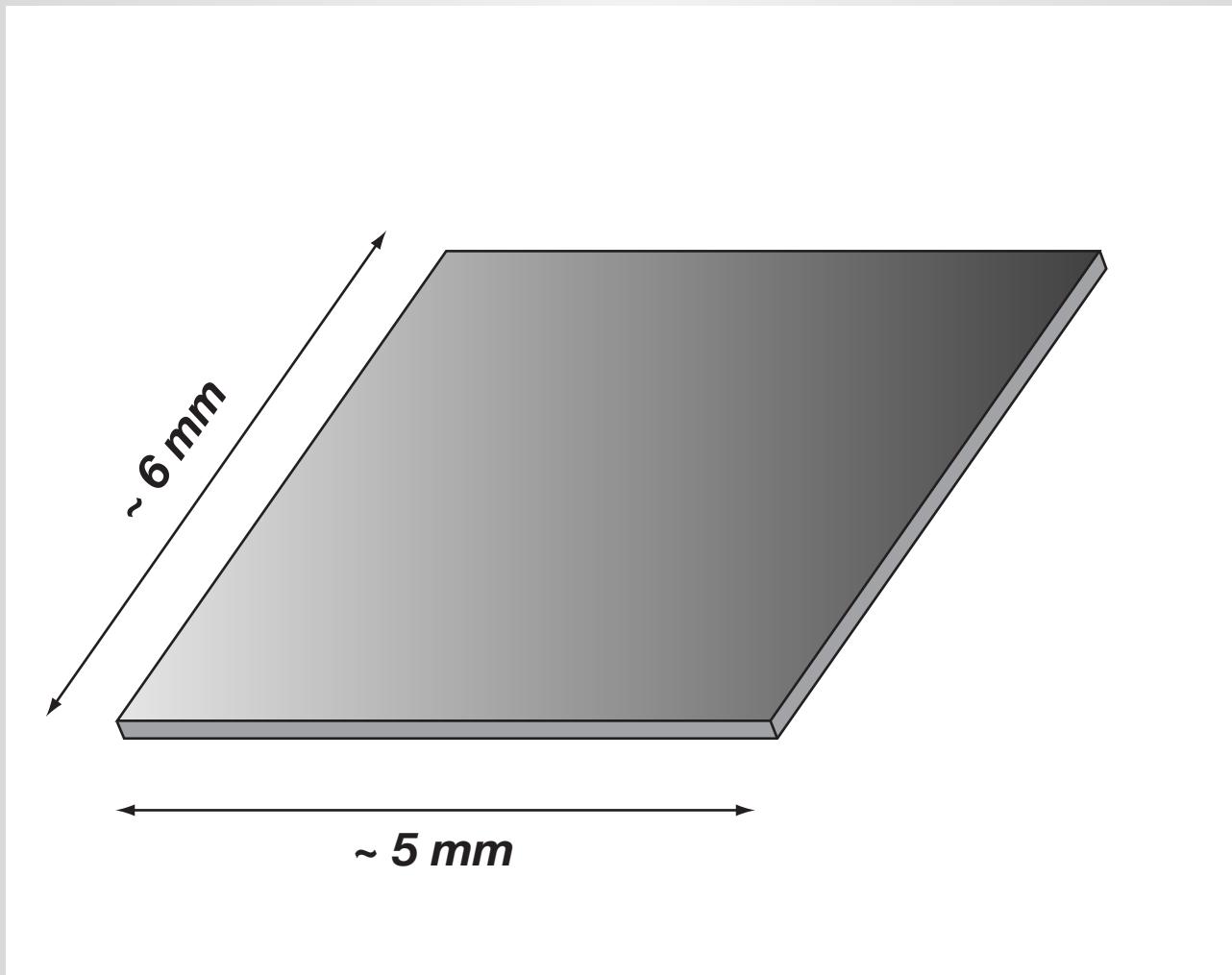
# Photodetectors

**create photodiode using black silicon/silicon junction**

1  $\mu\text{m}$

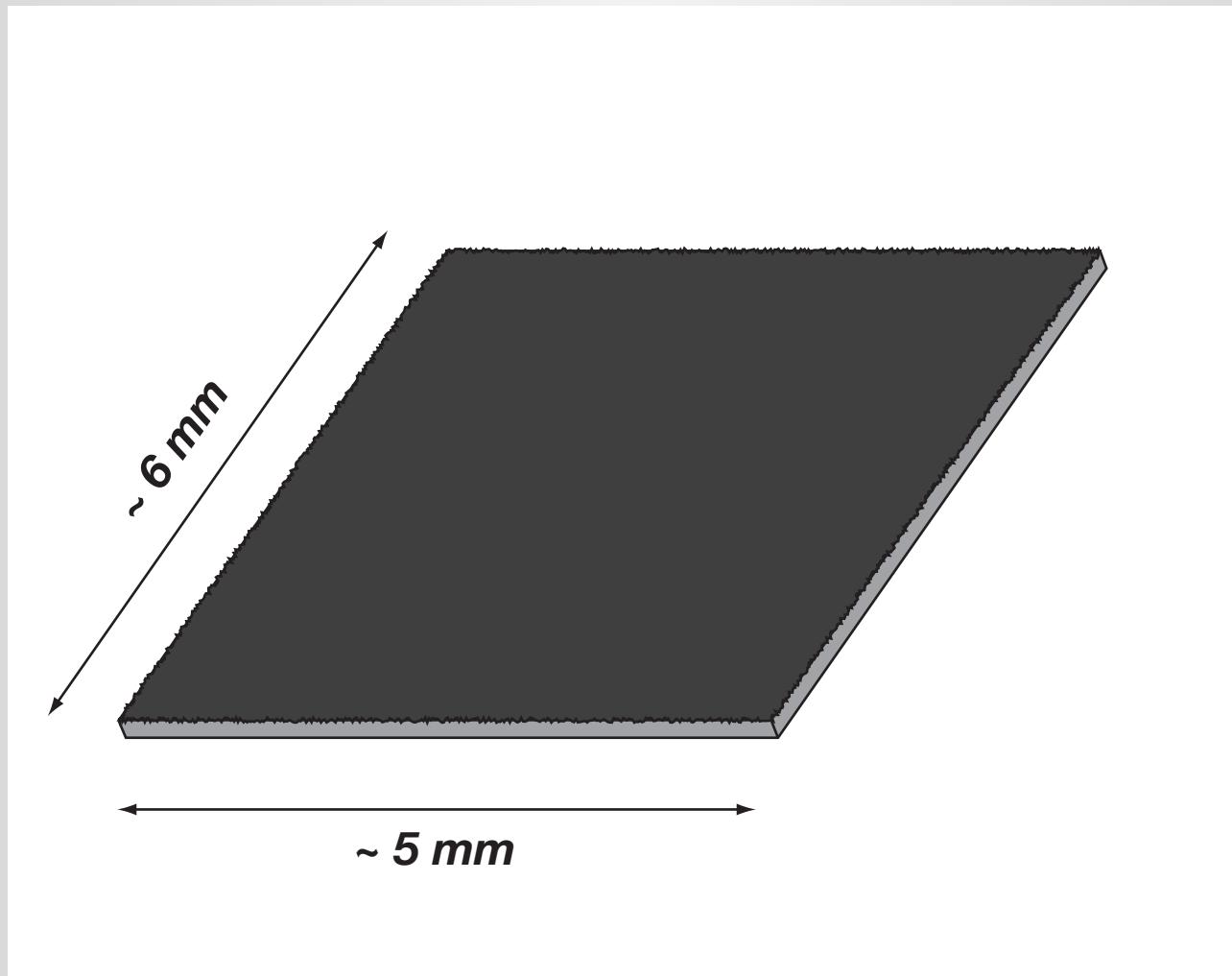
# Photodetectors

**crystalline Si**



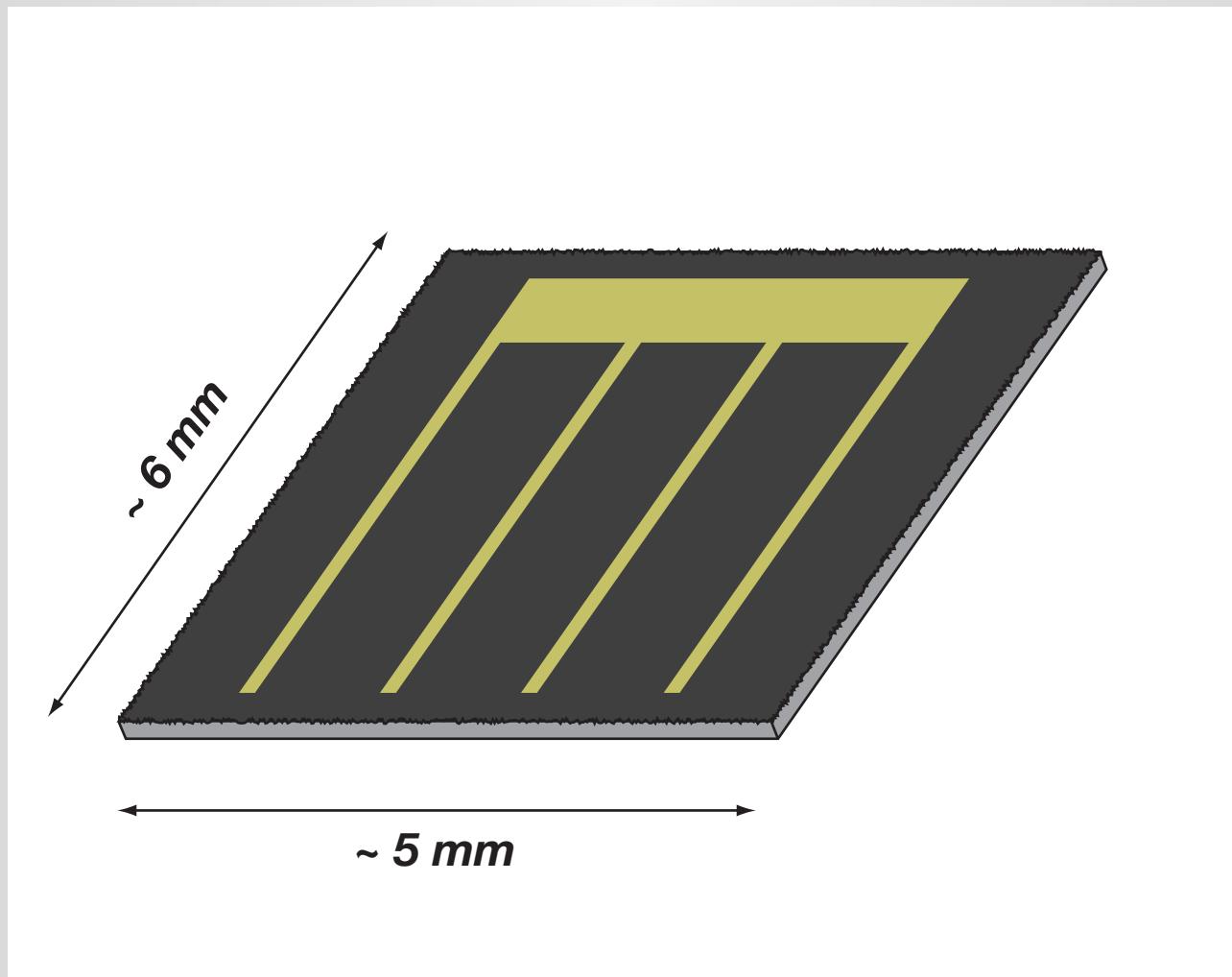
# Photodetectors

irradiate with 100-fs laser pulses in SF<sub>6</sub>



# Photodetectors

Cr/Au contact



# Photodetectors

cross section



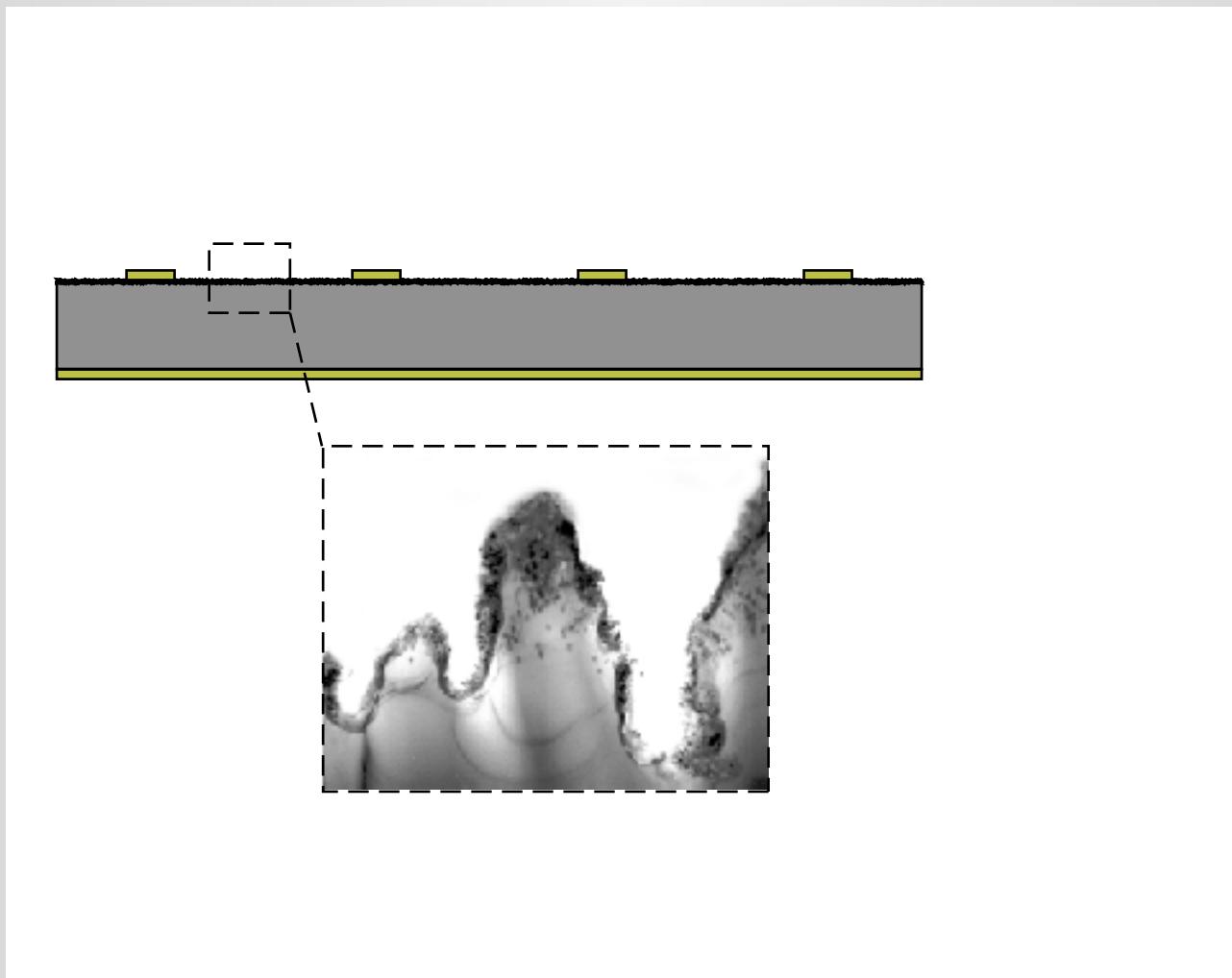
# Photodetectors

**Cr/Au contact**



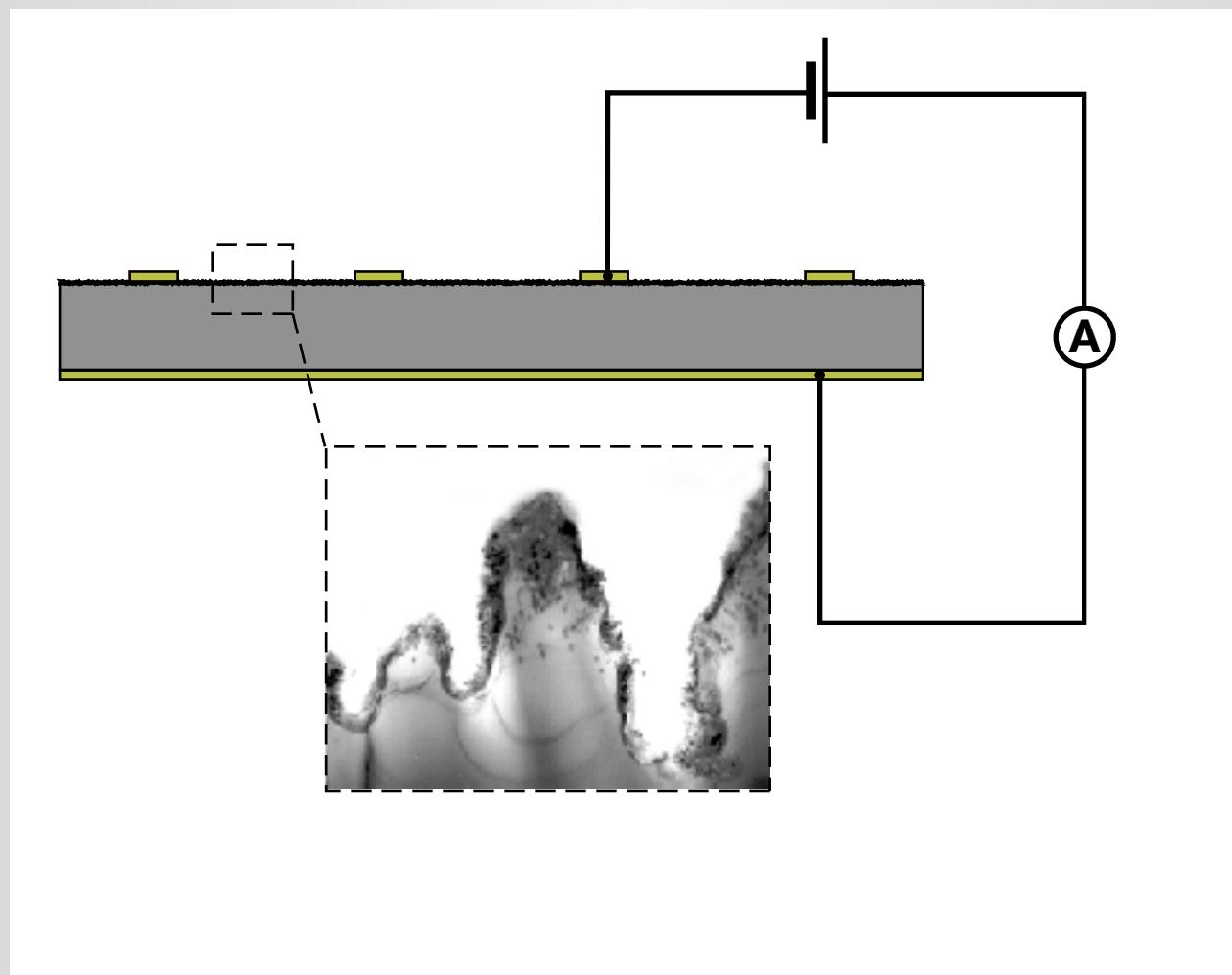
# Photodetectors

**black silicon/silicon junction**



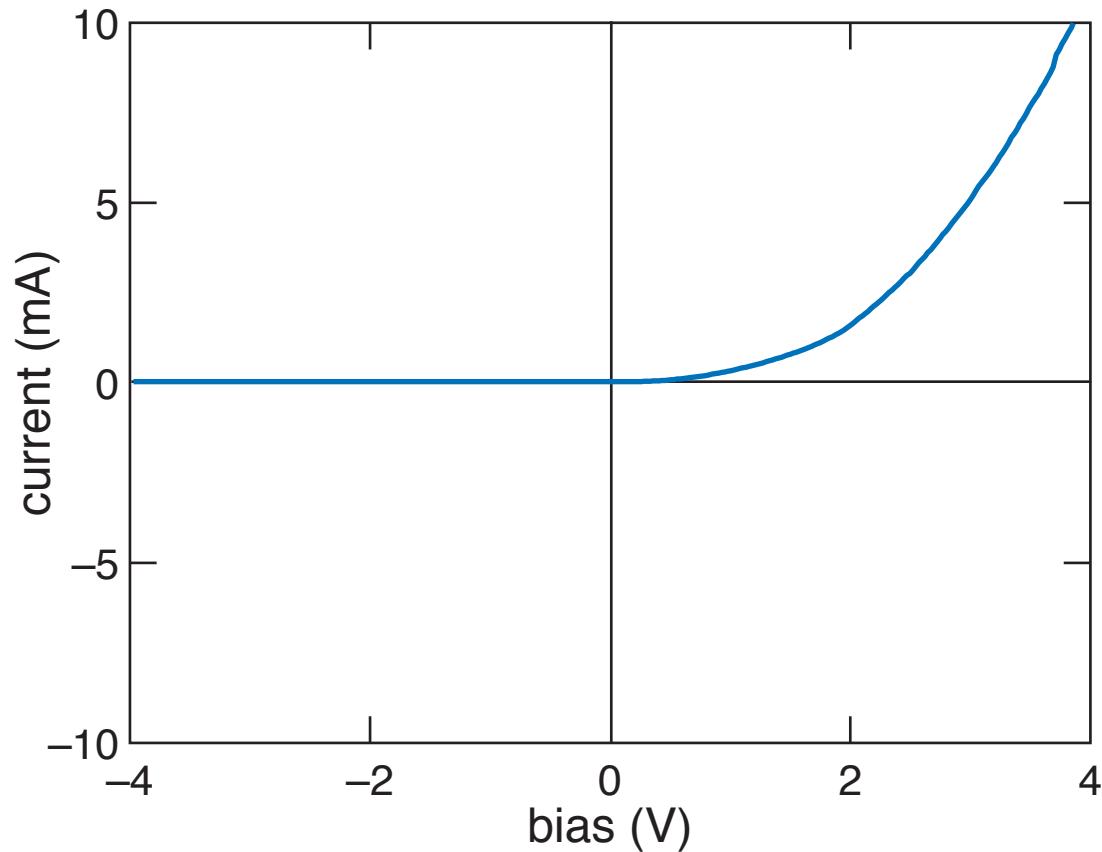
# Photodetectors

## *I/V* characteristics



# Photodetectors

## *IV* characteristics

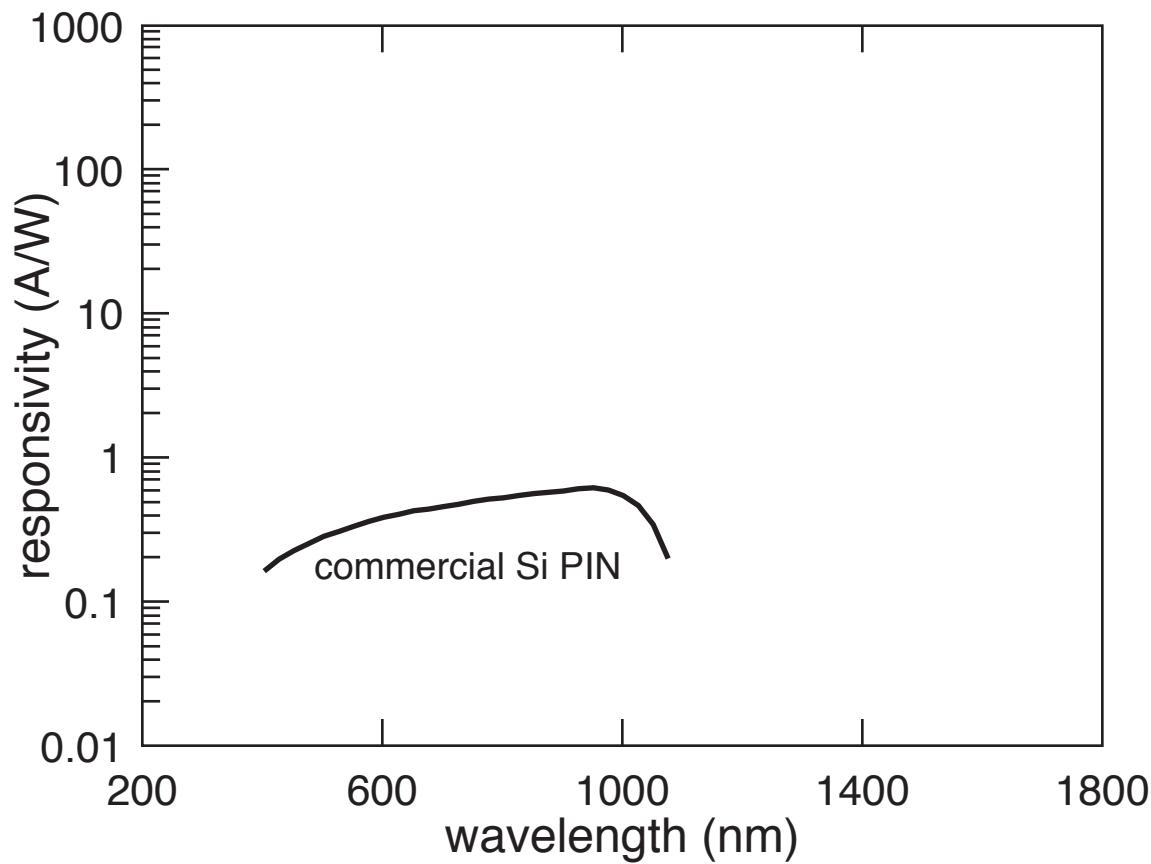


# Photodetectors

**We have a diode. What about a photodiode?**

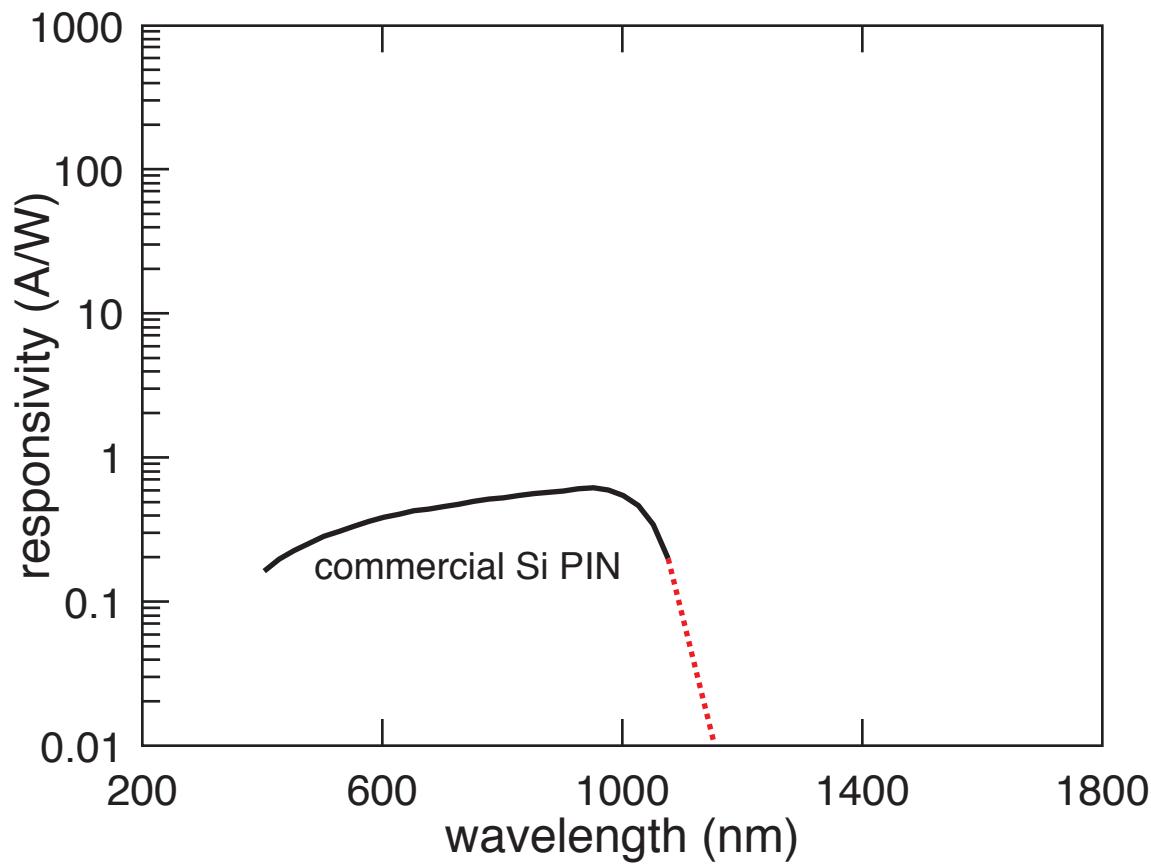
# Photodetectors

## responsivity



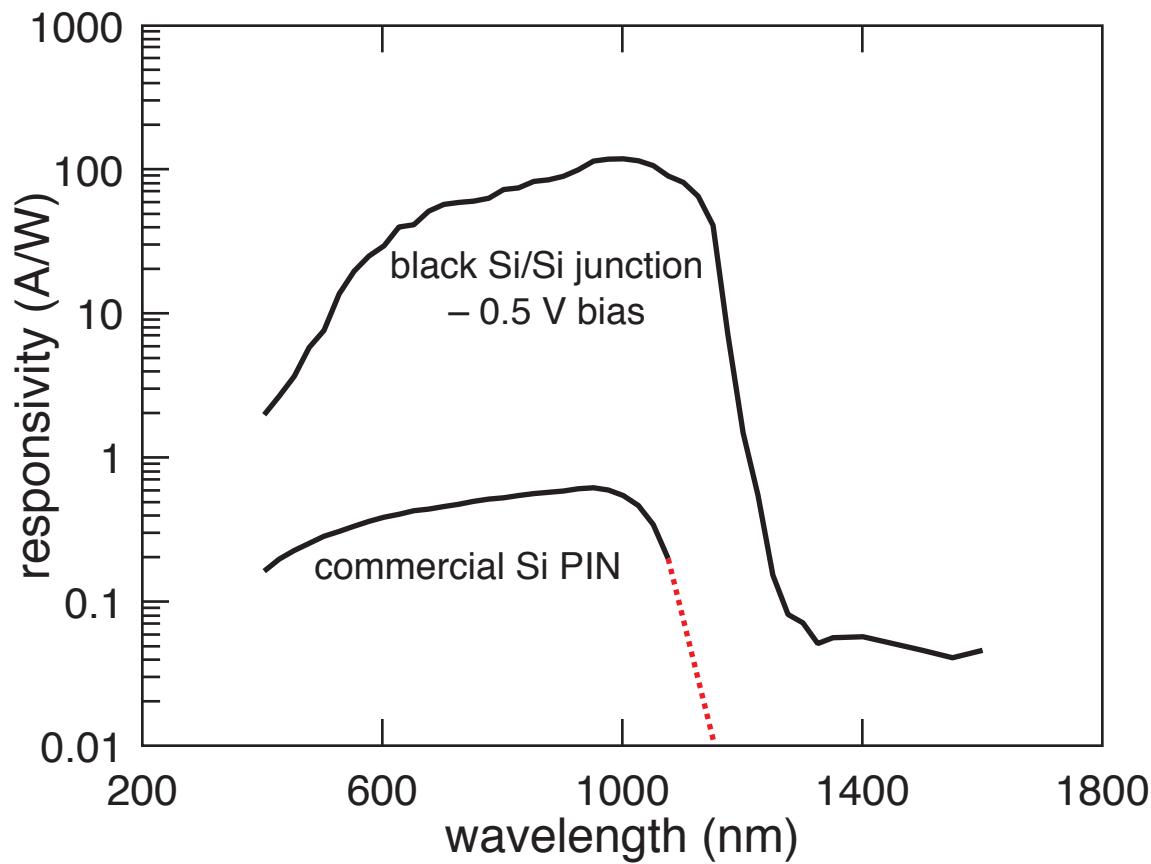
# Photodetectors

## responsivity



# Photodetectors

## responsivity



# Photodetectors

## **black silicon/silicon photodiode**

- nearly 100x larger signal in visible
- $10^4$  larger signal in near-IR
- quantum efficiency  $>> 1$ , gain!

# Outlook

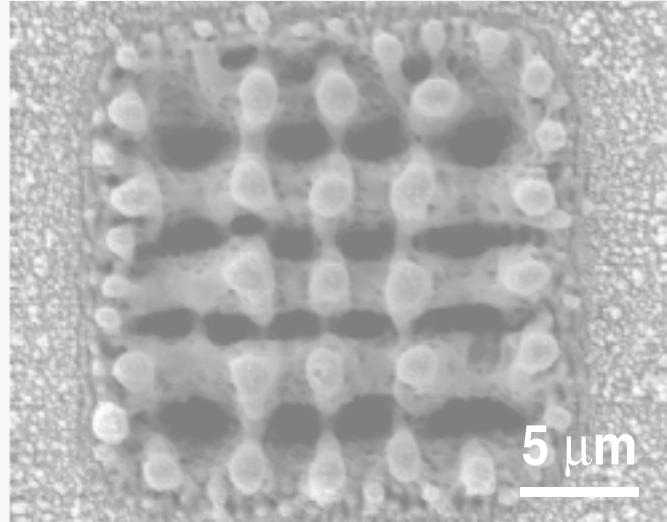
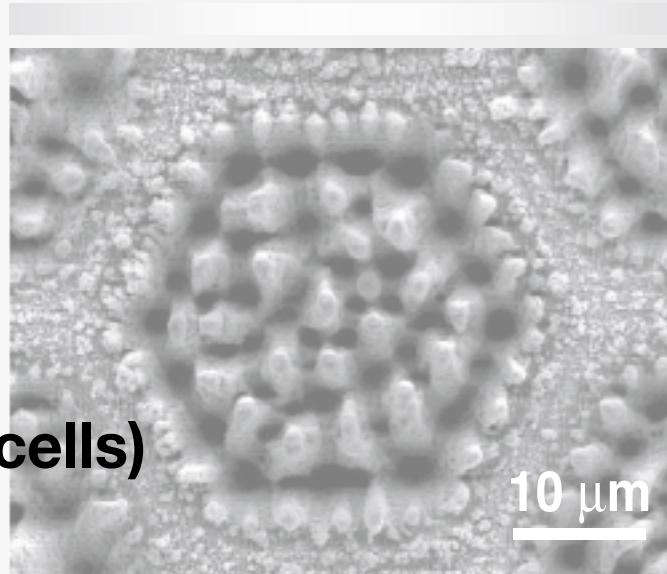
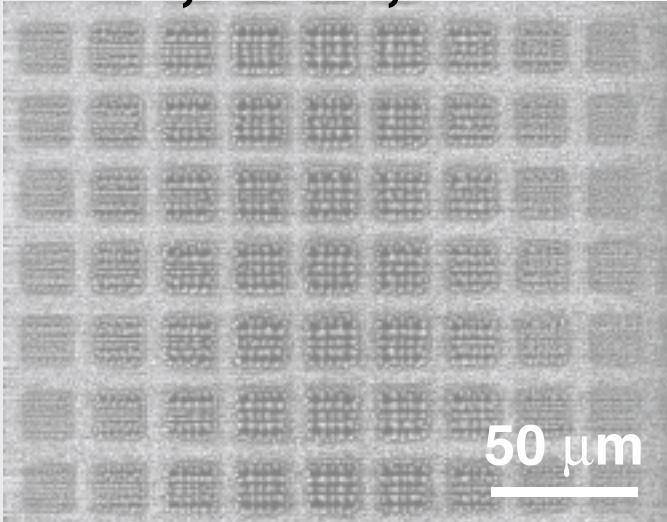
- photodetectors

- detector arrays

- photovoltaics (~2-3% solar cells)

$50 \mu\text{m}$

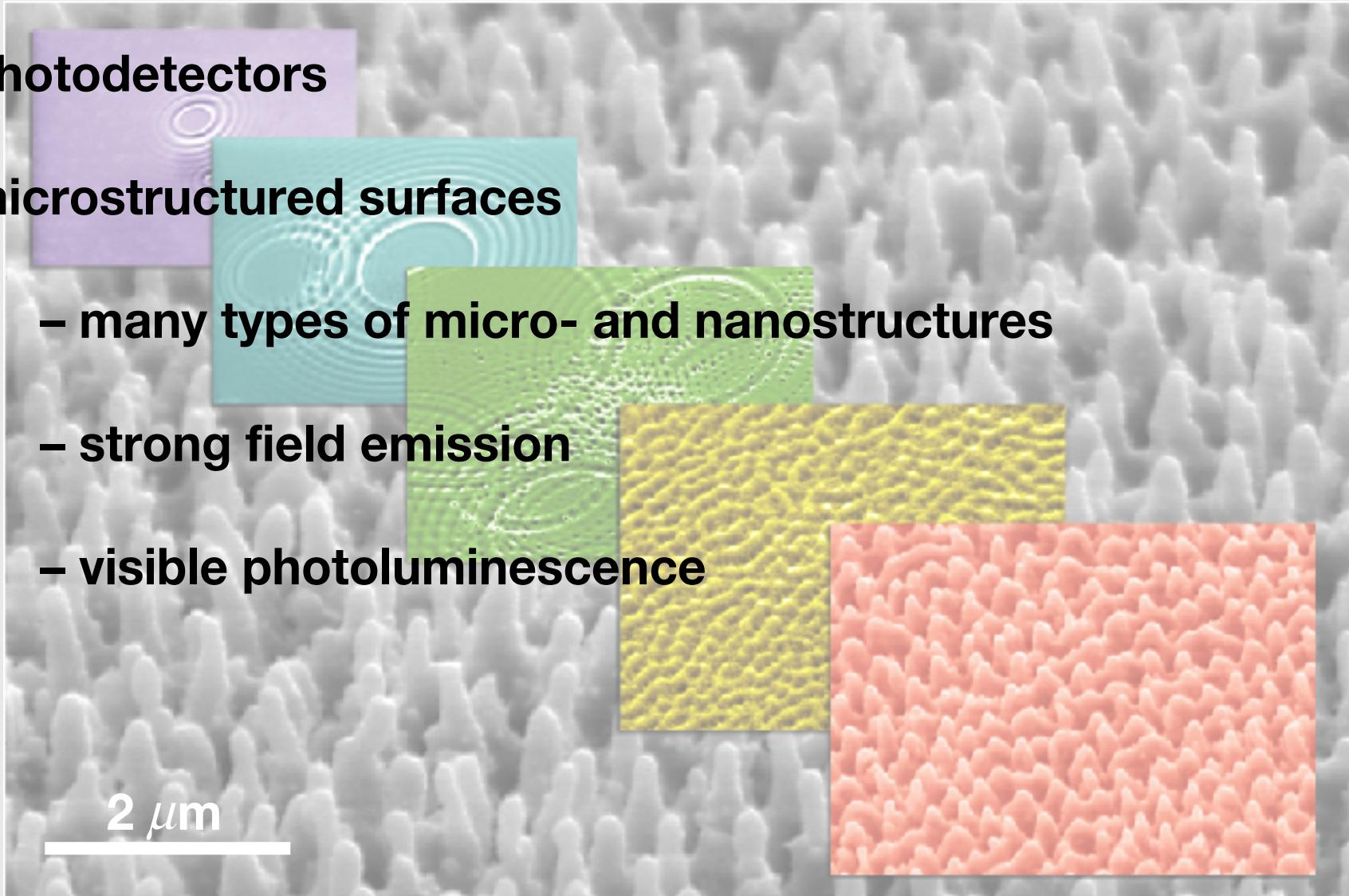
- APDs, CCDs, etc.



# Outlook

- photodetectors
- microstructured surfaces
  - many types of micro- and nanostructures
  - strong field emission
  - visible photoluminescence

2  $\mu\text{m}$



# Outlook

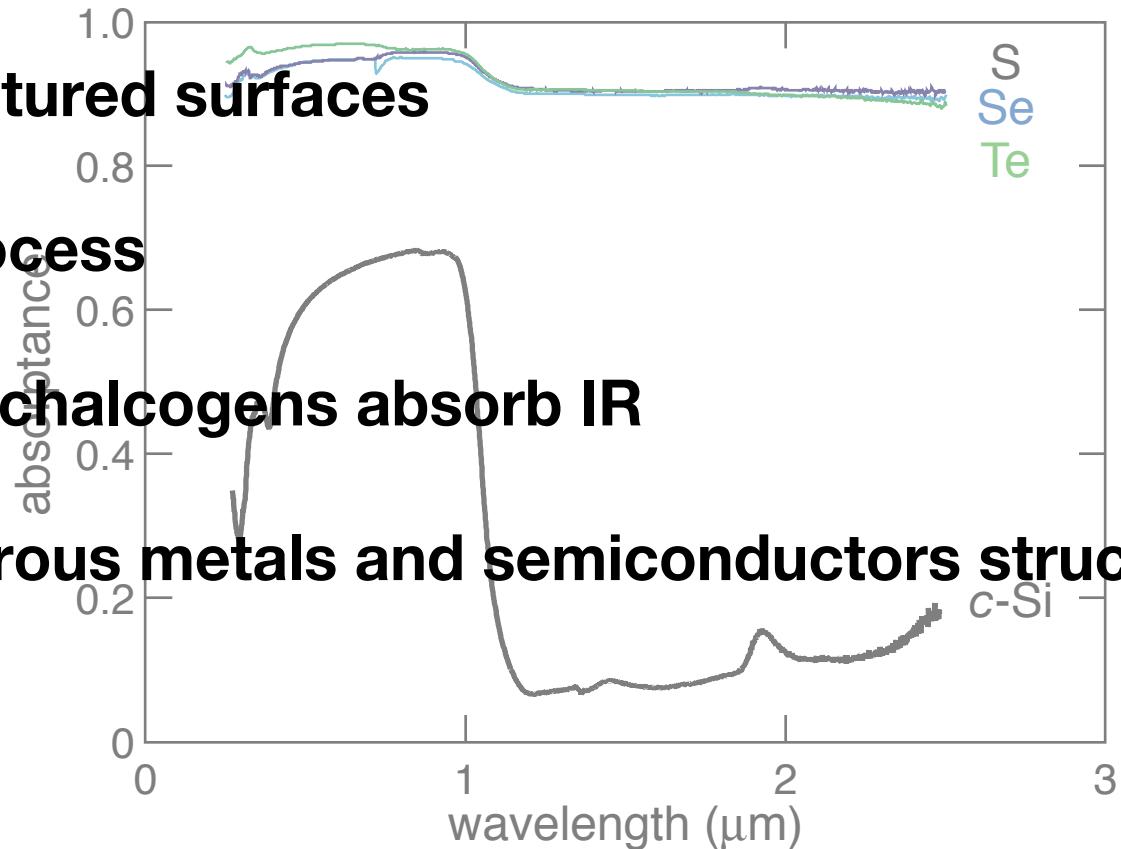
- photodetectors

- microstructured surfaces

- flexible process

- other chalcogens absorb IR

- numerous metals and semiconductors structured



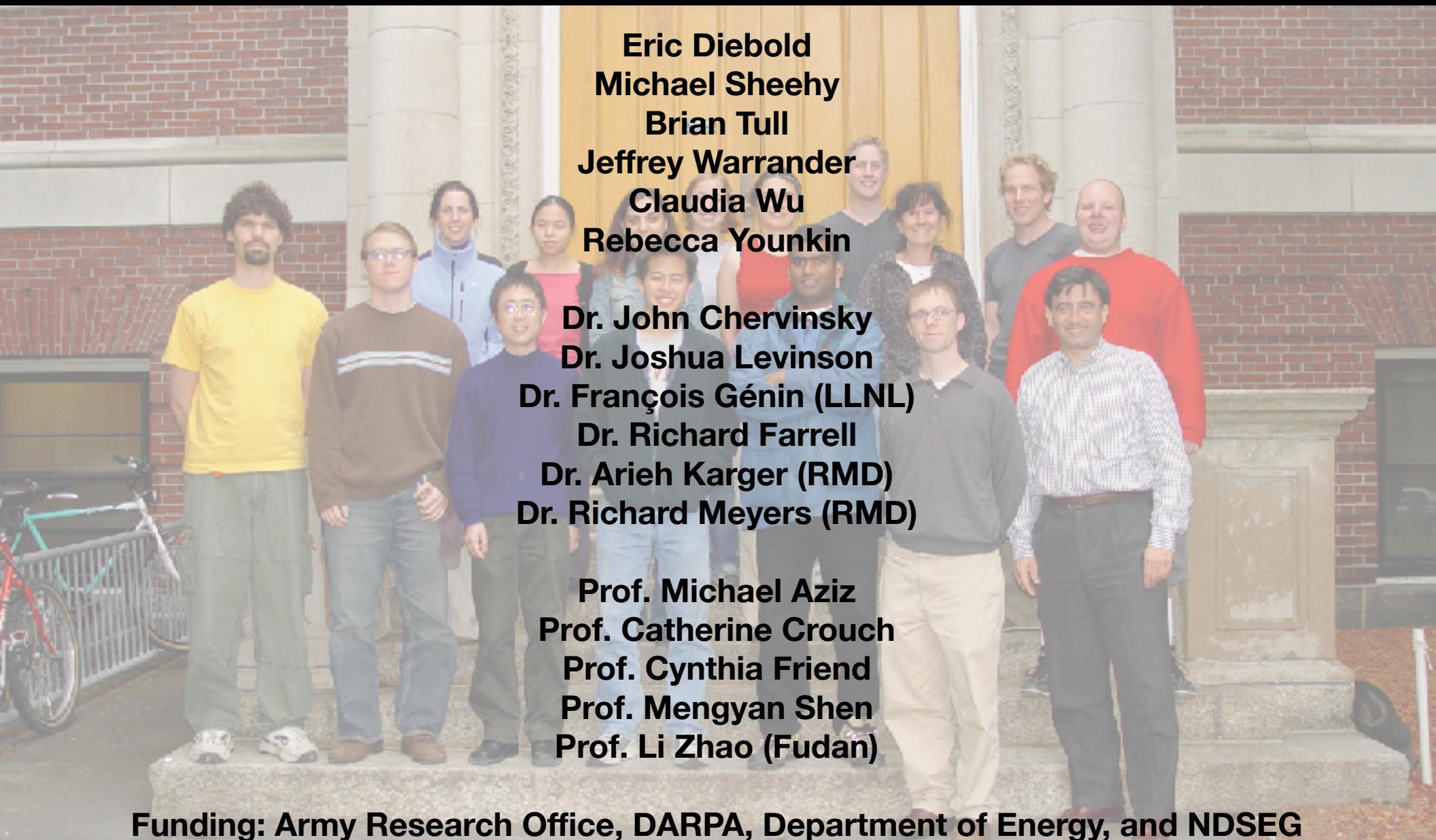
# Summary



# Summary

- **self-organized, conical microstructures**
- **near-unity absorption from near-UV to near-IR**
- **high sensitivity VIS/NIR silicon-based photodiodes**
- **maskless process, easily integrated with microelectronics**
- **just the beginning: many promising applications**

# Acknowledgements



**Eric Diebold**

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**Dr. François Génin (LLNL)**

**Dr. Richard Farrell**

**Dr. Arieh Karger (RMD)**

**Dr. Richard Meyers (RMD)**

**Prof. Michael Aziz**

**Prof. Catherine Crouch**

**Prof. Cynthia Friend**

**Prof. Mengyan Shen**

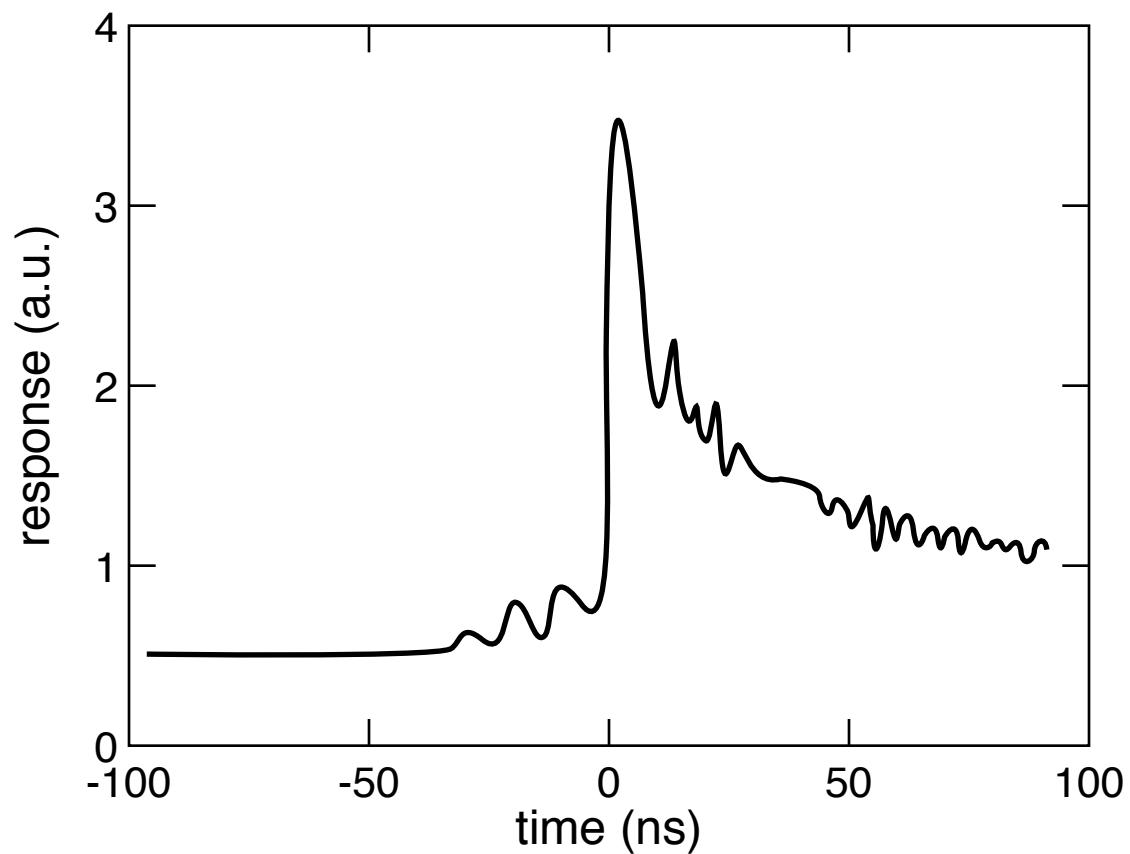
**Prof. Li Zhao (Fudan)**

**Funding: Army Research Office, DARPA, Department of Energy, and NDSEG**

**<http://mazur-www.harvard.edu/>**

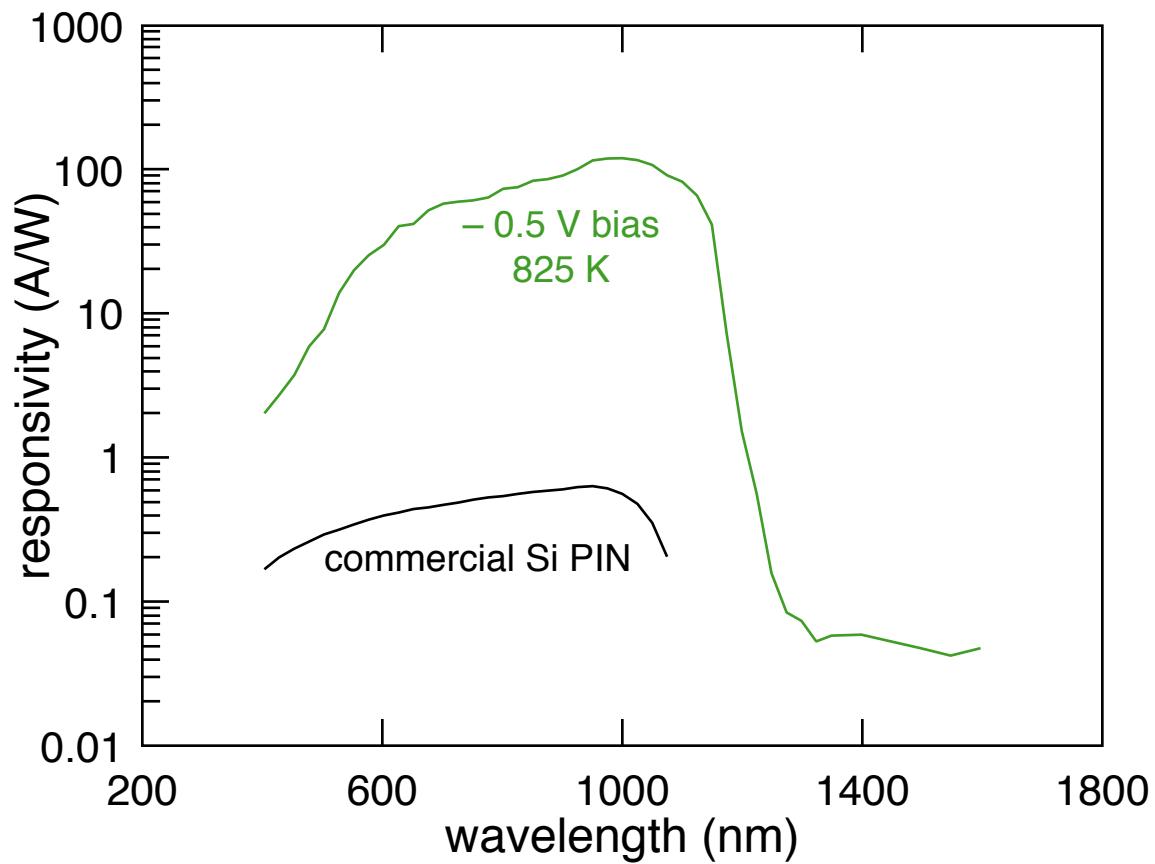
# Results

**response time: 10 ns rise, 30 ns fall**



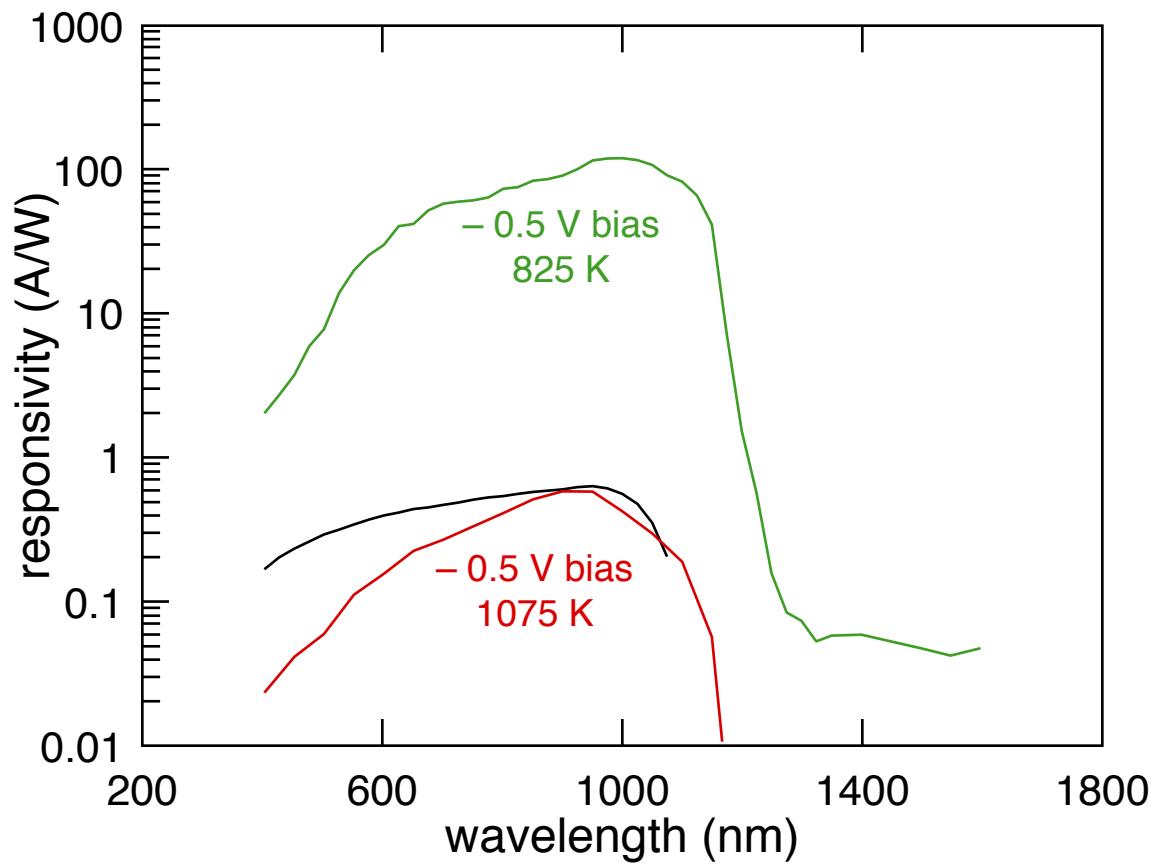
# Results

## effect of annealing



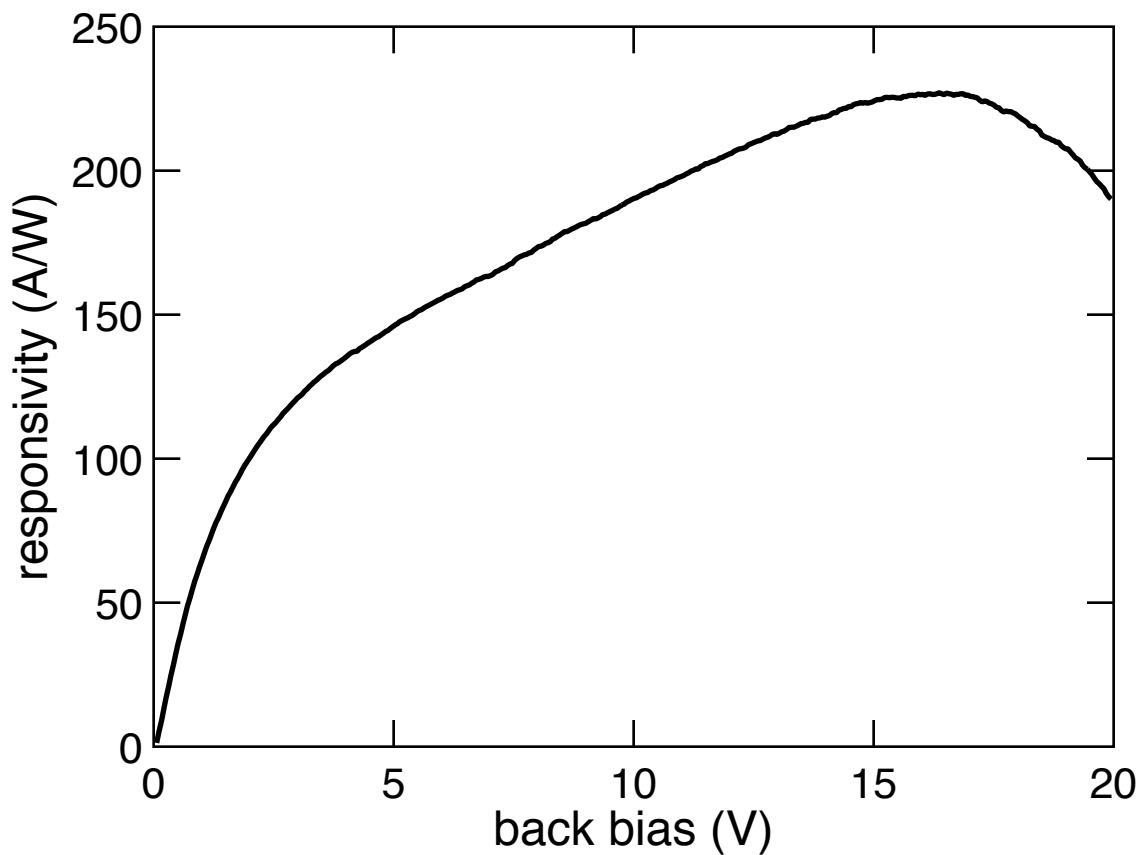
# Results

## effect of annealing



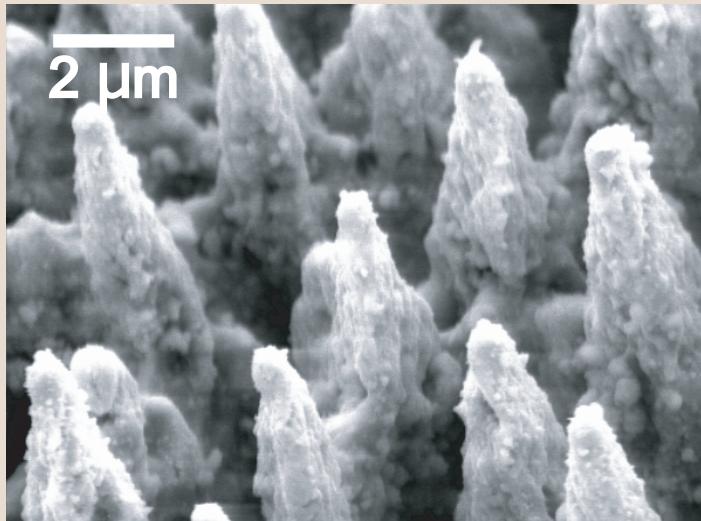
# Results

## responsivity (white light)

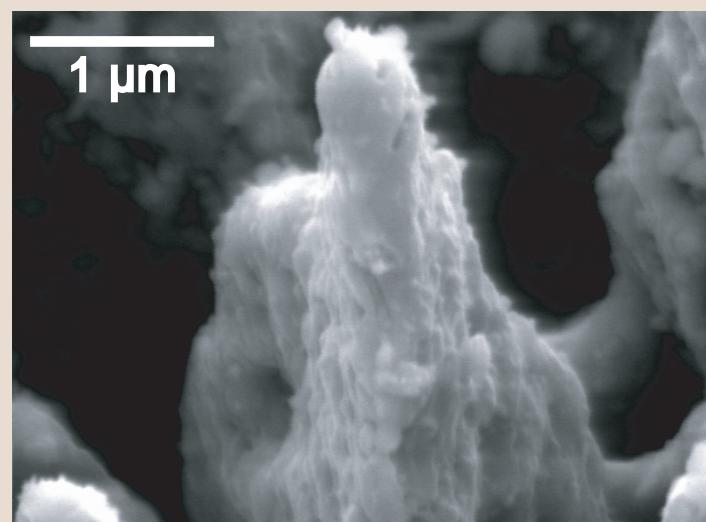
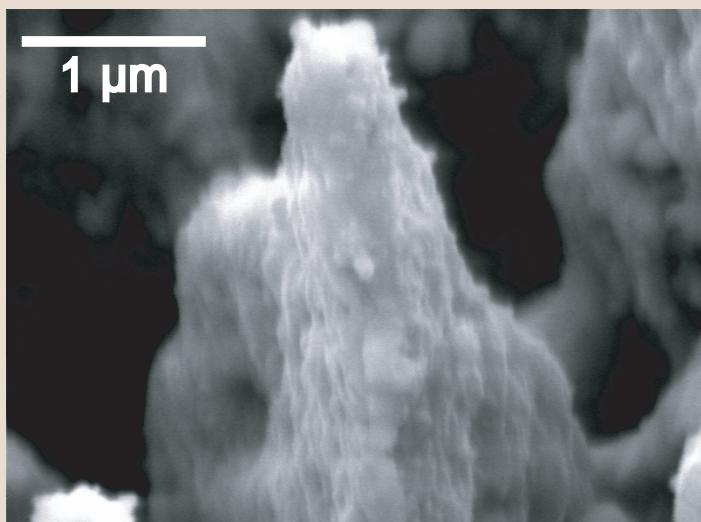
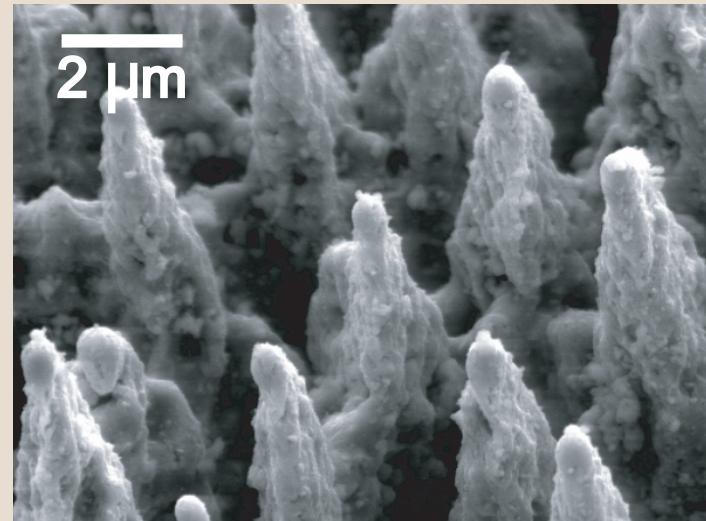


# *Structural analysis*

before annealing

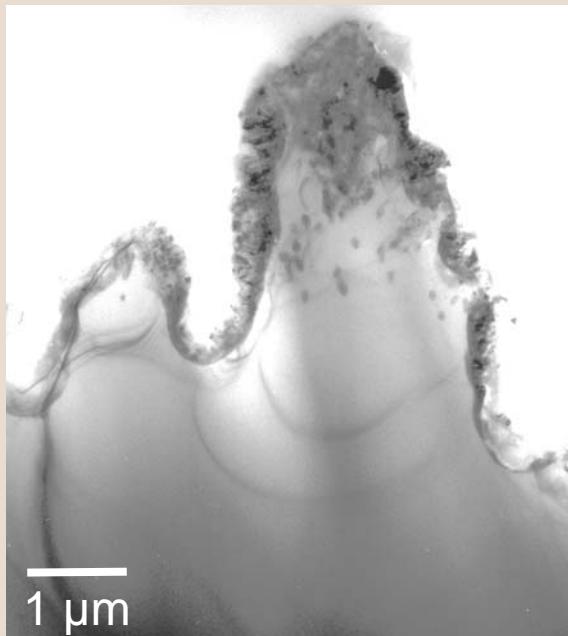


after annealing

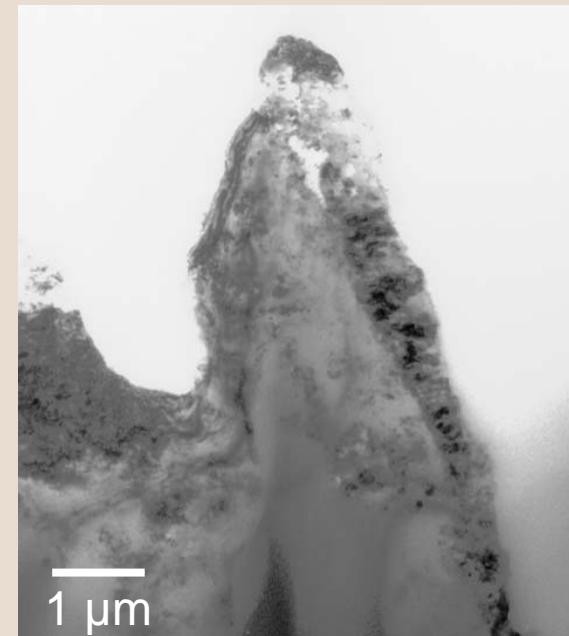


# *Structural analysis*

**not annealed**



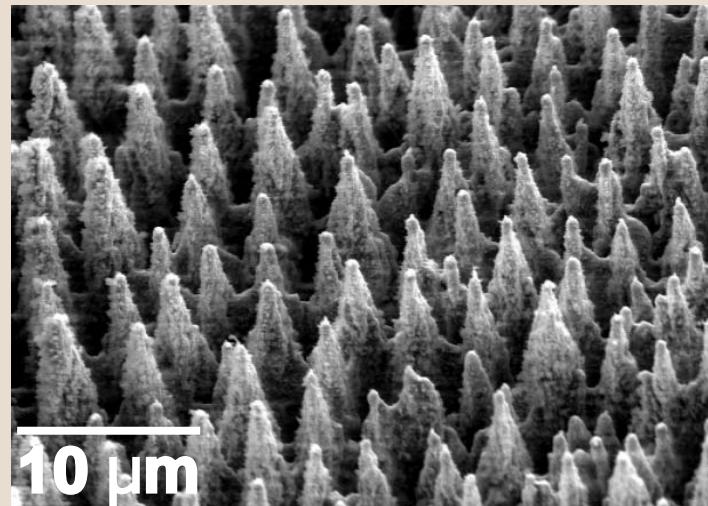
**annealed**



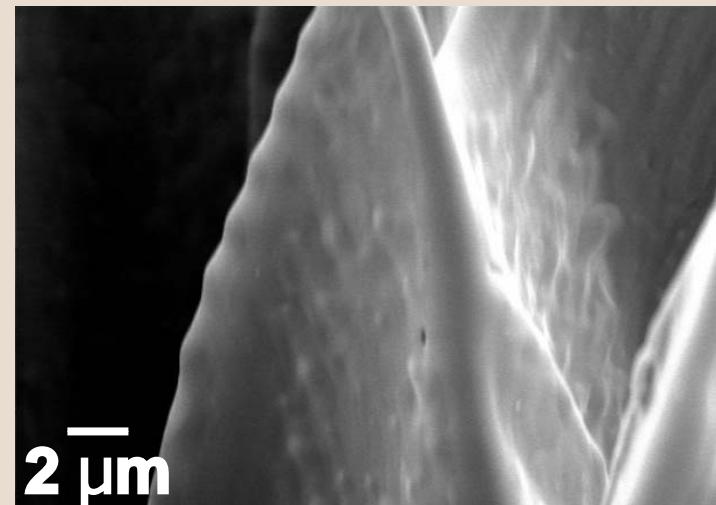
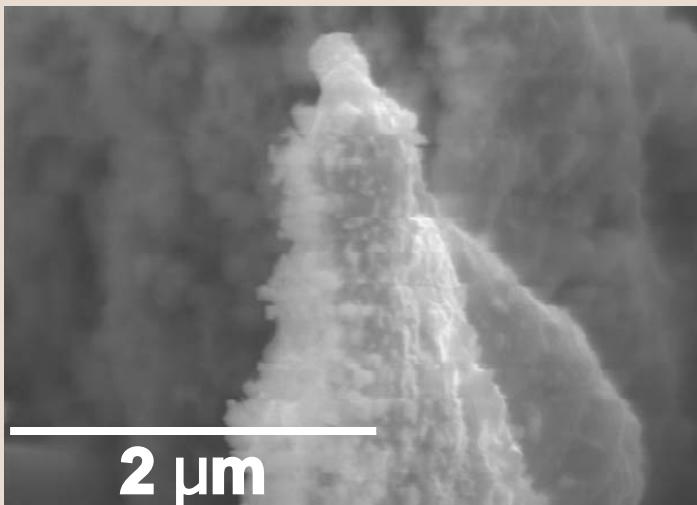
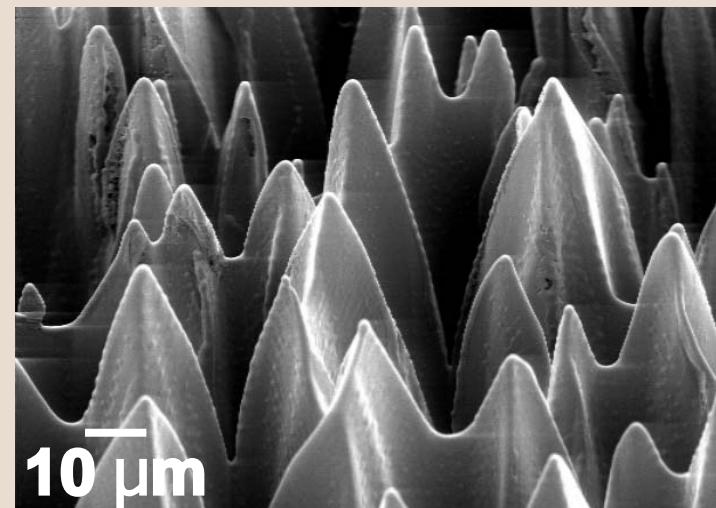
**annealing does not affect visible structure**

# *Nanosecond vs femtosecond*

**800 nm, 100 fs, 10 kJ/m<sup>2</sup>**

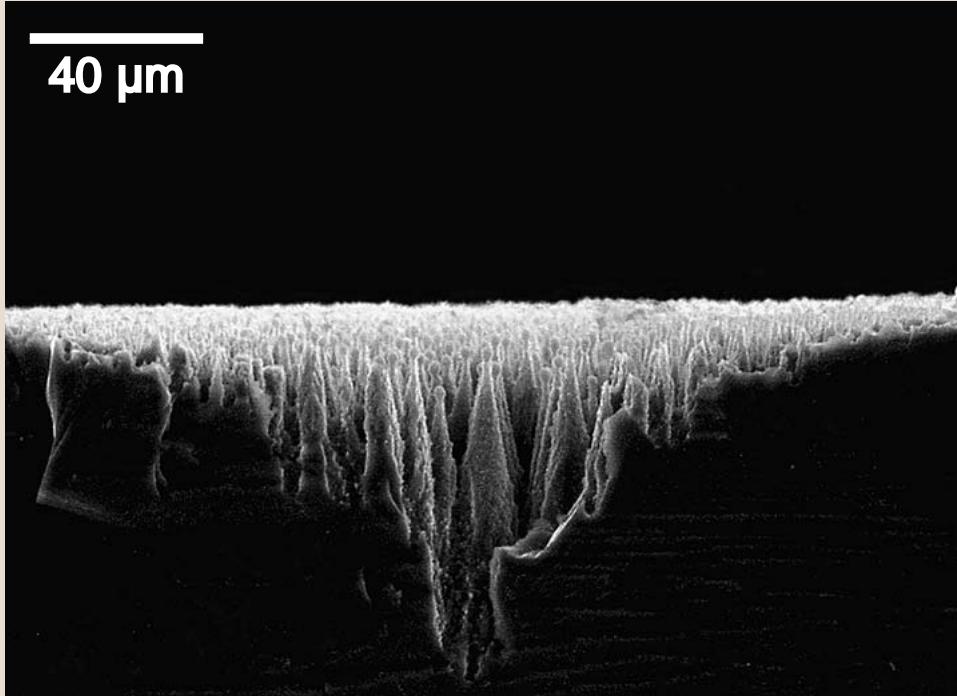


**248 nm, 30 ns, 30 kJ/m<sup>2</sup>**



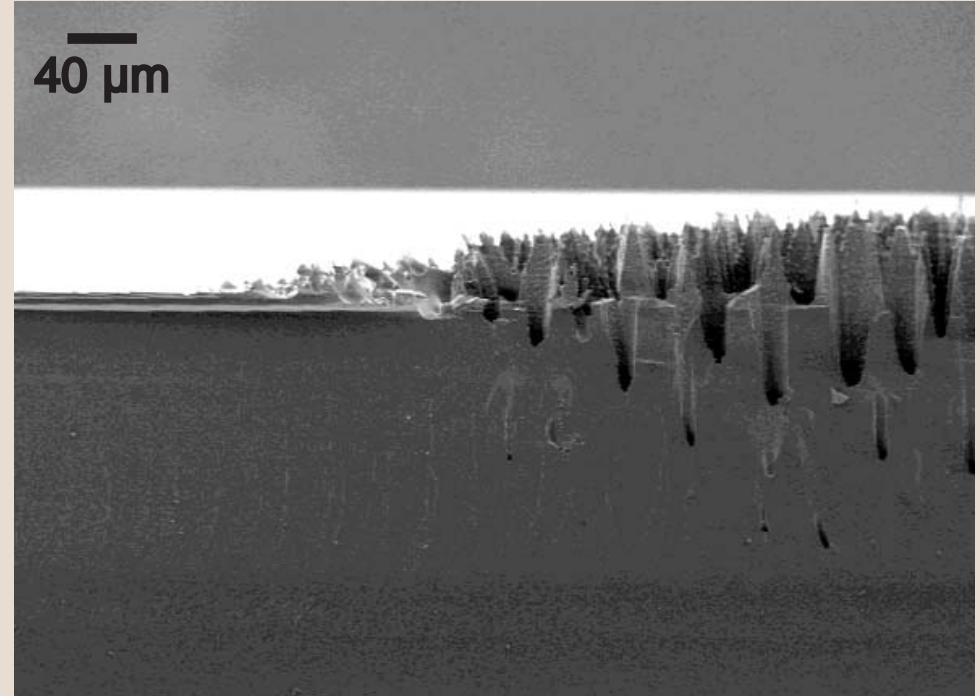
# *Nanosecond vs femtosecond*

**800 nm, 100 fs, 10 kJ/m<sup>2</sup>**



**fs cones etched below surface**

**248 nm, 30 ns, 30 kJ/m<sup>2</sup>**



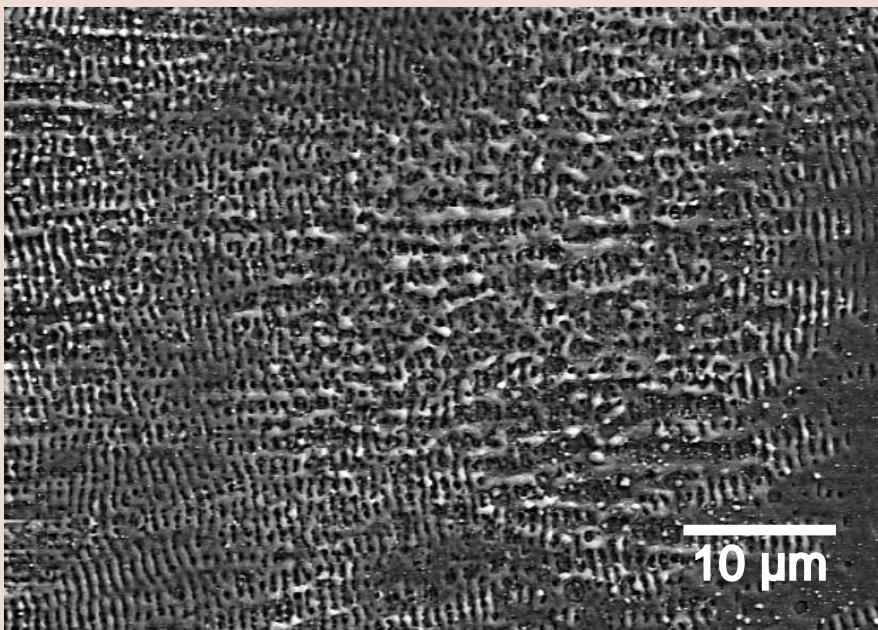
**ns cones grow above surface**

# *Formation process*

ripples

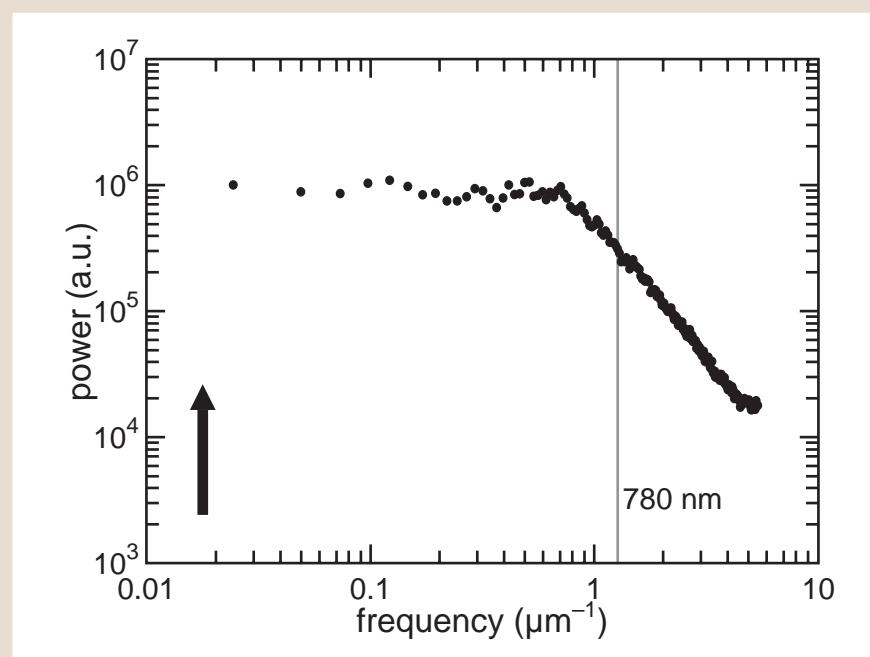
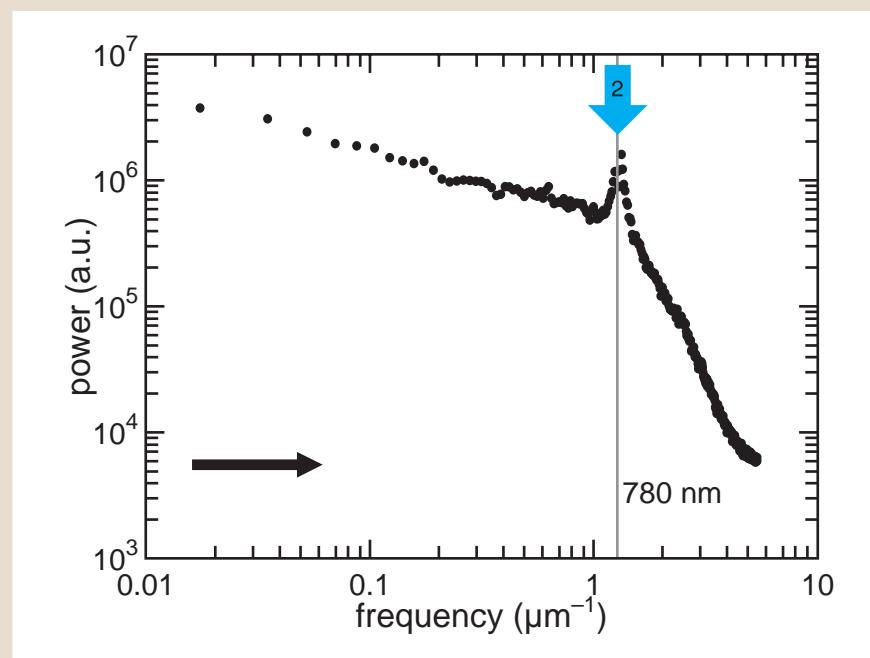
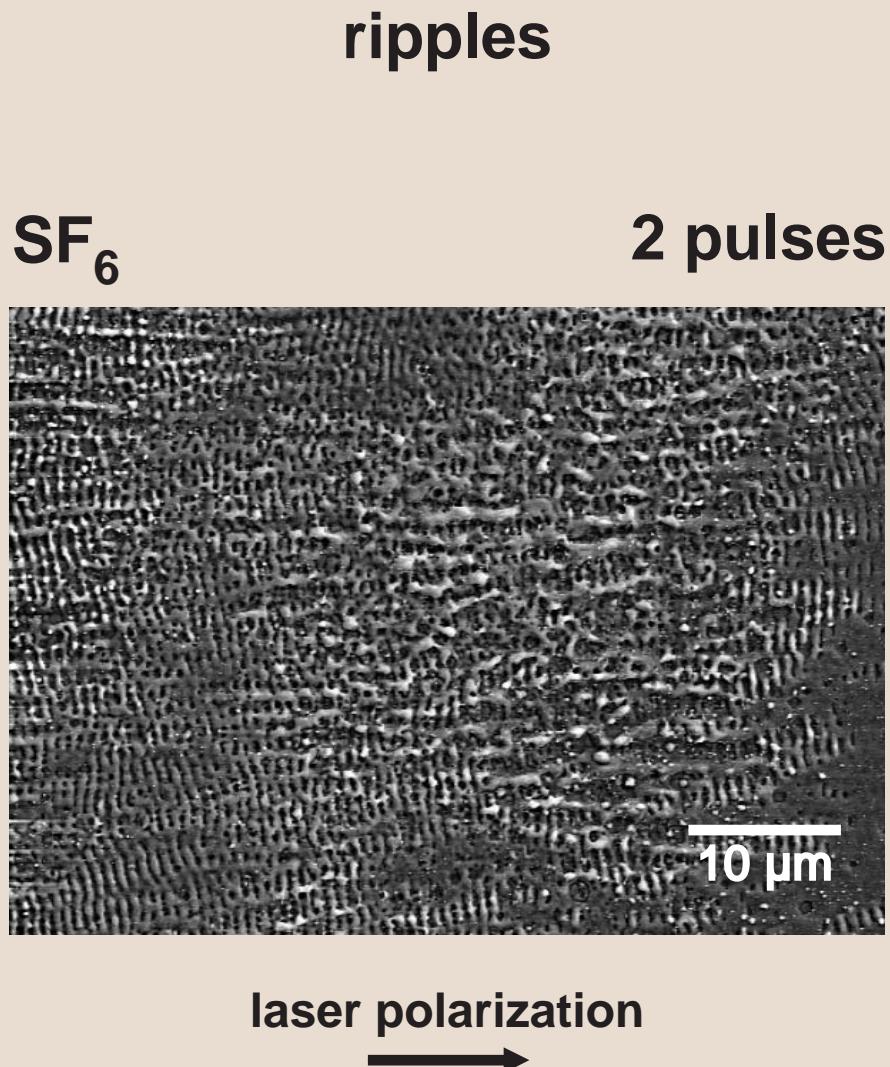
$SF_6$

2 pulses

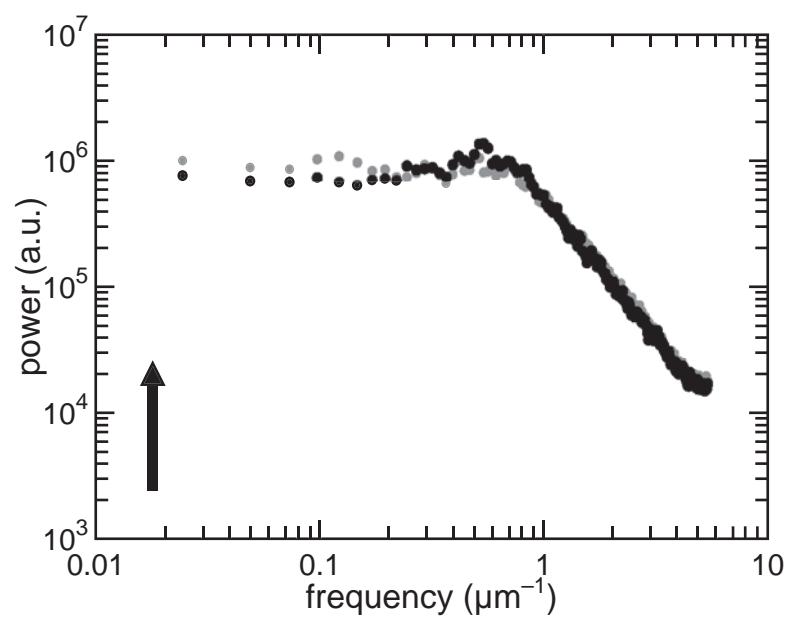
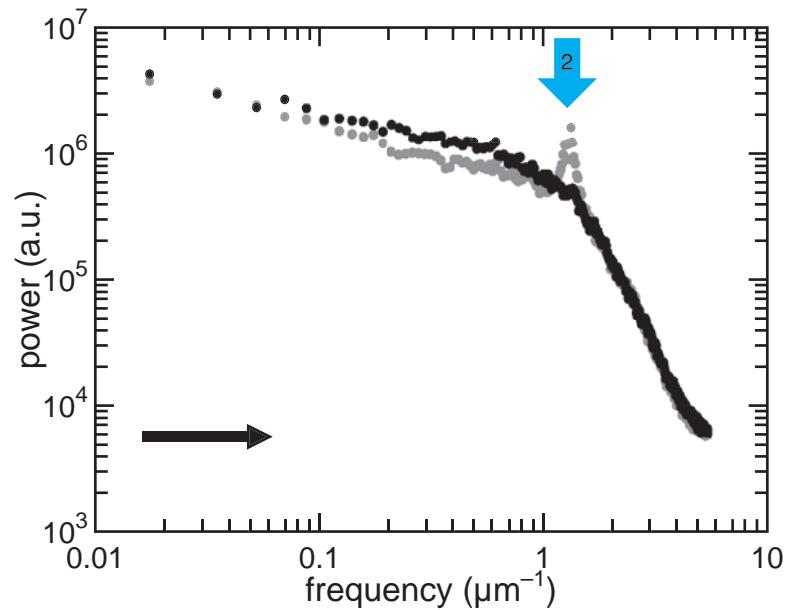
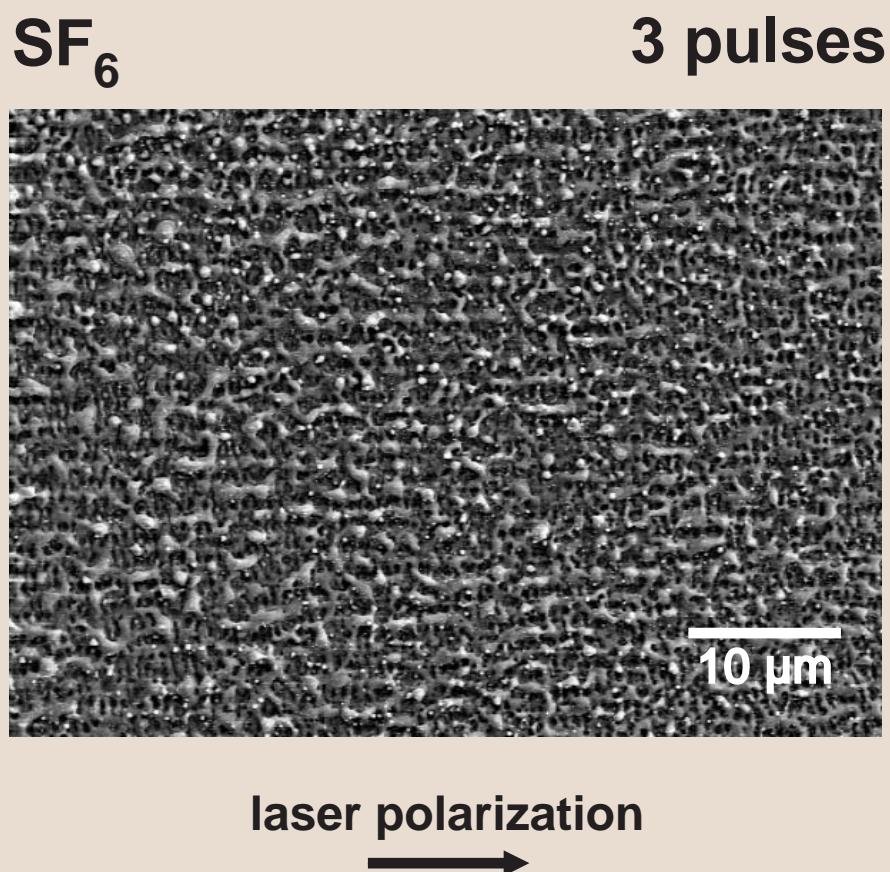


laser polarization  
→

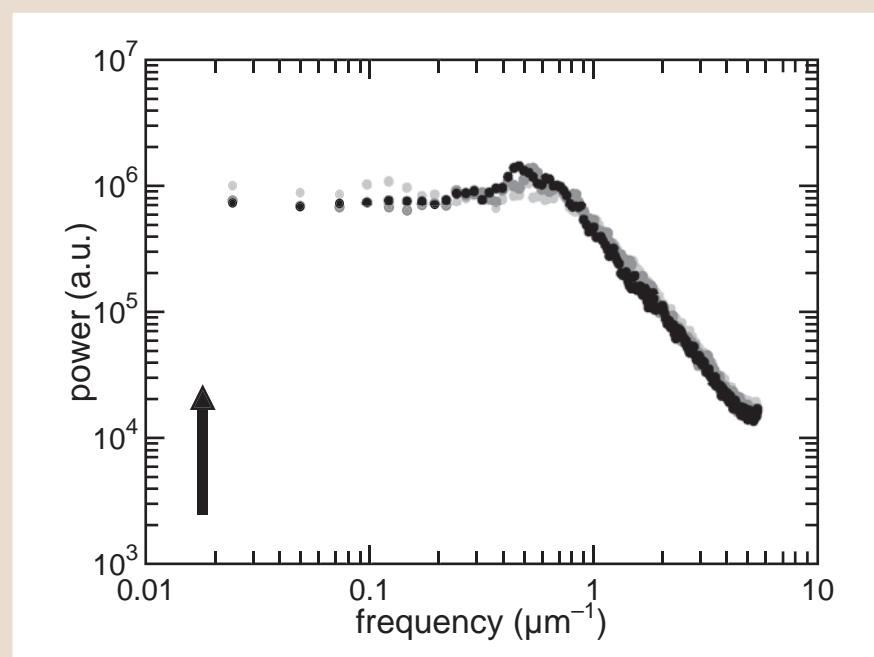
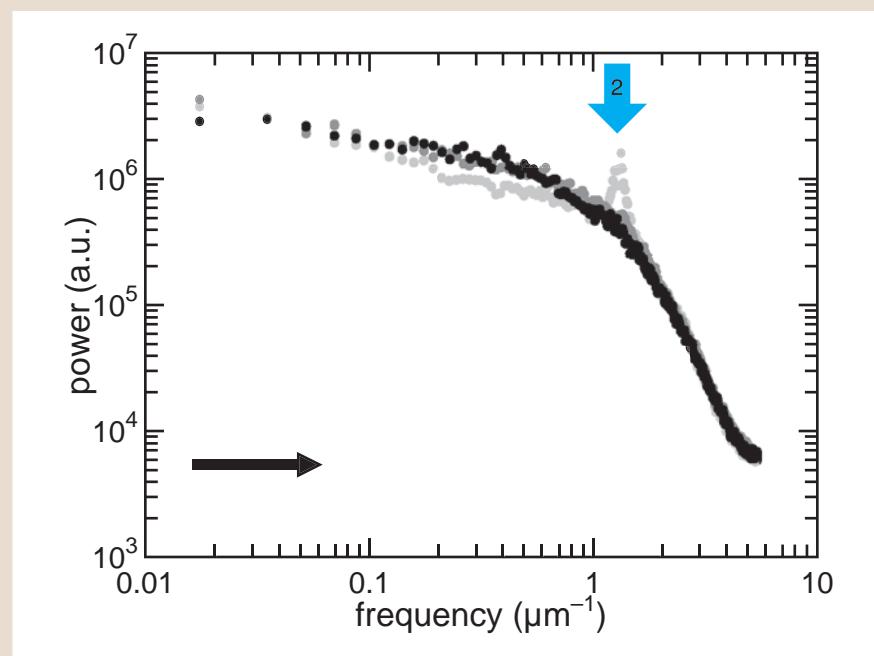
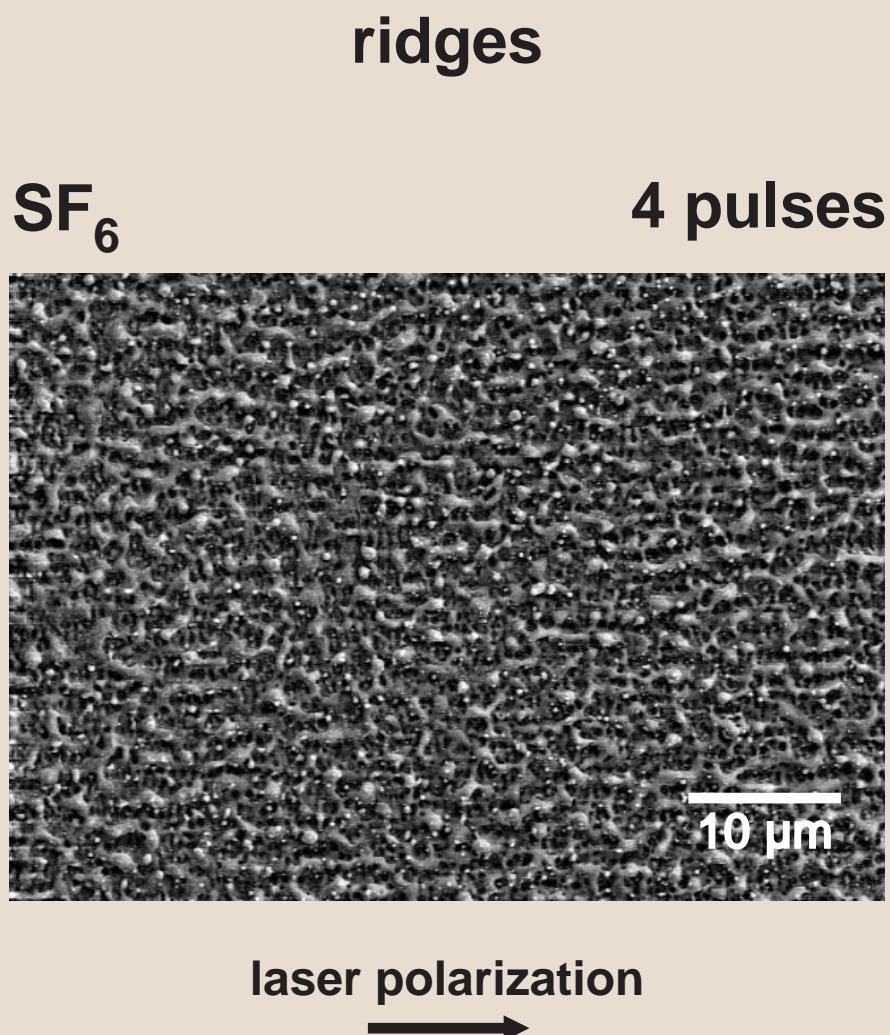
# *Formation process*



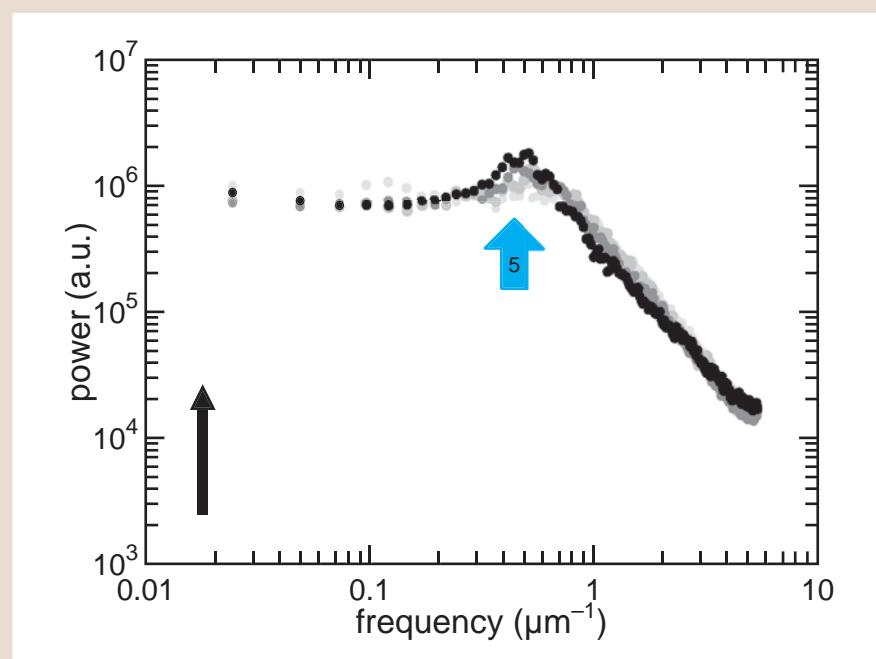
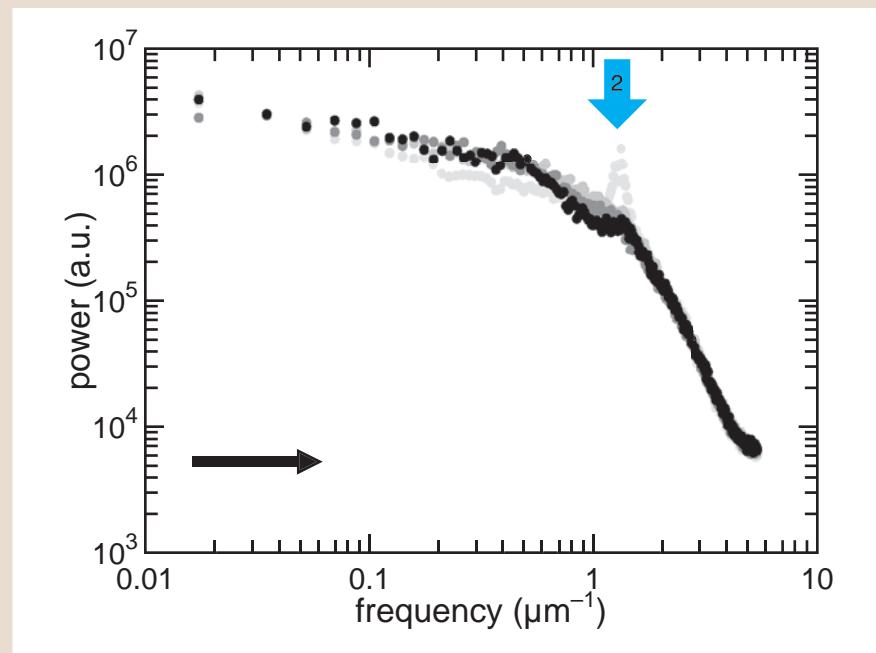
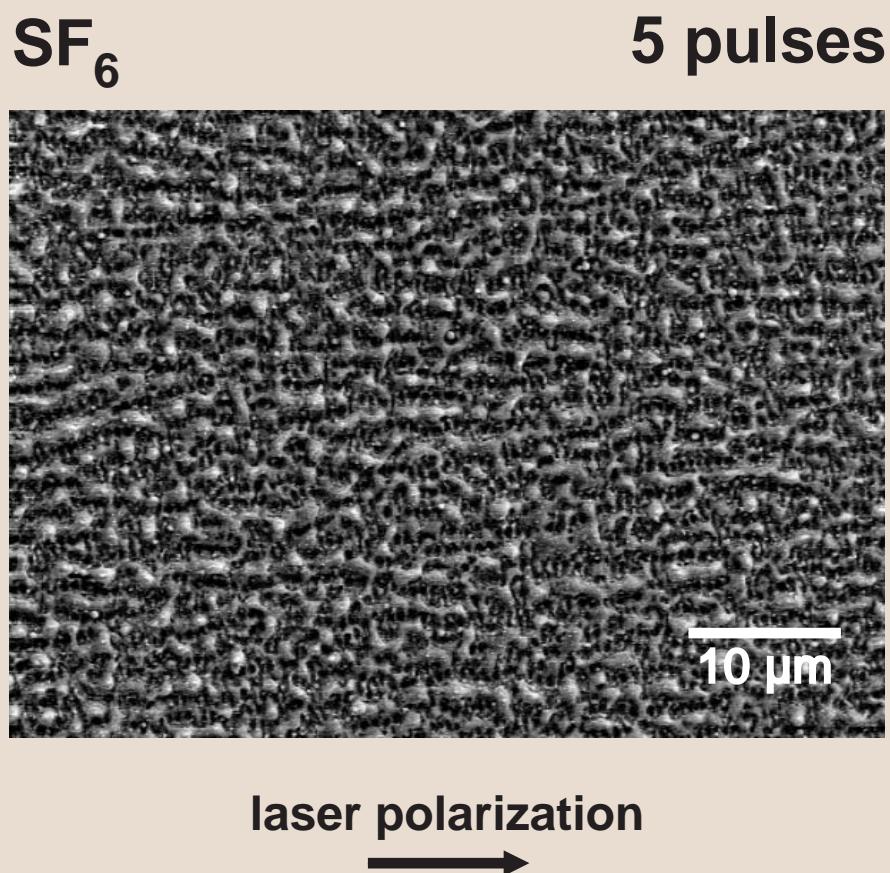
# *Formation process*



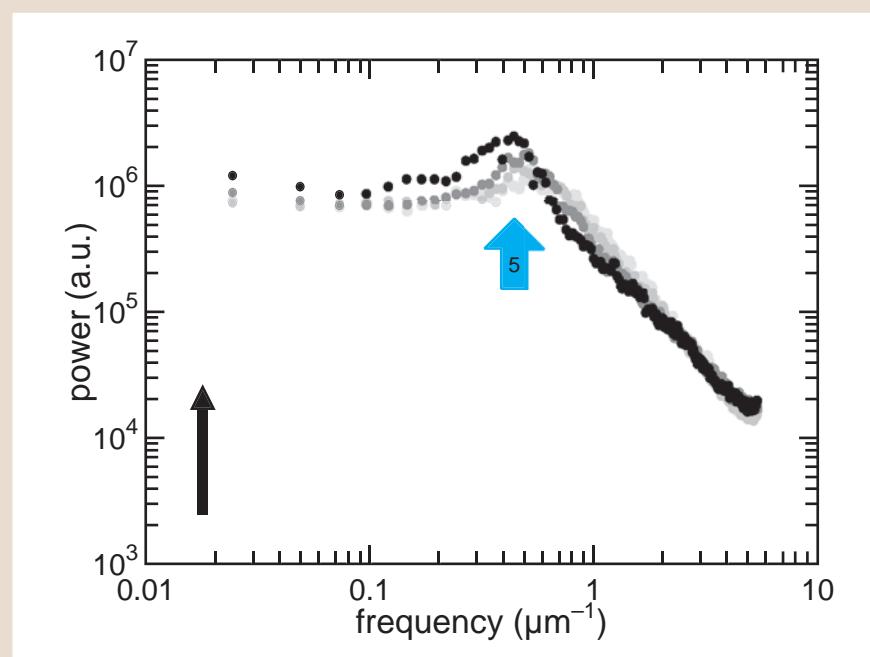
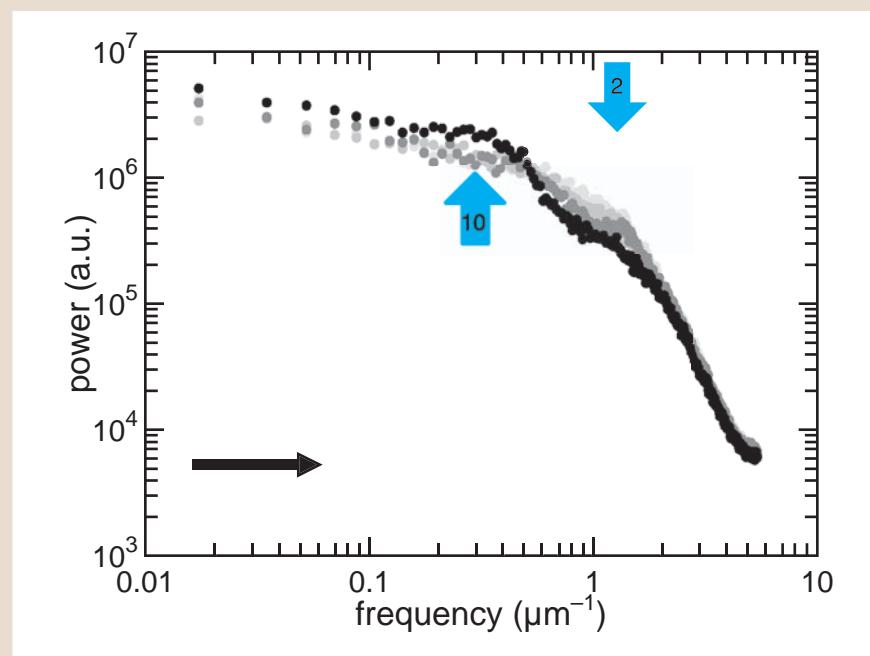
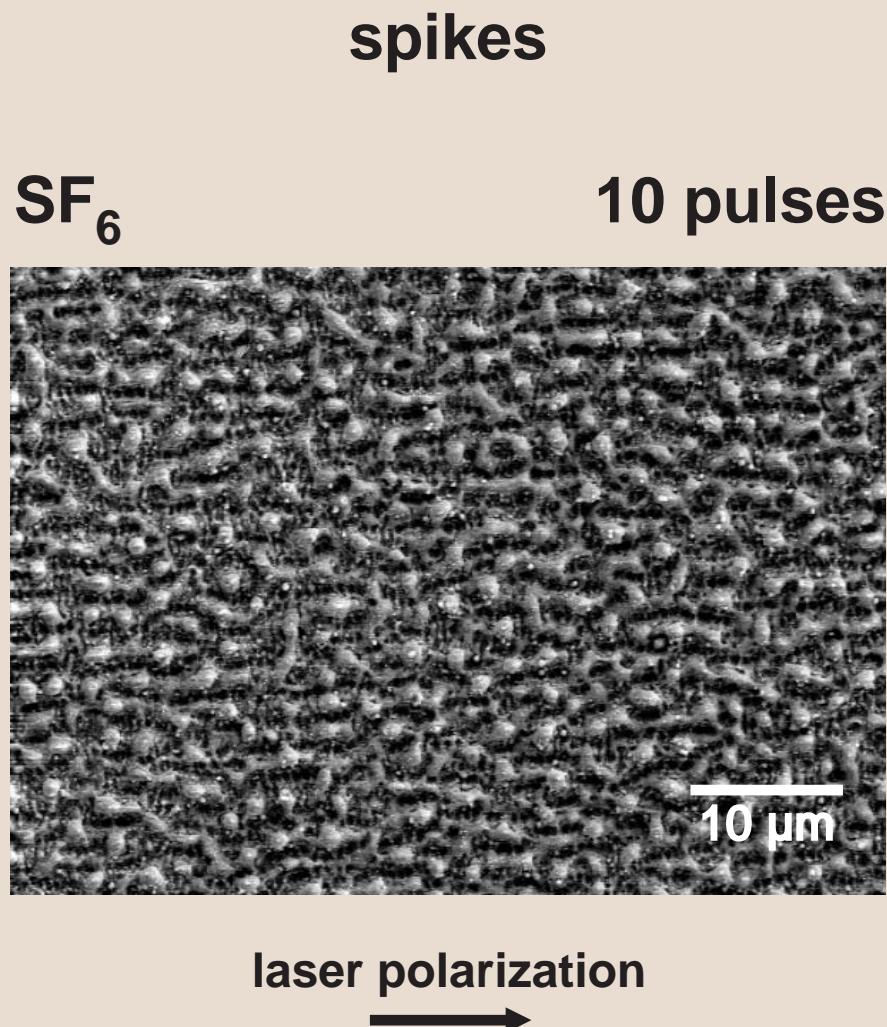
# *Formation process*



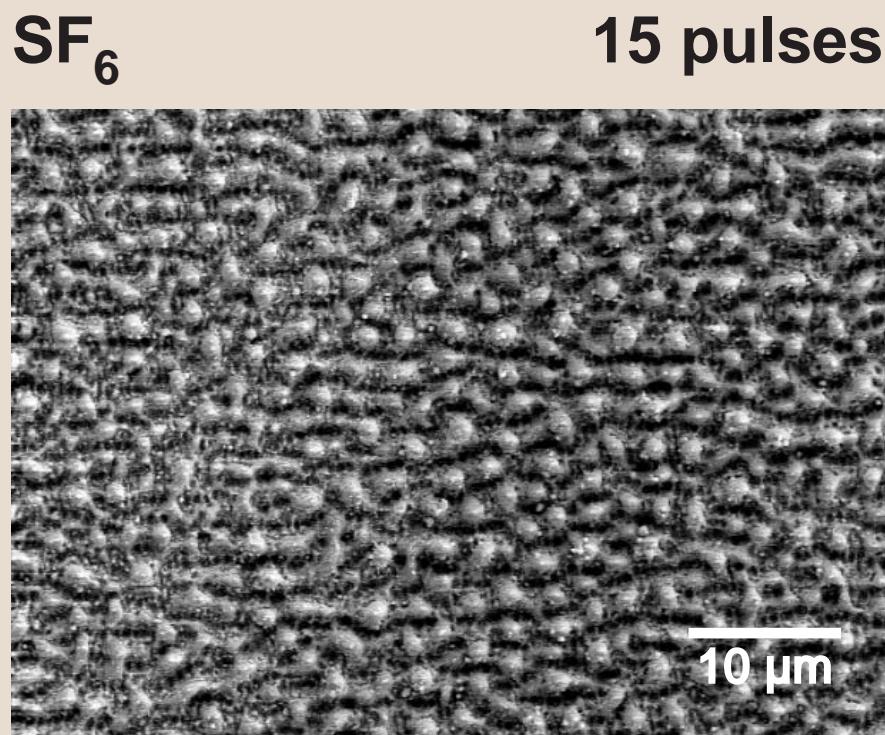
# *Formation process*



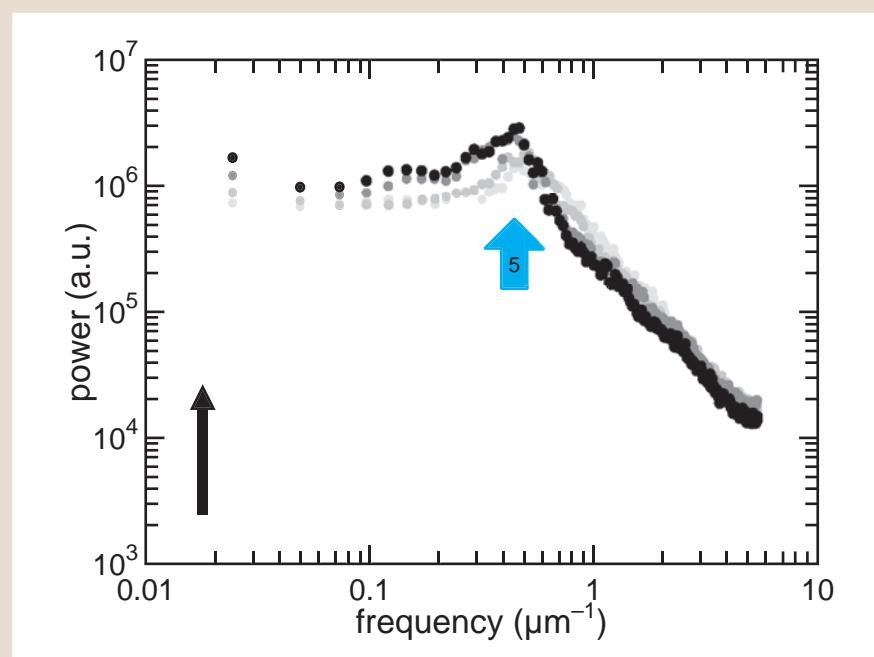
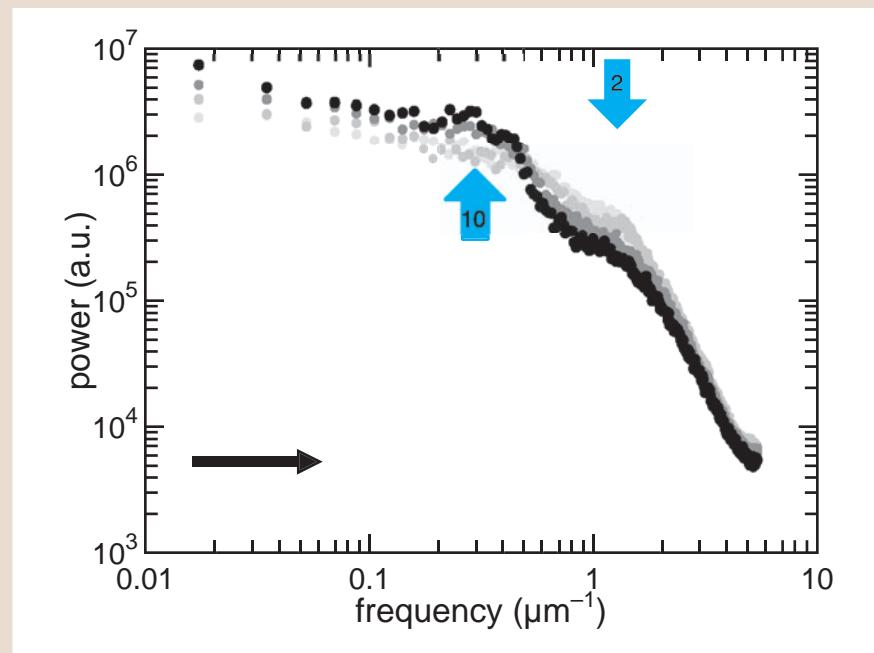
# *Formation process*



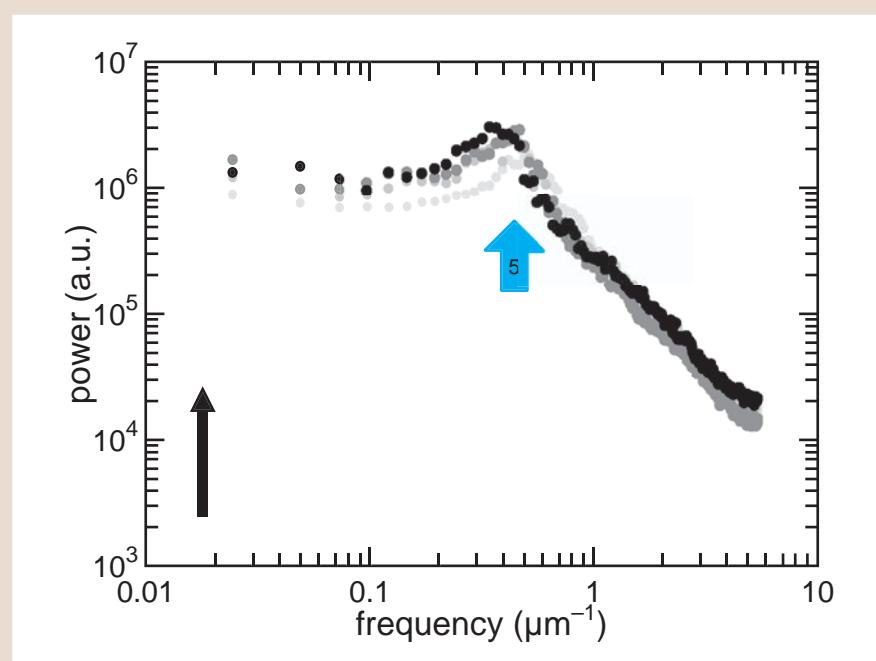
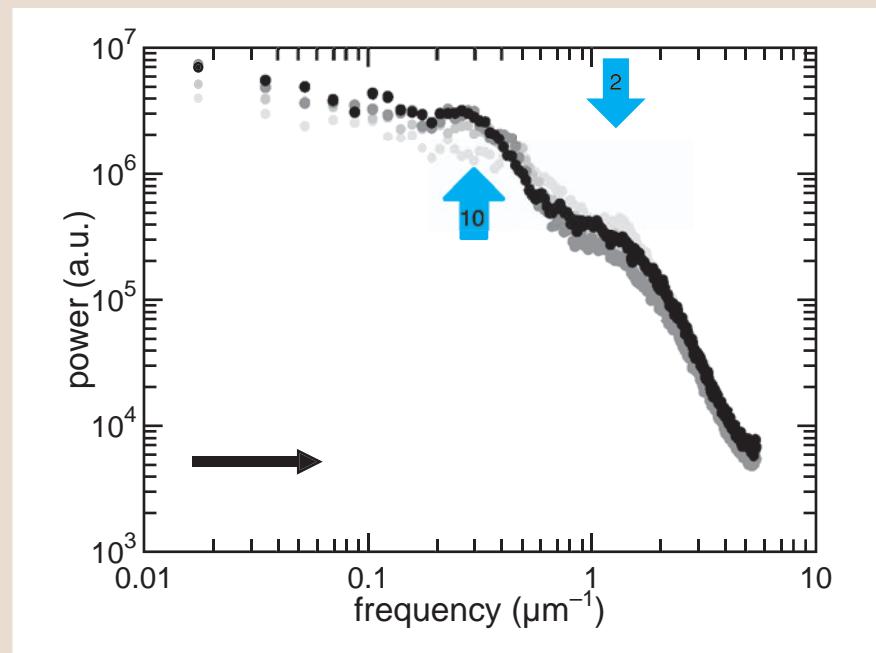
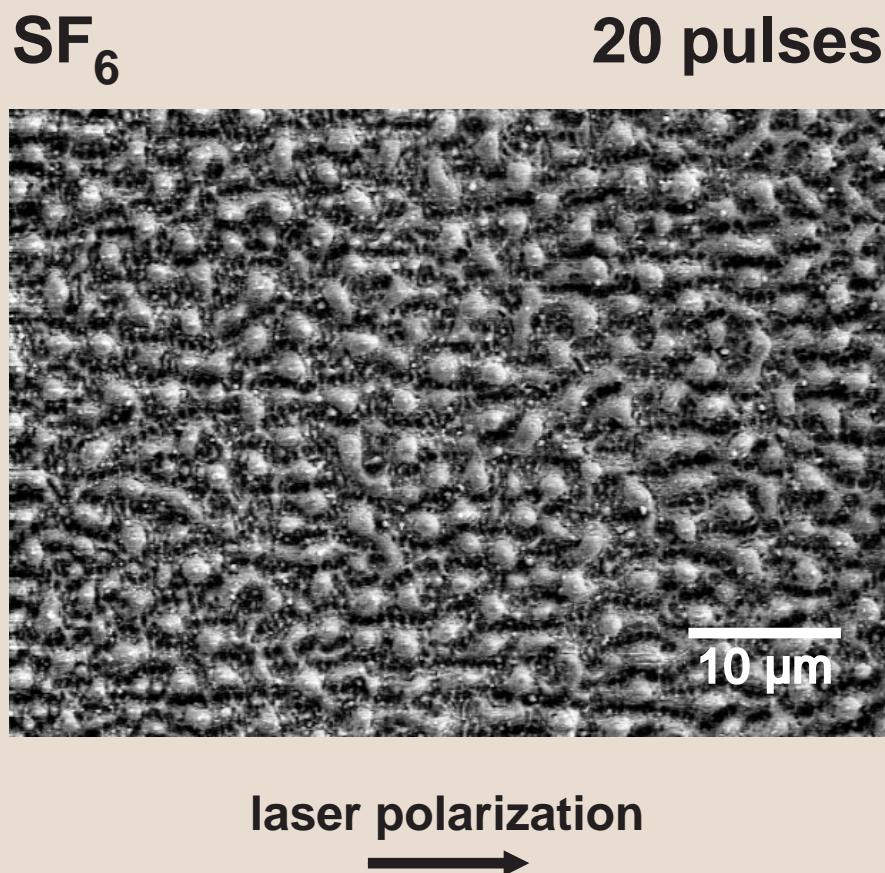
# *Formation process*



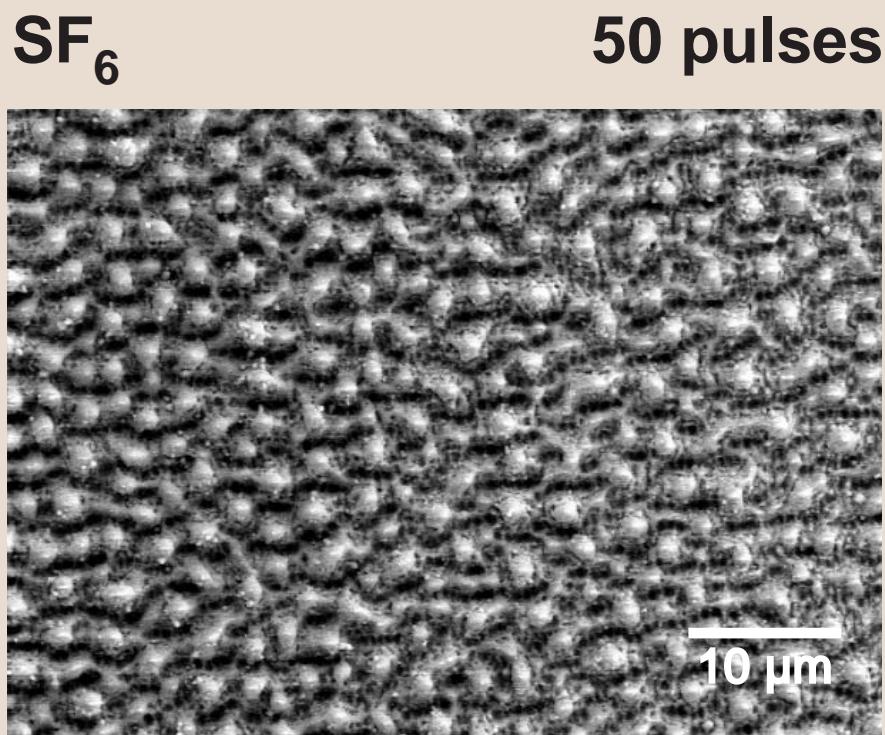
**laser polarization**  
→



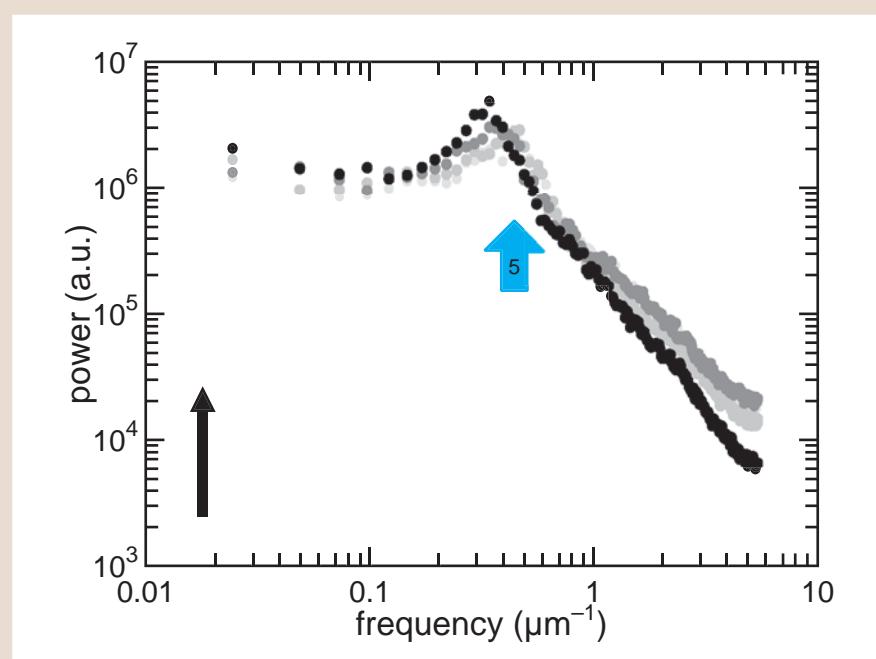
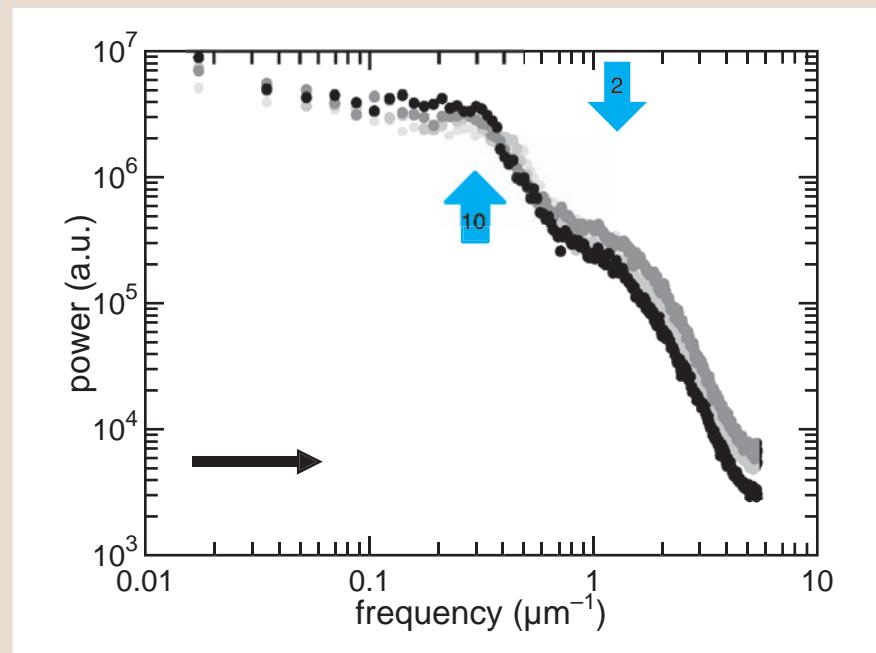
# *Formation process*



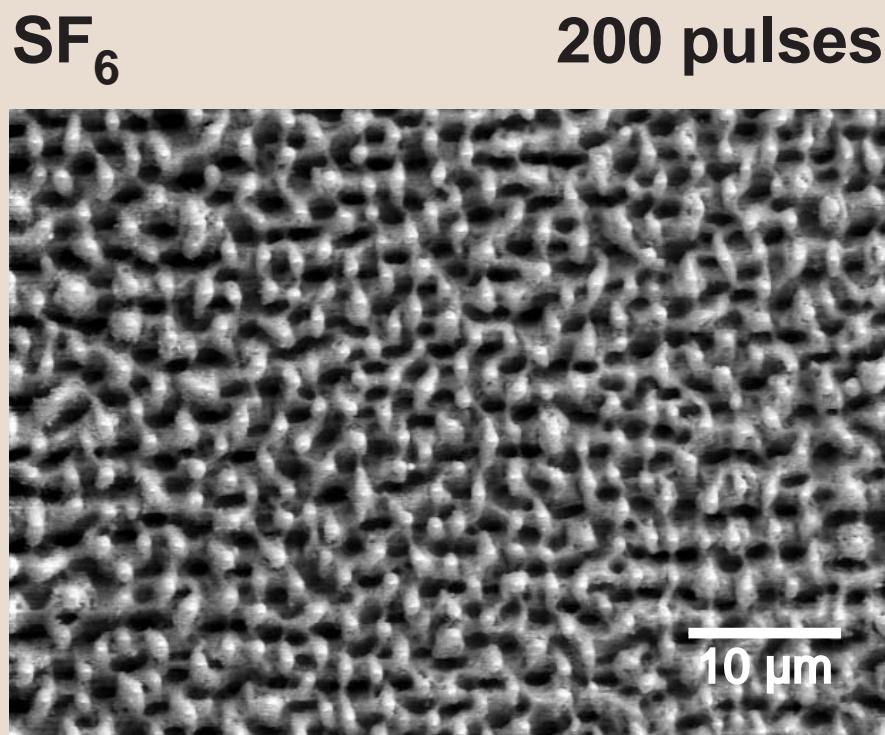
# *Formation process*



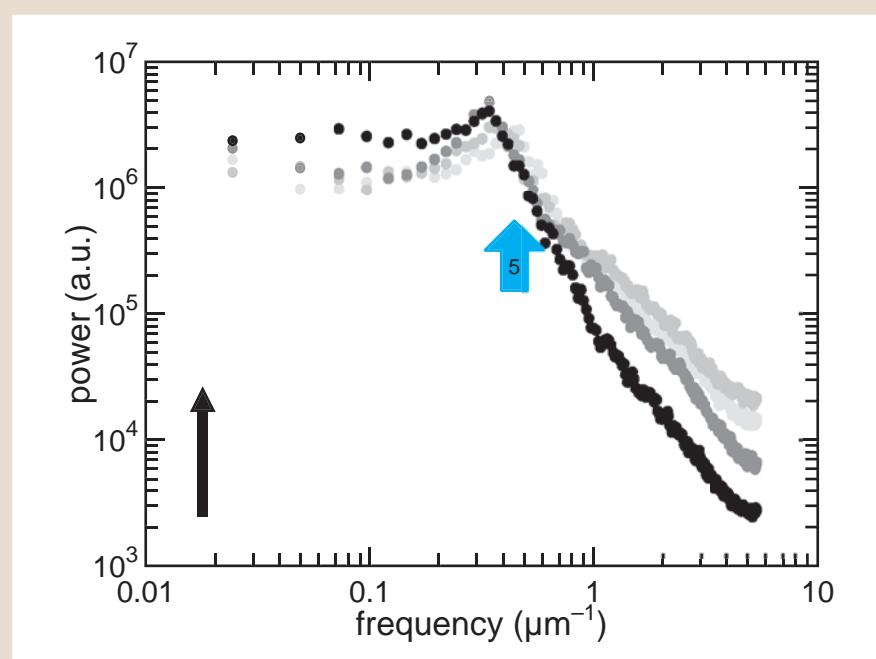
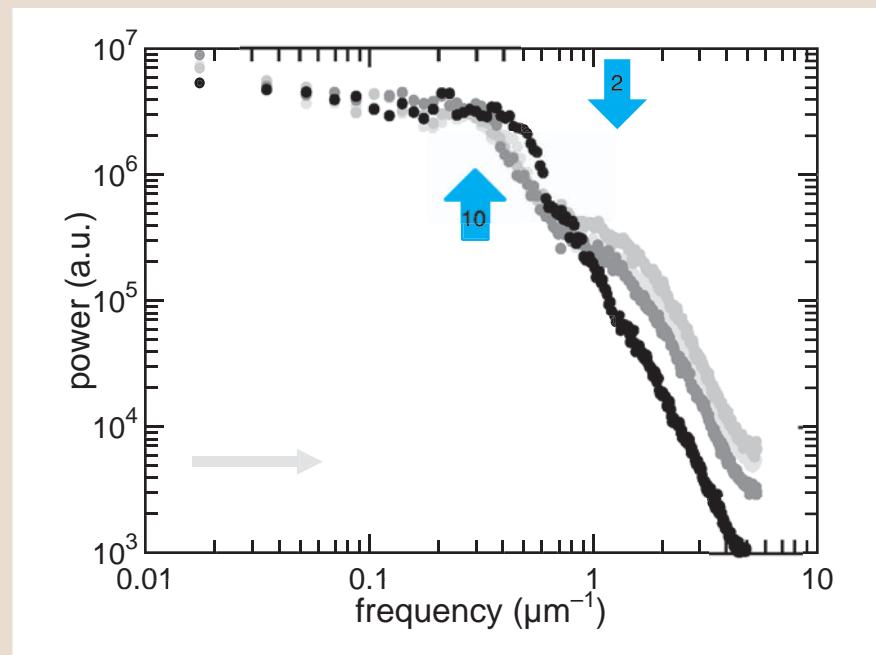
**laser polarization**  
→



# *Formation process*

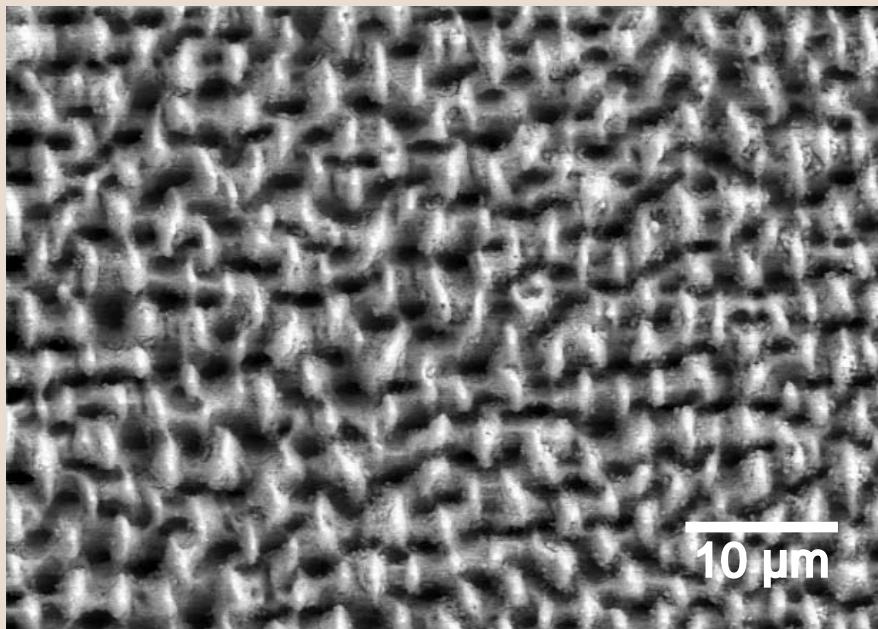


**laser polarization**  
→

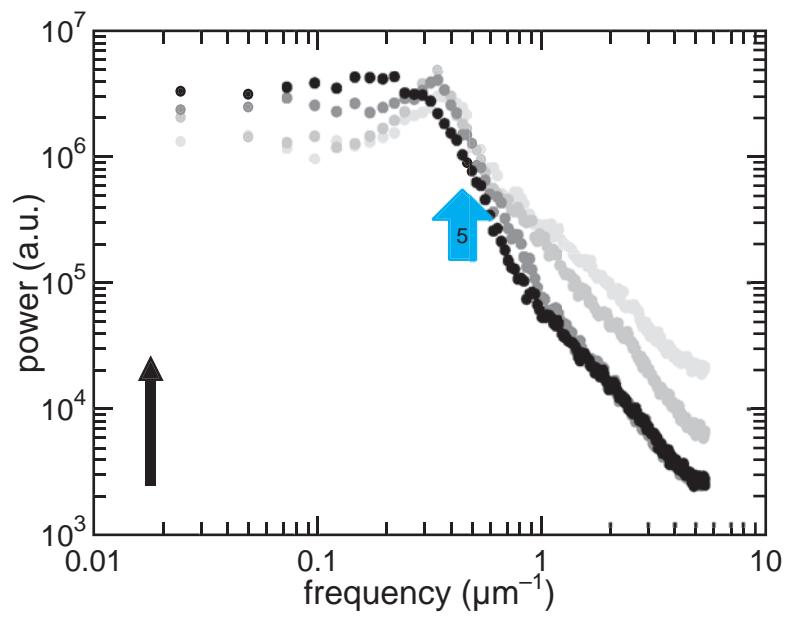
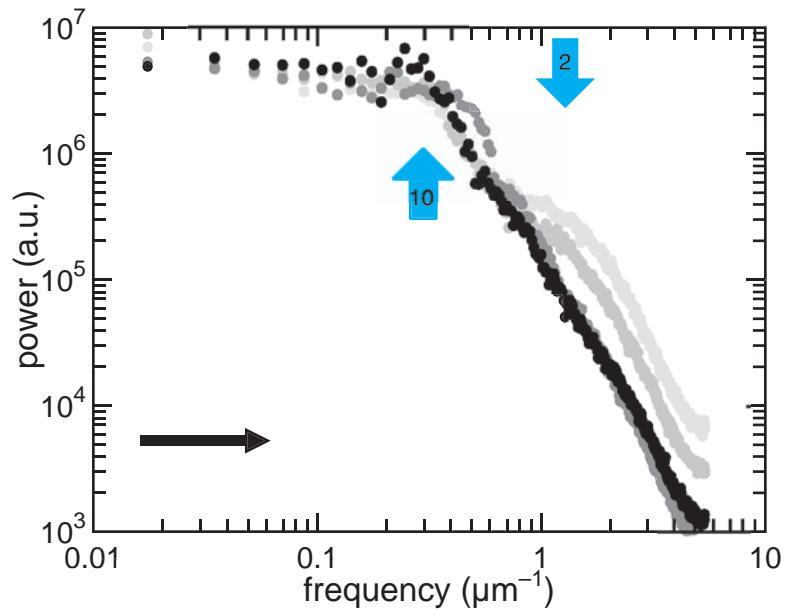


# *Formation process*

**SF<sub>6</sub>**      **500 pulses**

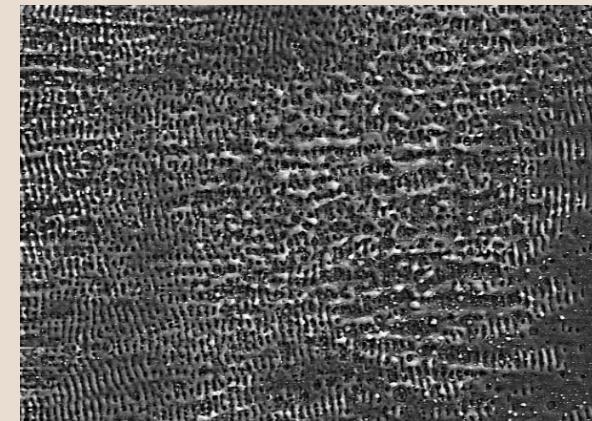


**laser polarization**  
→



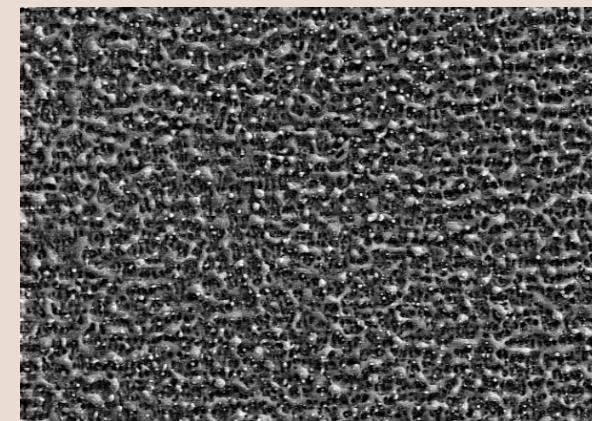
# *Formation process*

**1. Interference ripples  
( $\perp$  to polarization)**



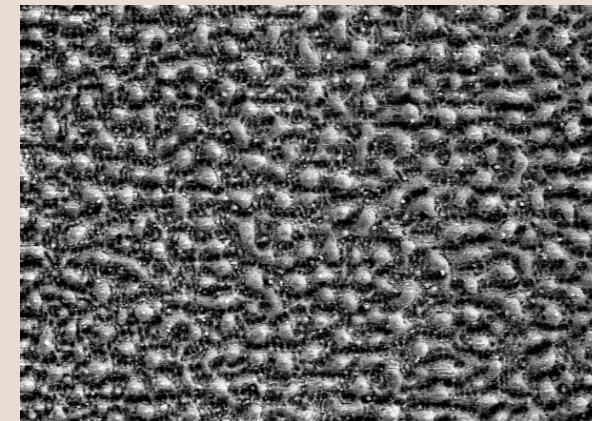
N = 2

**2. Coarsened ridges  
( $\perp$  to ripples)**



N = 4

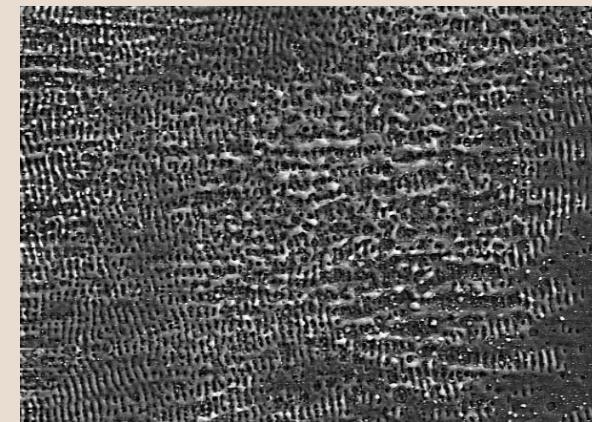
**3. Beads sharpening  
into spikes**



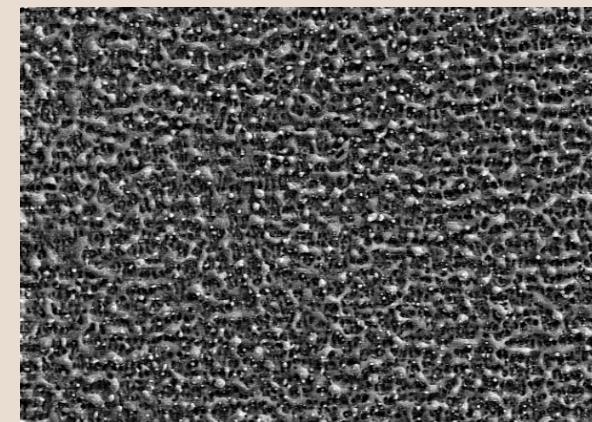
N = 10

# *Formation process*

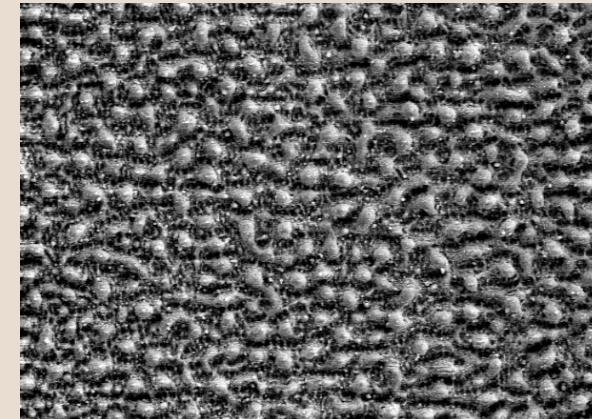
**Two distinct wavelengths:  
ripples and spikes**



N = 2



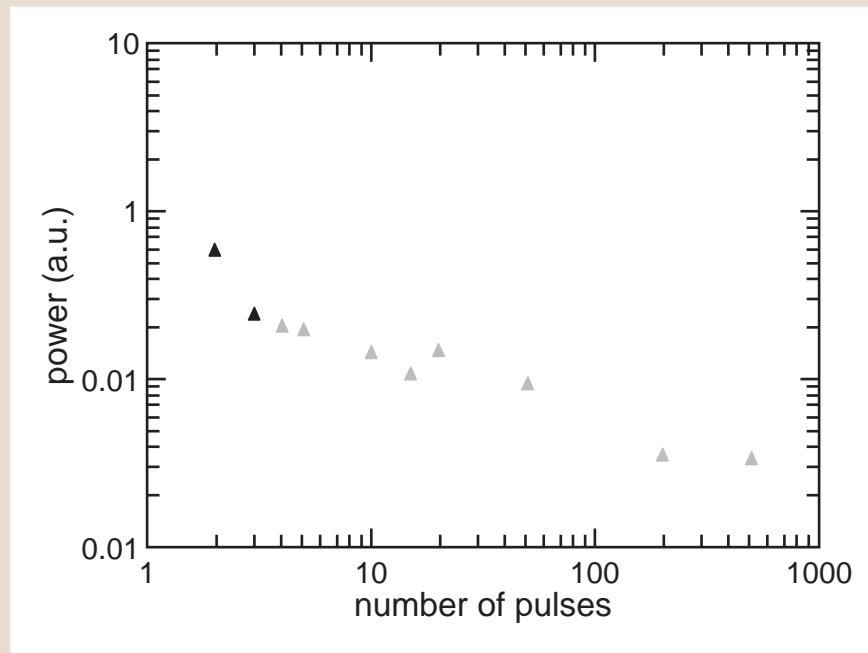
N = 4



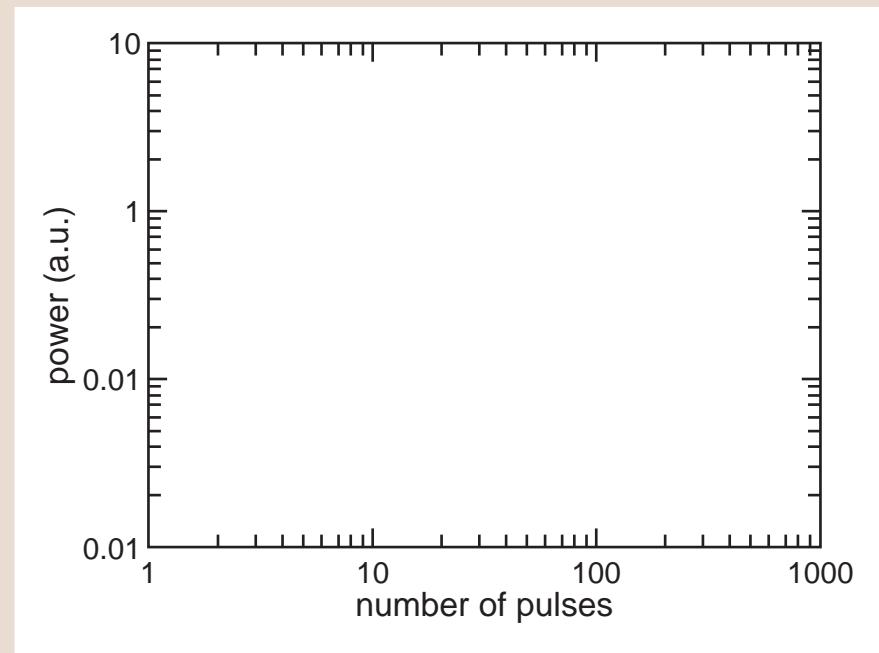
N = 10

## feature intensities

### **SF<sub>6</sub> ripples**



**parallel**

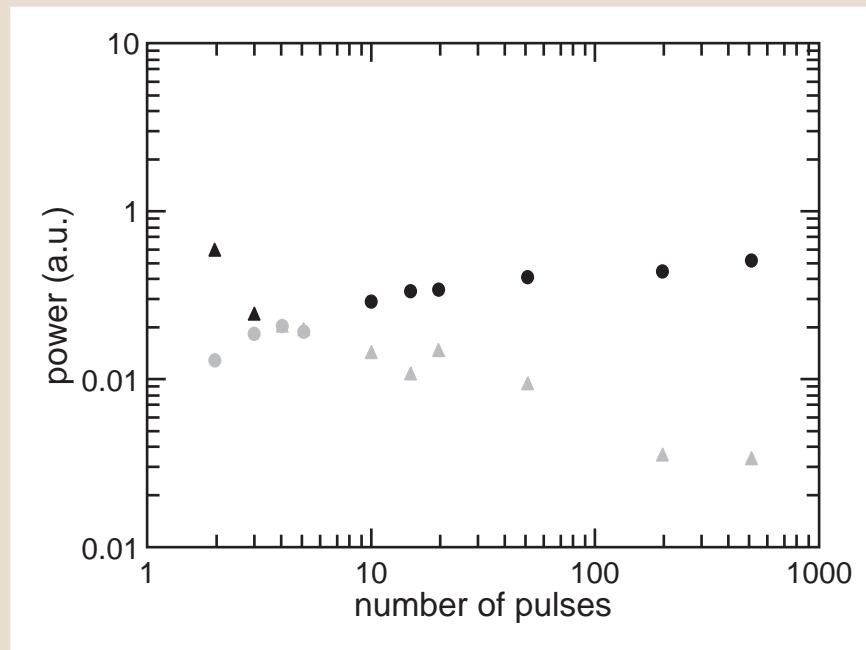


**perpendicular**

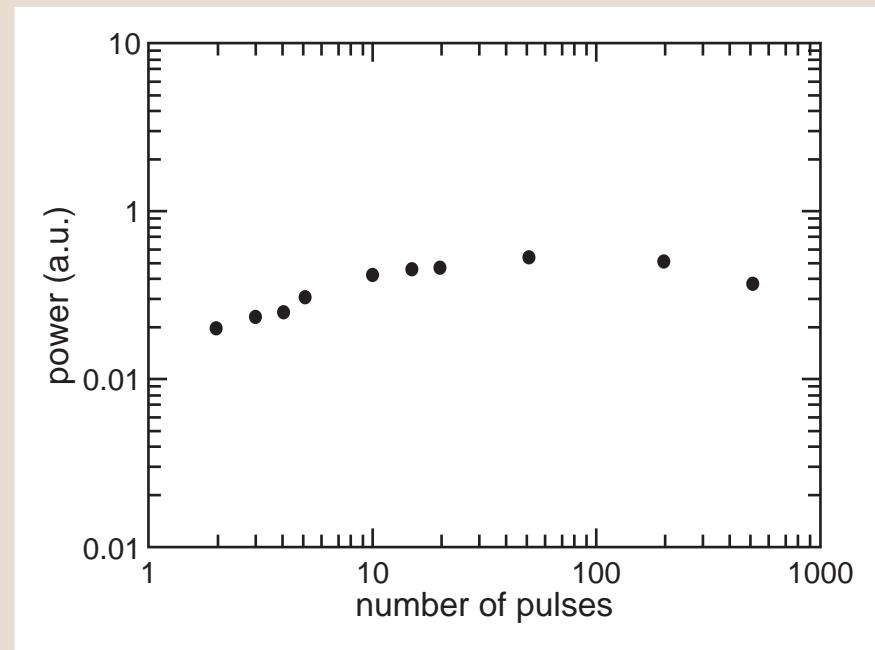
# *Formation process*

## feature intensities

### **SF<sub>6</sub> spikes**



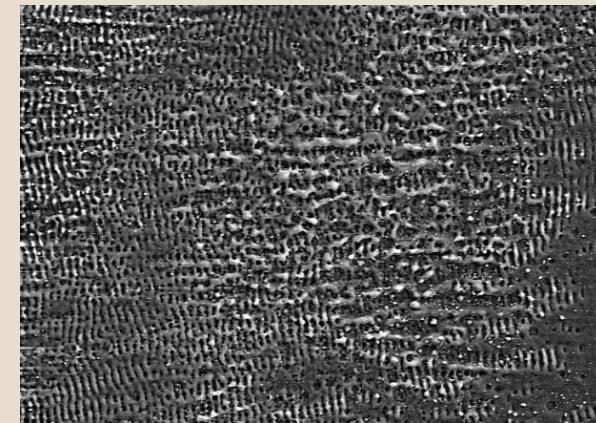
**parallel**



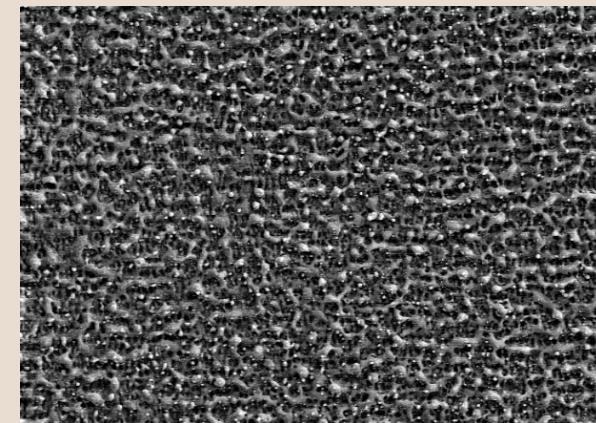
**perpendicular**

# *Formation process*

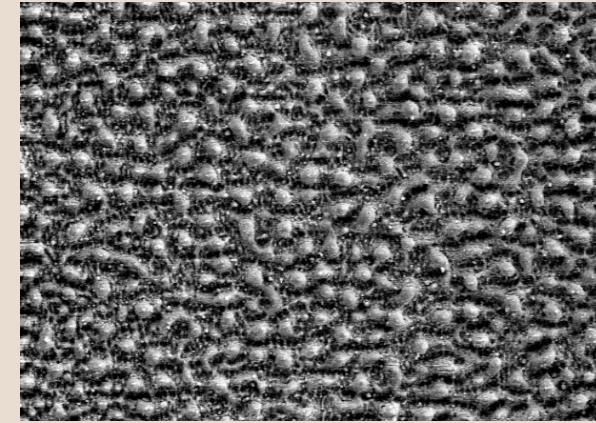
- ▶ **spike wavelength appears as ripple wavelength disappears**
- ▶ **spike wavelength appears first perpendicular to polarization**



N = 2



N = 4



N = 10

## **What sets the length scales?**

- ▶ ripples: laser wavelength
- ▶ ridges and spikes: perhaps capillary waves

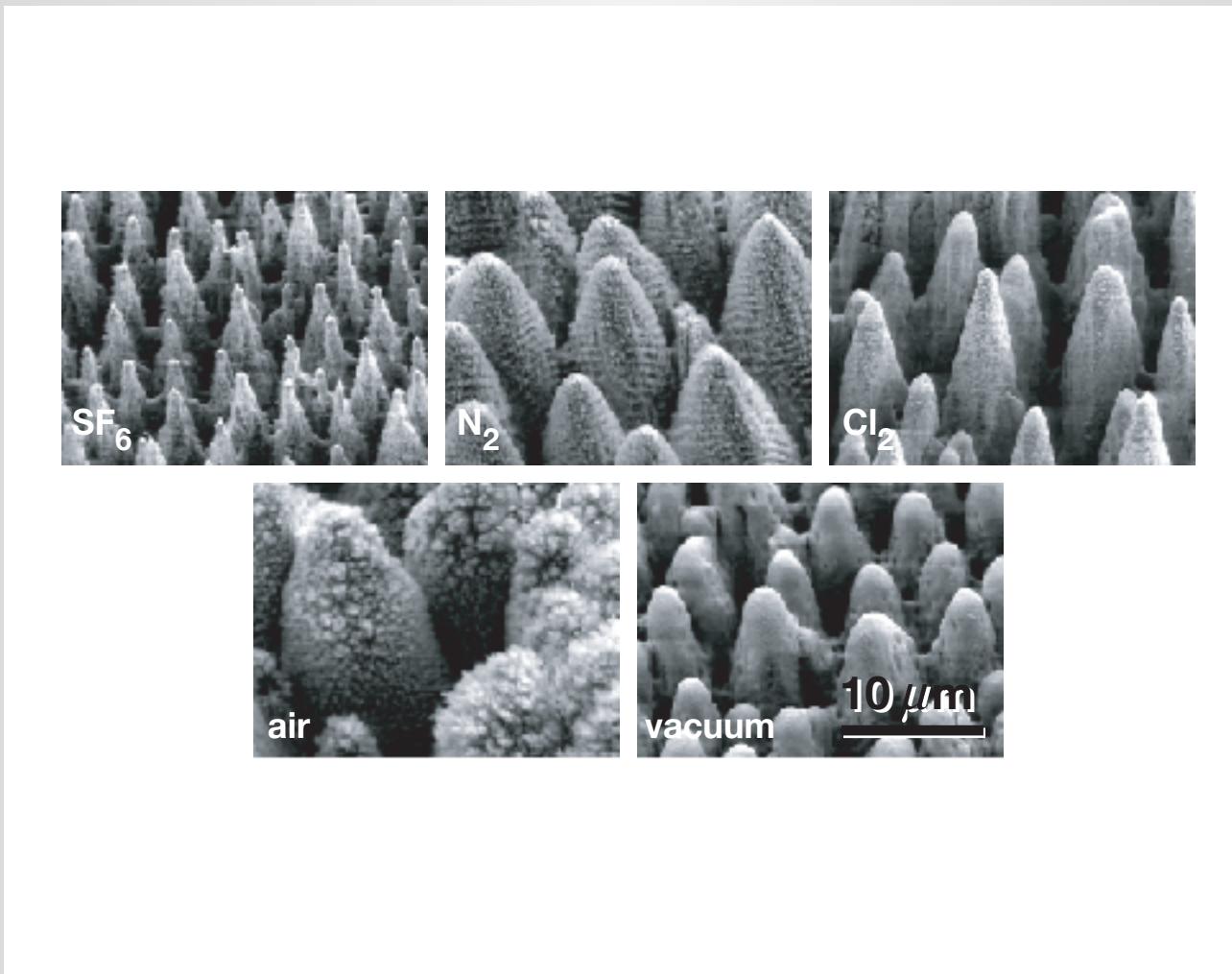
## **Capillary wavelength set by melt depth, duration**

$$\lambda = \left[ \frac{\sigma d}{\rho} \right]^{\frac{1}{4}} (2\pi\tau)^{\frac{1}{2}}$$

- ▶ longest wavelength similar to spike spacing (10 µm)
- ▶ both spike spacing and capillary wavelength increase with laser fluence

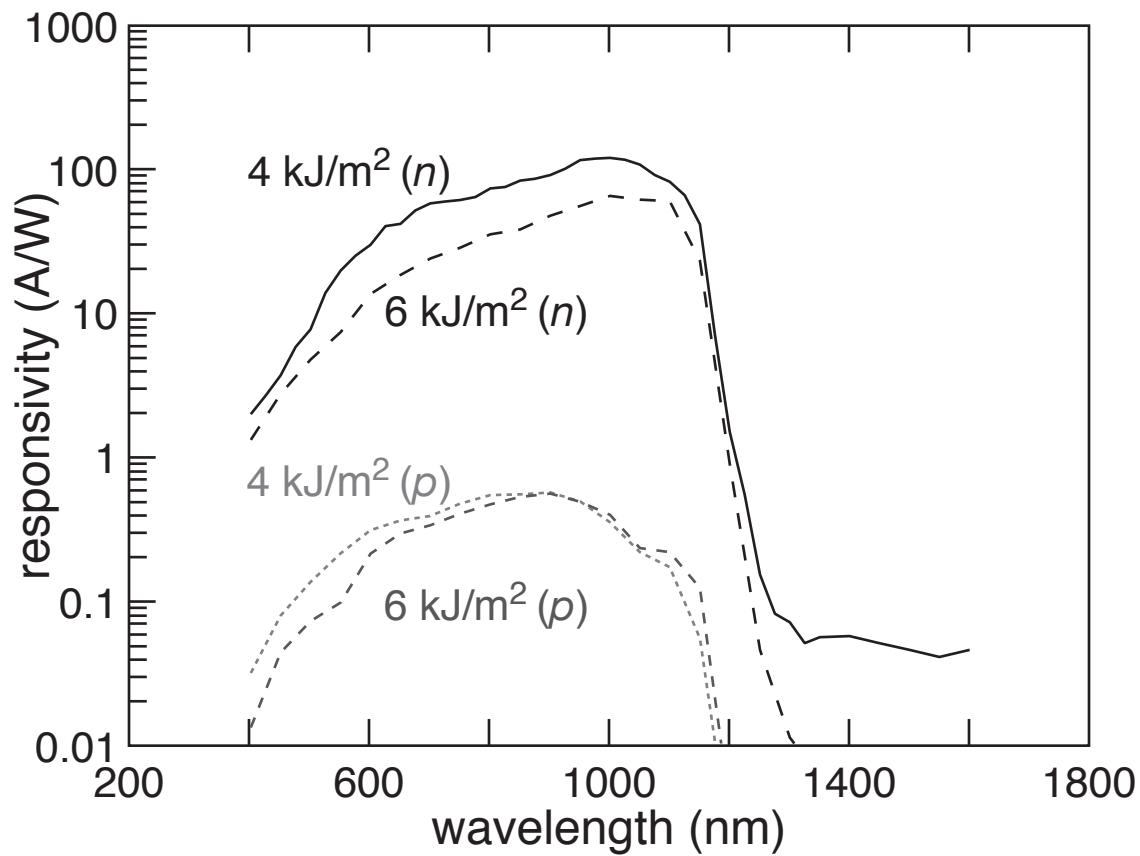
# Structural and chemical analysis

microstructured in different gases



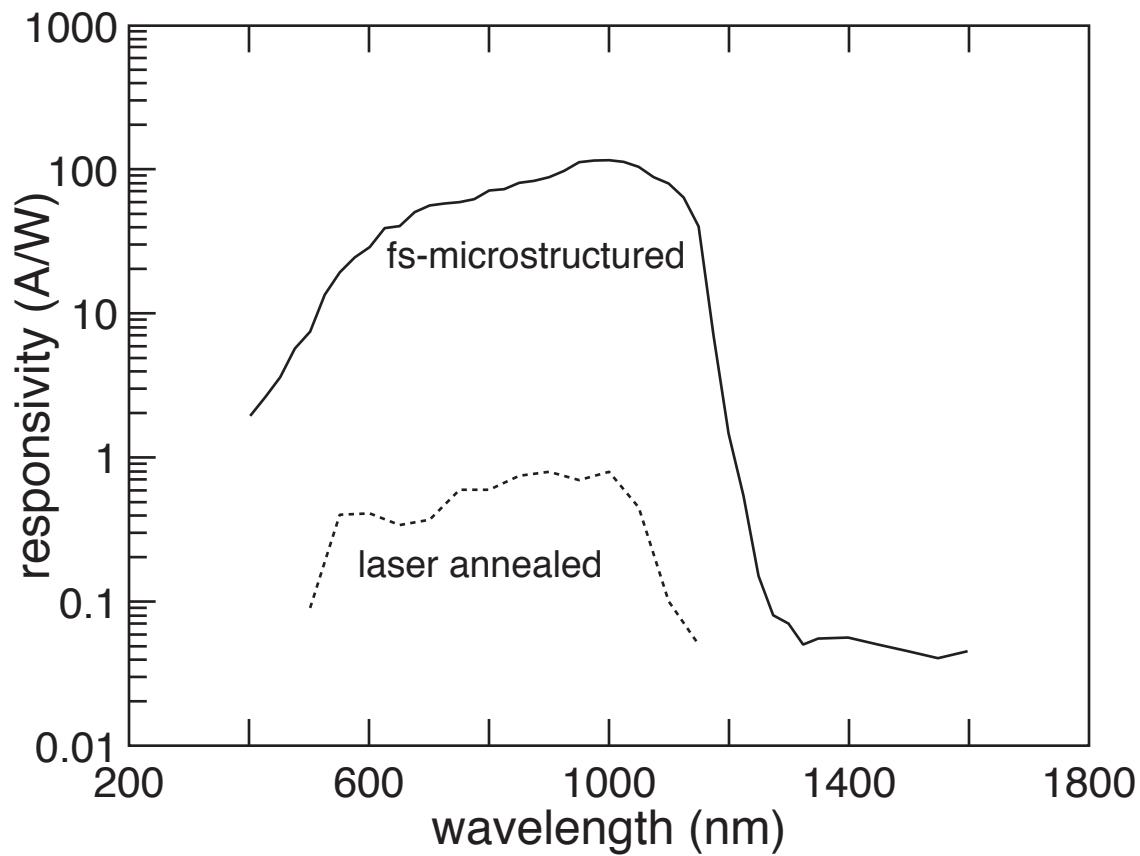
# Responsivity

doping



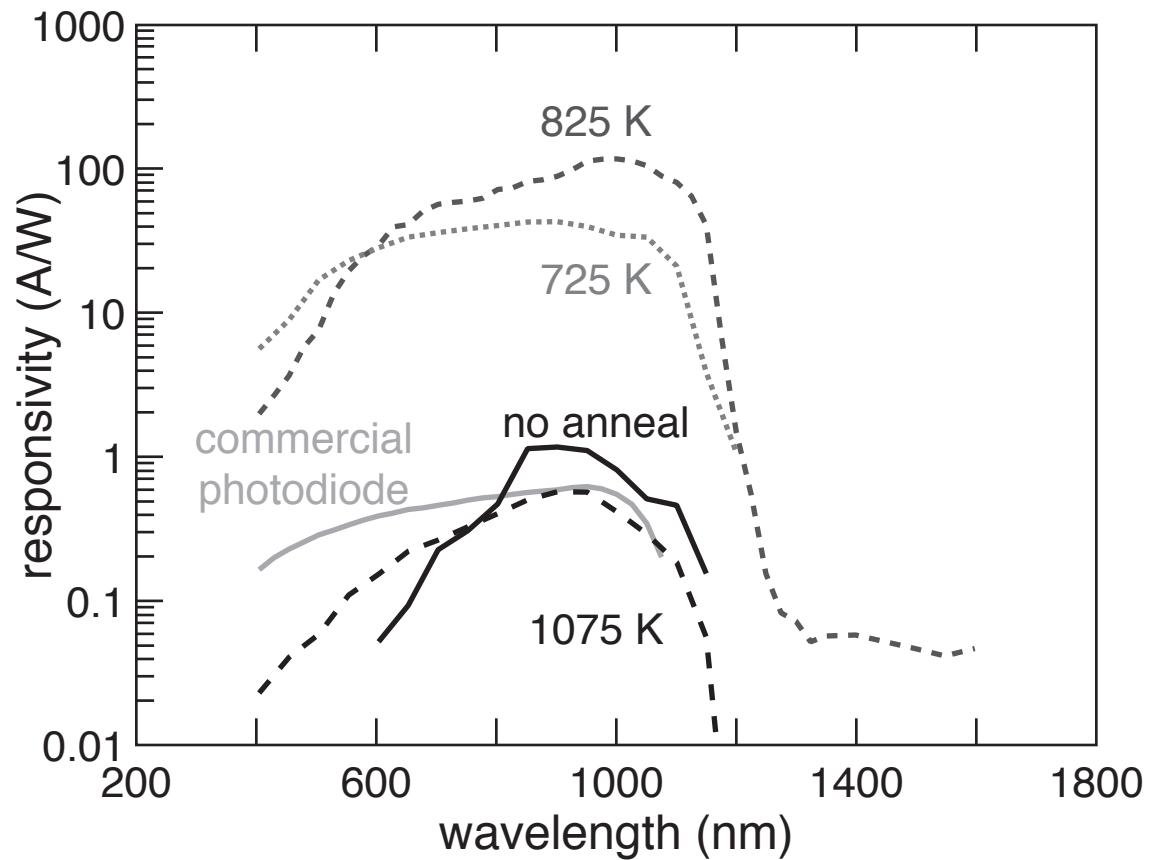
# Responsivity

ion implanted/laser annealed



# Responsivity

annealing



# Responsivity

fluence

